TEXAS INSTRUMENTS

# SCR and Triac

# Data Manual & Application Information

1995

# *SCR and Triac*

## *Data Manual and Application Information*

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## INTRODUCTION

The 1995 SCR AND TRIAC DATA MANUAL AND APPLICATIONS INFORMATION from Texas Instruments includes complete detailed specifications on the thyristor product line. These devices are designed to control the power taken by alternating current equipment, including household appliances (motor control) and industrial systems (power control). The SCRs can be used for ac half wave control of mains power circuits up to 2 kW or in dc circuits with commutation or current limitation (e.g. gas ignitors) For full wave ac control, the triacs can be used for mains power circuits up to 6 kW

The data book is divided into 6 chapters. Below you will find a brief description of each chapter.

*Chapter 1.* Selection Guide - An easy-to-use reference guide that includes specific device information. Page numbers are shown for easy access to the detailed specifications.

*Chapter 2.* Glossary/Data Sheet Structure - Defines terms and standards used throughout the book.

*Chapters 3 - 4.* Product specifications for over 60 thyristors are given in these sections.

*Chapter 5.* Applications Information - Includes thyristor electrical and thermal characteristics, triggering modes, design tolerancing and circuit examples.

*Chapter 6.* Mechanical Data - Detailed package drawings and specifications are shown in this section.

For ordering information or further assistance please contact the sales representation listed in the back of this book. For additional copies of this book please return the pre-paid order form included inside the back cover.

# Contents

**Contents continued**

**Contents continued**

# *Selection Guide*

## SILICON CONTROLLED RECTIFIERS

| DEVICE NUMBER | $V_{DRM}$ (V) | $I_{T(RMS)}$ (A) | $I_{TM}$ (A) | dv/dt typ (V/µs) | $V_{GT(MAX)}$ (V) | $I_{GT(MAX)}$ (mA) | PACKAGE | PAGE |
|---|---|---|---|---|---|---|---|---|
| TIC106D | 400 | 5 | 30 | 10 | 1.0 | 0.2 | TO-220 | 3-3 |
| TIC106M | 600 | | | | | | | |
| TIC106S | 700 | | | | | | | |
| TIC106N | 800 | | | | | | | |
| TIC108D | 400 | 5 | 20 | 80 | 1.0 | 1 | TO-220 | 3-9 |
| TIC108M | 600 | | | | | | | |
| TIC108S | 700 | | | | | | | |
| TIC108N | 800 | | | | | | | |
| TIC116D | 400 | 8 | 80 | 100 | 1.5 | 20 | TO-220 | 3-15 |
| TIC116M | 600 | | | | | | | |
| TIC116S | 700 | | | | | | | |
| TIC116N | 800 | | | | | | | |
| TIC126D | 400 | 12 | 100 | 100 | 1.5 | 20 | TO-220 | 3-21 |
| TIC126M | 600 | | | | | | | |
| TIC126S | 700 | | | | | | | |
| TIC126N | 800 | | | | | | | |
| TICP106D | 400 | 2 | 15 | 10 | 1.0 | 0.2 | TO-92 | 3-27 |
| TICP106M | 600 | | | | | | | |

## TRIACS

| DEVICE NUMBER | $V_{DRM}$ (V) | $I_{T(RMS)}$ (A) | $I_{TSM}$ (A) | dv/dt (V/µs) | $dv/dt_{(c)}min$ (V/µs) | $I_{GT(MAX)}$ (mA) | | | | $V_{GT(MAX)}$ (V) | | PACKAGE | PAGE |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| | | | | | | MT2 + G + | MT2 + G - | MT2 - G- | MT2 - G + | MT2 + + - G + - - | MT2 - G + | | |
| TIC201D | 400 | 2.5 | 14 | 50 | 2 | 5 | 8 | 10 | 25 | 2.5 | - | TO-220 | 4-3 |
| TIC201M | 600 | | | | | | | | | | | | |
| TIC201S | 700 | | | | | | | | | | | | |
| TIC201N | 800 | | | | | | | | | | | | |
| TIC206D | 400 | 4 | 30 | 50 | 1 | 5 | 5 | 5 | 10 | 2 | 2 | TO-220 | 4-5 |
| TIC206M | 600 | | | | | | | | | | | | |
| TIC206S | 700 | | | | | | | | | | | | |
| TIC206N | 800 | | | | | | | | | | | | |
| TIC216D | 400 | 6 | 70 | 50 | 5 | 5 | 5 | 5 | 10 | 2.2 | 3 | TO-220 | 4-9 |
| TIC216M | 600 | | | | | | | | | | | | |
| TIC216S | 700 | | | | | | | | | | | | |
| TIC216N | 800 | | | | | | | | | | | | |

TEXAS INSTRUMENTS

## TRIACS (continued)

| DEVICE NUMBER | $V_{DRM}$ (V) | $I_{T(RMS)}$ (A) | $I_{TSM}$ (A) | dv/dt (V/µs) | $dv/dt_{(c)}min$ (V/µs) | $I_{GT(MAX)}$ (mA) | | | | $V_{GT(MAX)}$ (V) | | PACKAGE | PAGE |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| | | | | | | MT2 + G + | MT2 + G - | MT2 - G- | MT2 - G + | MT2 + + - G + - - | MT2 - G + | | |
| TIC225D | 400 | 8 | 70 | 50 | 1 | 5 | 10 | 10 | 30 | 2 | 2 | TO-220 | 4-11 |
| TIC225M | 600 | | | | | | | | | | | | |
| TIC225S | 700 | | | | | | | | | | | | |
| TIC225N | 800 | | | | | | | | | | | | |
| TIC226D | 400 | 8 | 80 | 100 | 5 | 50 | 50 | 50 | - | 2 | 2 | TO-220 | 4-15 |
| TIC226M | 600 | | | | | | | | | | | | |
| TIC226S | 700 | | | | | | | | | | | | |
| TIC226N | 800 | | | | | | | | | | | | |
| TIC236D | 400 | 12 | 100 | 400 | 1.2 | 50 | 50 | 50 | - | 2 | 2 | TO-220 | 4-19 |
| TIC236M | 600 | | | | | | | | | | | | |
| TIC236S | 700 | | | | | | | | | | | | |
| TIC236N | 800 | | | | | | | | | | | | |
| TIC246D | 400 | 16 | 125 | 400 | 1.2 | 50 | 50 | 50 | - | 2 | 2 | TO-220 | 4-23 |
| TIC246M | 600 | | | | | | | | | | | | |
| TIC246S | 700 | | | | | | | | | | | | |
| TIC246N | 800 | | | | | | | | | | | | |
| TIC253D | 400 | 20 | 150 | 450 | 1 typ. | 50 | 50 | 50 | - | 2 | 2 | SOT-93 | 4-27 |
| TIC253M | 600 | | | | | | | | | | | | |
| TIC253S | 700 | | | | | | | | | | | | |
| TIC253N | 800 | | | | | | | | | | | | |
| TIC256D | 400 | 20 | 150 | 450 | 1 typ. | 50 | 50 | 50 | - | 2 | 2 | TO-220 | 4-31 |
| TIC256M | 600 | | | | | | | | | | | | |
| TIC256S | 700 | | | | | | | | | | | | |
| TIC256N | 800 | | | | | | | | | | | | |
| TIC263D | 400 | 25 | 175 | 450 | 1 typ. | 50 | 50 | 50 | - | 2 | 2 | SOT-93 | 4-35 |
| TIC263M | 600 | | | | | | | | | | | | |
| TIC263S | 700 | | | | | | | | | | | | |
| TIC263N | 800 | | | | | | | | | | | | |
| TIC266D | 400 | 25 | 175 | 450 | 1 typ. | 50 | 50 | 50 | - | 2 | 2 | TO-220 | 4-39 |
| TIC266M | 600 | | | | | | | | | | | | |
| TIC266S | 700 | | | | | | | | | | | | |
| TIC266N | 800 | | | | | | | | | | | | |
| TICP206D | 400 | 1.5 | 12 | - | - | 8 | 8 | 8 | 10 | 2.5 | 2.5 | TO-92 | 4-43 |
| TICP206M | 600 | | | | | | | | | | | | |

TEXAS INSTRUMENTS

# *Glossary/Data Sheet Structure*

TEXAS INSTRUMENTS

## PART 1 - THYRISTOR STANDARDS

The documents listed below have overriding authority where any conflict may occur with this book.

**EIA and JEDEC Standards**
Electronics Industries Association
2001 Pennsylvania Avenue, N. W.
Washington, D.C. 20006

EIA Standard RS-397: Recommended Standards for Thyristors

JEDEC Standard 77: Letter Symbols, Abbreviations, Terms, and Definitions for Discrete Semiconductor and Optoelectronic Devices

JEDEC Publication 104: Quick reference Guide to Letter Symbols

**IEEE Standards**
Institute of Electrical and Electronic Engineers, Inc.
345 East 47th. Street
New York, N.Y. 10017

IEEE No. 233: Standard Definitions of Terms for Thyristors

**International Electrotechnical Commission Standards**
American National Standards Institute, Inc.
1430 Broadway
New York, N.Y. 10018

IEC Publication 147-IC: Essential Ratings and Characteristics of Semiconductor Devices and General Principals of Measuring Methods

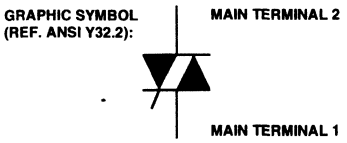
IEC Publication 148: Letter Symbols for Semiconductor Devices and Integrated Circuits

IEC Publication 191: Mechanical Standardization of Semiconductor Devices

## PART 2 - CLASSES OF THYRISTOR

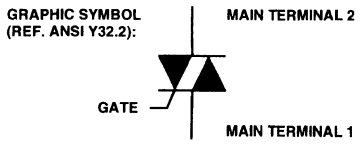
### Bidirectional Diode Thyristor

A two-terminal thyristor having substantially the same switching behaviour in the first and third quadrants of the thyristor voltage-current characteristic. (See Figures 2 and 4)



### Bidirectional Triode Thyristor

A n-gate or p-gate three-terminal thyristor having substantially the same switching behaviour in the first and third quadrants of the thyristor voltage-current characteristic. (See Figures 2 and 4)




### Diac

Originally a synonym for "bidirectional diode thyristor" derived from DIode Alternating Current semiconductor switch. This term now refers to a diode transistor which is used in thyristor trigger circuits.

### N-Gate Thyristor

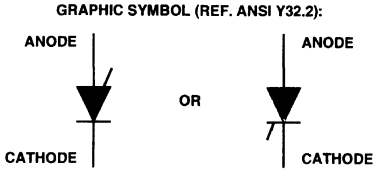
A unidirectional triode thyristor whose gate terminal is connected to the N-region nearest the anode and that is normally switched to the on-state by applying a negative signal to gate terminal with respect to the anode terminal. (See Figure 1 and reverse-blocking triode thyristor).

### P-Gate Thyristor

A unidirectional triode thyristor whose gate terminal is connected to the P-region nearest the cathode and that is normally switched to the on-state by applying a positive signal to gate terminal with respect to the cathode terminal. (See Figure 1 and reverse-blocking triode thyristor).

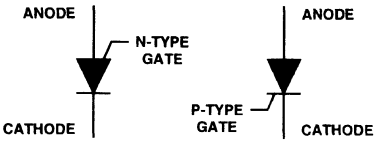
### Reverse-Blocking Diode Thyristor

A two-terminal thyristor that switches only for positive anode-to-cathode voltage and exhibits a reverse blocking state for negative anode-to-cathode voltages. (See Figure 1)




### Reverse-Blocking Triode Thyristor

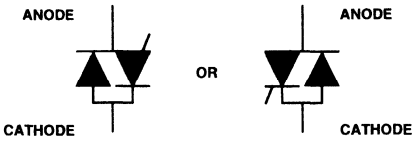
An n-gate or p-gate three-terminal thyristor that switches only for positive anode-to-cathode voltages and exhibits a reverse-blocking state for negative anode-to-cathode voltages. (See Figure 1)



### Reverse-Conducting Diode Thyristor

A two-terminal thyristor that switches only for positive anode-to-cathode voltages and conducts large currents at negative anode-to-cathode voltages comparable in magnitude to the on-state voltage.

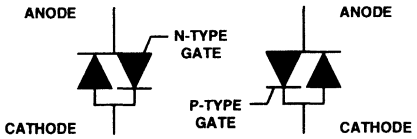
GRAPHIC SYMBOL (UNDER CONSIDERATION BY ANSI):




### Thyristor, Reverse-Conducting Triode

A n-gate or p-gate three-terminal thyristor that switches only for positive anode-to-cathode voltages and conducts large currents at negative anode-to-cathode voltages comparable in magnitude to the on-state voltage.

GRAPHIC SYMBOL (UNDER CONSIDERATION BY ANSI):




### SCR

A depreciated synonym for "reverse-blocking triode thyristor" derived from "Silicon Controlled Rectifier" or "Semiconductor Controlled Rectifier"

### Thyristor

A bistable semiconductor device that comprises three or more junctions and can be switched from the off-state to the on-state or vice versa. (Ref. IEC 147-0) (See Figures 1 through 5).

NOTE :1. A thyristor is a switch that can be switched on either for only one direction of the principal current (a unidirectional thyristor) or for both directions (a bidirectional thyristor).

NOTE :2. The term "thyristor" is used as a generic term to cover the whole range of PNPN-type switches. It may be used by itself for any member of the thyristor family when such use does not result in ambiguity or misunderstanding. In particular the abbreviated term "thyristor" is widely used for the reverse-blocking triode thyristor formally called "silicon controlled rectifier" or "semiconductor controlled rectifier" (SCR).

### Unidirectional Diode Thyristor

A two-terminal thyristor that can switch only when the anode voltage is positive. (See reverse-blocking diode thyristor and reverse-conducting diode thyristor.)

### Unidirectional Triode Thyristor

A three-terminal thyristor that can switch only when the anode voltage is positive. (See reverse-blocking triode thyristor and reverse-conducting triode thyristor.)

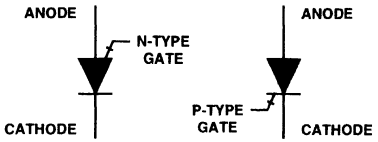
NOTE : In this definition, a second cathode or anode terminal for connecting to the control circuit is not counted.

### Triac

A synonym for "bidirectional triode thyristor" derived from Triode Alternating Current semiconductor switch.

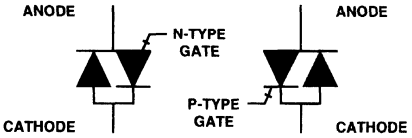
### Gate-Turn-Off (GTO) Reverse-Blocking Thyristor

A reverse-blocking triode thyristor that can be switched from the on state to the off state and vice versa by applying control signals of appropriate polarities to the gate terminal, with the ratio of triggering power to triggered power appreciably less than one. (See Figures 1 and 3)




### Gate-Turn-Off (GTO) Reverse-Conducting Thyristor

A reverse-conducting triode thyristor that can be switched from the on state to the off state and vice versa by applying control signals of appropriate polarities to the gate terminal, with the ratio of triggering power to triggered power appreciably less than one.




## PART 3 - PHYSICAL STRUCTURE NOMENCLATURE

### Anode

The electrode by which current enters the thyristor when the thyristor is in the on state with the gate open circuited. (Ref. RS-397).

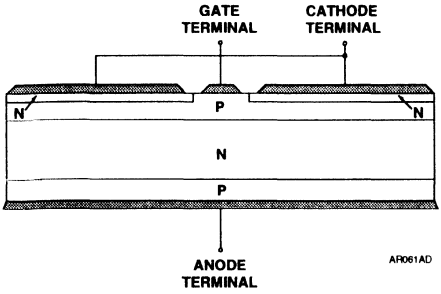
NOTE : This term does not apply to bidirectional thyristors.

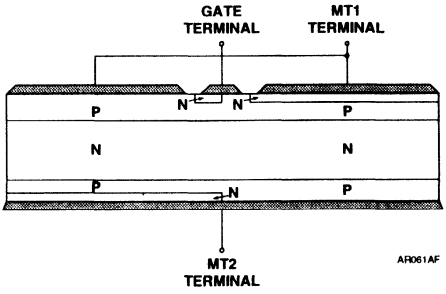
### Anode Terminal

The terminal that is connected to the anode.

NOTE :1 This term does not apply to bidirectional thyristors

NOTE :2 A second anode terminal may be provided for connecting to the control circuit of an n-gate thyristor.

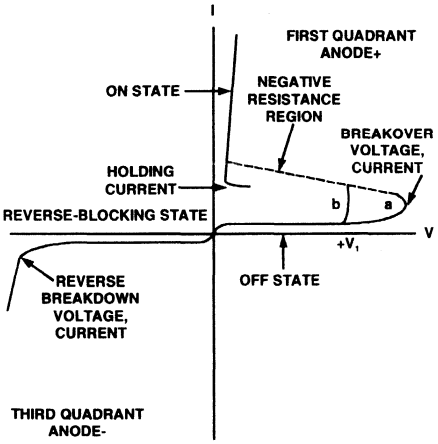


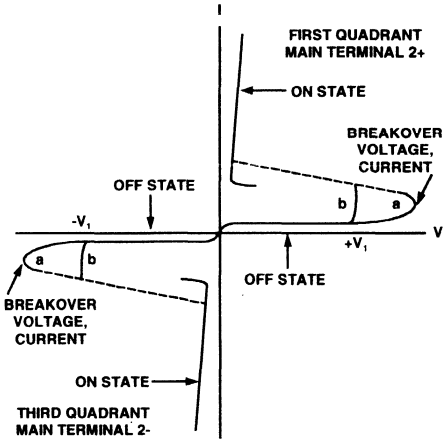




The gate electrode may be connected to the central N-type base region in some structures or omitted in the case of a diode thyristor.

**Figure 1. Schematic Representation of a (P-Type Gate) Reverse-Blocking Thyristor**

**Figure 2. Schematic Representation of a Bidirectional Triode Thyristor**




Curve "a" applies for zero gate current or a diode thyristor. Curve "b" applies for the case of gate trigger current applied when off-state voltage is $V_1$

**Figure 3. Principal Voltage-Current Characteristics of a Typical Reverse-Blocking Thyristor**

Curve "a" applies for zero gate current or a diode bidirectional thyristor. Curve "b" applies for the case of gate trigger current applied when off-state voltage is $\pm V_1$

**Figure 4. Principal Voltage-Current Characteristics of a Typical Bidirectional Thyristor**

### Cathode

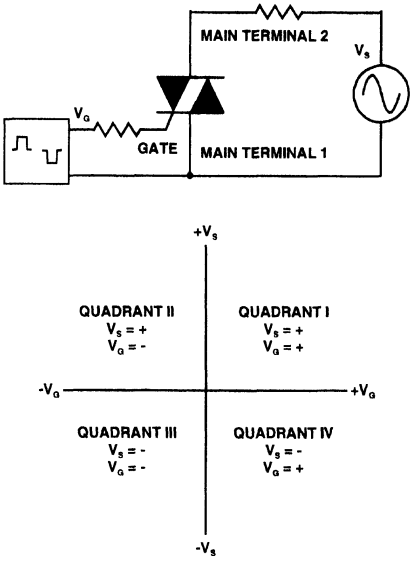
The electrode by which current leaves the thyristor when the thyristor is in the on state with the gate open circuited.

NOTE : This term does not apply to bidirectional thyristors.

### Cathode Terminal

The terminal that is connected to the cathode.

NOTE : This term does not apply to bidirectional thyristors.




The polarities of $V_S$ and $V_G$ are with respect to Main Terminal 1.

**Figure 5. Quadrant Definitions**

### Collector Junction

The junction across which the polarity of the voltage reverses when switching occurs. (Ref. RS-397) (See Figures 1,3 and 5).

### Electrode (Of A Semiconductor Device)

An element that performs one or more of the functions of emitting or collecting electrons or holes, or of controlling their movement by an electric field. (Ref. IEEE Std.100).

**Gate**

An electrode connected on one of the semiconductor regions for introducing control current. (Ref. RS-397).

**Gate Terminal**

A terminal that is connected to a gate.

**Junction (In A Semiconductor Device)**

A region of transition between semiconductor regions of different electrical properties (e.g. N-N+, P-N, P-P+ semiconductors), or between a metal and a semiconductor. (Ref. RS-282).

**Main Terminals**

The terminals through which the principal current flows. (Ref. RS-397).

**Main Terminal 1 (Of A Bidirectional Thyristor)**

The main terminal which is named "1" by the device manufacturer. (Ref. RS-397).

NOTE : This is normally the reference terminal for all voltages.

**Main Terminal 2 (Of A Bidirectional Thyristor)**

The main terminal which is named "2" by the device manufacturer. (Ref. RS-397).

**Terminal (Of A Semiconductor Device)**

An externally available point of connection. (Ref. IEC 147-0).

## PART 4 - ELECTRICAL CHARACTERISTIC AND RATING TERMS

**Absolute Maximum Rating**

A rating that establishes either a limiting capability or a limiting condition beyond which damage to the device may occur. (Ref. IEC Pub. 747-1)

**Anode-To-Cathode Voltage (Anode Voltage)**

The voltage between the anode terminal and the cathode terminal.

NOTE : It is called positive when the anode potential is more positive than the cathode potential, and called negative when the anode potential is less positive than the cathode potential.

**Anode-To-Cathode Voltage-Current Characteristic (Anode Characteristics)**

A function, usually represented graphically, relating the anode-to-cathode voltage to the principal current with gate current, where applicable, as a parameter. (Ref. RS-397).

NOTE : This term does not apply to bidirectional thyristors.

**Breakover Point**

In a quadrant in which switching may occur, the point for which the differential resistance is zero and the off-state voltage reaches a maximum value. (See Figures 2 and 4).

**Characteristic**

An inherent and measureable property of a device.

NOTE: Such a propertry can be expressed as a value for stated or recognised conditions. A characteristic may also be shown as a set of related values, usually in graphical form. (Ref. IEC Pub. 134)

**Negative-Differential-Resistance Region**

Any portion of the principal voltage-current characteristic in the switching quadrant(s) within which the differential resistance is negative. (Ref. RS-397) (See Figures 2 and 4).

**Off-Impedance**

The differential impedance between the terminals through which the principal current flows when the thyristor is in the off-state. (Ref. RS-397).

**Off-State**

The condition of the thyristor corresponding to the high-resistance, low-current portion of the principal voltage-current characteristic between the origin and the breakover point(s) in the switching quadrant(s). (Ref. RS-397).

**On-Impedance**

The differential impedance between the terminals through which the principal current flows when the thyristor is in the on-state.

**On-State**

The condition of a thyristor corresponding to the low-resistance, low-voltage portion of the principal voltage-current characteristic in the switching quadrant(s). (Ref. RS-397).

NOTE : In the case of reverse-conducting thyristors, this definition is applicable only for a positive anode-to-cathode voltage.

**Principal Voltage**

The voltage between the main terminals. (Ref. RS-397).

NOTE : 1. In the case of reverse-blocking and reverse-conducting thyristors, the principal voltage is called positive when the anode potential is more positive than the cathode potential, and called negative when the anode potential is less positive than the cathode potential.

NOTE : 2. For bidirectional thyristors, the principal voltage is called positive when the potential of main terminal 2 is more positive than the potential of main terminal 1.

**Principal Voltage-Current Characteristic (Principal Characteristic)**

A function, usually represented graphically, relating the principal voltage to the principal current with gate current, where applicable, as a parameter. (Ref. RS-397).

**Rating**

The nominal value of any parametric quantity assigned to define the operating conditions under which a device is expected to give satisfactory service. (Ref. IEC Pub. 747-1)

**Reverse-Blocking Impedance (Of A Reverse-Blocking Thyristor)**

The differential impedance between the two terminals through which the principal current flows when the thyristor is in the reverse-blocking state at a stated operating point. (Ref. RS-397).

**Reverse-Blocking State (Of A Reverse-Blocking Thyristor)**

The condition of a reverse-blocking thyristor corresponding to the portion of the anode-to-cathode voltage-current characteristic for which reverse currents are of lower magnitude than the reverse breakdown current. (Ref. RS-397) (See Figure 2).

## PART 5 - SYMBOLS, TERMS AND DEFINITIONS

| SYMBOL | TERM | DEFINITION |
|---|---|---|
| dv/dt | critical rate of rise of off-state voltage | The maximum rate of rise of principal voltage that will not cause switching from the off-state to the on-state. |
| dv/dt(c) | critical rate of rise of commutation voltage (of a bidirectional thyristor) | The maximum rate of rise of principal voltage that will not cause switching from the off-state to the on-state immediately following on-state current conduction in the opposite quadrant. |
| $I_{(BO)}$ | static breakover current | The principal current at the breakover point. |
| $i_{(BO)}$ | instantaneous breakover current | |
| $I_{(BR)}$ | static reverse breakdown current | The principal current at the reverse breakdown voltage. |
| $i_{(BR)}$ | instantaneous reverse breakdown current | |
| $I_{D(RMS)}$ | RMS off-state current | The principal current when the thyristor is in the off state. (Ref. EIA-397) |
| $I_D$ | static off-state current | |
| $I_{D(AV)}$ | average off-state current | |
| $i_D$ | instantaneous off-state current | |
| $I_{DM}$ | peak off-state current | |
| $I_{DOM}$ | off-state recovery current | The maximum value of the current that results from the application of the off-state voltage during the transition from an opposite-polarity off state, a reverse-blocking state, or a reverse-conducting state. |
| $I_{DRM}$ | repetitive peak off-state current | The maximum (peak) instantaneous value of the off-state current that results from the application of repetitive peak off-state voltage. |
| $I_G$ | static gate current | The current that results from the gate voltage. (Ref. EIA-397.) |
| $I_{G(AV)}$ | average gate current | |
| $i_G$ | instantaneous gate current | NOTES : 1. Positive gate current refers to conventional current entering the gate terminal. |
| $i_{GM}$ | peak gate current | 2. Negative gate current refers to conventional current leaving the gate terminal. |
| $I_{GD}$ | static gate non-trigger current | The maximum gate current that will not cause the thyristor to switch from the off-state to the on-state. |
| $i_{GD}$ | instantaneous gate non-trigger current | |
| $I_{GDM}$ | peak gate non-trigger current | |
| $I_{GQ}$ | static gate turn-off current | The minimum gate current required to switch a thyristor from the on-state to the off-state. |
| $i_{GQ}$ | instantaneous gate turn-off current | |
| $I_{GQM}$ | peak gate turn-off current | |
| $I_{GT}$ | static gate trigger current | The minimum gate current that will not cause the thyristor to switch from the off-state to the on-state. |
| $i_{GT}$ | instantaneous gate trigger current | |
| $I_{GTM}$ | peak gate trigger current | |
| $I_H$ | static holding current | The minimum principal current required to maintain the thyristor in the on-state. |
| $i_H$ | instantaneous holding current | |

| SYMBOL | TERM | DEFINITION |
|---|---|---|
| $I_L$ | static latching current | The minimum principal current required to maintain the thyristor in the on-state immediately after switching from the off-state to the on-state has occurred and the triggering signal has been removed. |
| $i_L$ | instantaneous latching current | |
| $I_{R(RMS)}$ | RMS reverse current | The current for negative anode-to-cathode voltage. |
| $I_R$ | static reverse current | |
| $I_{R(AV)}$ | average reverse current | |
| $i_R$ | instantaneous reverse current | |
| $I_{RM}$ | peak reverse current | |
| $I_{RQM}$ | reverse recovery current | The maximum current that results from a transition from an on-state current to a reverse-blocking state |
| $I_{RRM}$ | repetitive peak reverse current | The maximum (peak) instantaneous value of the reverse current that results from the application of repetitive peak reverse voltage. |
| $I_{RSM}$ | nonrepetitive peak reverse current (of a reverse-blocking thyristor) | The maximum (peak) surge reverse current having a specified waveform and a short, specified time interval. |
| $I_{T(RMS)}$ | RMS on-state current | The principal current when the thyristor is in the on-state. |
| $I_T$ | static on-state current | |
| $I_{T(AV)}$ | average on-state current | |
| $i_T$ | instantaneous on-state current | |
| $I_{TM}$ | peak on-state current | |
| $I_{TM(OV)}$ | overload peak on-state current | The maximum (peak) value of the on-state current having substantially the same waveshape as the normal on-state current and having a greater value than the normal on-state current. |
| $I_{TRM}$ | repetitive peak on-state current | The maximum (peak) value of the on-state current including all repetitive transient currents. |
| $I_{TSM}$ | surge (non-repetitive) peak on-state current | The maximum (peak) value of the surge on-state current having a specified waveform and a short specified time interval. |
| $P_G$ | static gate power dissipation | The power dissipation resulting from the respective gate currents. |
| $P_{G(AV)}$ | average gate power dissipation | |
| $p_G$ | instantaneous gate power dissipation | |
| $P_{GM}$ | peak gate power dissipation | |
| $P_T$ | static on-state power dissipation | The power dissipation resulting from the respective on-state currents through the main terminals or the anode and cathode terminals. |
| $P_{T(AV)}$ | average on-state power dissipation | |
| $p_T$ | instantaneous on-state power dissipation | |
| $P_{TM}$ | peak on-state power dissipation | |
| $R_\theta$ | thermal resistance | The temperature difference between two specified points or regions divided by the power dissipation under conditions of thermal equilibrium. |
| $R_{\theta JA}$ | thermal resistance, junction to ambient | |
| $R_{\theta JC}$ | thermal resistance, junction-to-case | |
| $R_{\theta CA}$ | thermal resistance, case-to-ambient | |

| SYMBOL | TERM | DEFINITION |
|---|---|---|
| $T_A$ | free-air temperature (ambient temperature) | The air temperature measured below a device, in an environment of substantially uniform temperature, cooled only by natural air convection and not materially affected by reflective and radiant surfaces. (Ref. MIL-S-19500). |
| $T_C$ | case temperature | The temperature measured at a specified location on the case of a device. (Ref. MIL-S-19500). |
| $T_J$ | virtual junction temperature (junction temperature) | A temperature representing the temperature of the junction(s) calculated on the basis of a simplified model of the thermal and electrical behaviour of the semiconductor device.<br>NOTE : This term (and its definition) is taken from IEC standards. It is particularly applicable to multi-junction semiconductors and is used in this publication to denote the temperature of the active semiconductor element when required in specifications and test methods. The term "junction temperature" is used interchangeably with the term "virtual junction temperature" in this publication. |
| $T_{stg}$ | storage temperature | The temperature at which the device, without any power applied, is stored. (Ref. MIL-S-19500). |
| $t_{gt}$ | gate-controlled turn-on time | The time interval between a specified point at the beginning of the gate pulse and the instant when the principal voltage (current) has dropped (risen) to a specified low (high) value during switching of a thyristor from the off-state to the on-state by a gate pulse. |
| $t_{gq}$ | gate-controlled turn-off time | The time interval between a specified point at the beginning of the gate pulse and the instant when the principal current has decreased to a specified value during switching from the on-state to the off-state by a gate pulse. |
| $t_q$ | circuit-commutated turn-off time | The time interval between the instant when the principal current has decreased to zero after external switching of the principal voltage circuit, and the instant when the thyristor is capable of supporting a specified principal voltage without turning on. |
| $V_{(BO)}$ | static breakover voltage | The principal voltage at the breakover point. |
| $v_{(BO)}$ | instantaneous breakover voltage | |
| $V_{(BR)}$ | static reverse breakdown voltage | The value of negative anode-to-cathode voltage at which the differential resistance between the anode and cathode terminals changes from a high value to a substantially lower value. |
| $v_{(BR)}$ | instantaneous reverse breakdown voltage | |
| $V_{D(RMS)}$ | RMS off-state voltage | The principal voltage when the thyristor is in the off-state. |
| $V_D$ | static off-state voltage | |
| $V_{D(AV)}$ | average off-state voltage | |
| $v_D$ | instantaneous off-state voltage | |
| $V_{DM}$ | peak off-state voltage | |

| SYMBOL | TERM | DEFINITION |
|---|---|---|
| $V_{DRM}$ | repetitive peak off-state voltage | The maximum instantaneous value of the off-state voltage that occurs across a thyristor, including all repetitive transient voltages, but excluding all non-repetitive transient voltages. |
| $V_{DSM}$ | non-repetitive peak off-state voltage | The maximum instantaneous value of any non-repetitive transient off-state voltage that occurs across the thyristor. |
| $V_{DWM}$ | working peak off-state voltage | The maximum instantaneous value of the off-state voltage that occurs across a thyristor, excluding all repetitive and non-repetitive transient voltages. |
| $V_G$ | static gate voltage | The voltage between a gate terminal and a specified main terminal.<br>NOTE : Gate voltage polarity is referenced to the specified main terminal. |
| $V_{G(AV)}$ | average gate voltage | |
| $v_G$ | instantaneous gate voltage | |
| $V_{GM}$ | peak gate voltage | |
| $V_{GD}$ | static gate non-trigger voltage | The maximum gate voltage that will not cause the thyristor to switch from the off-state to the on-state. |
| $v_{GD}$ | instantaneous gate non-trigger voltage | |
| $V_{GDM}$ | peak gate non-trigger voltage | |
| $V_{GQ}$ | static gate turn-off voltage | The gate voltage resulting from the gate turn-off current. |
| $v_{GQ}$ | instantaneous gate turn-off voltage | |
| $V_{GQM}$ | peak gate turn-off voltage | |
| $V_{GT}$ | static gate trigger voltage | The gate voltage resulting from the gate trigger current. |
| $v_{GT}$ | instantaneous gate trigger voltage | |
| $V_{GTM}$ | peak gate trigger voltage | |
| $V_{R(RMS)}$ | RMS reverse voltage | A negative anode-to-cathode voltage. |
| $V_R$ | static reverse voltage | |
| $V_{R(AV)}$ | average reverse voltage | |
| $v_R$ | instantaneous reverse voltage | |
| $V_{RM}$ | peak reverse voltage | |
| $V_{RRM}$ | repetitive peak reverse voltage | The maximum instantaneous value of the reverse voltage that occurs across the thyristor, including all repetitive transient voltages, but excluding all non-repetitive transient voltages. |
| $V_{RSM}$ | non-repetitive peak reverse voltage | The maximum instantaneous value of any non-repetitive transient reverse voltage that occurs across the thyristor. |
| $V_{RWM}$ | working peak reverse voltage | The maximum instantaneous value of the reverse voltage that occurs across a thyristor, excluding all repetitive and non-repetitive transient voltages. |
| $V_{T(RMS)}$ | RMS on-state voltage | The principal voltage when the thyristor is in the on-state. |
| $V_T$ | static on-state voltage | |
| $V_{T(AV)}$ | average on-state voltage | |
| $v_T$ | instantaneous on-state voltage | |
| $V_{TM}$ | peak on-state voltage | |
| $V_{T(MIN)}$ | static minimum on-state voltage | The minimum positive principal voltage for which the differential resistance is zero with the gate open-circuited. |

| SYMBOL | TERM | DEFINITION |
|---|---|---|
| $Z_\theta$ | transient thermal impedance | The change of temperature difference between two specified points or regions at the end of a time interval divided by the step-function change in power dissipation at the beginning of the same time interval causing the change of temperature difference. |
| $Z_{\theta JA}$ | transient thermal impedance, junction-to-ambient | |
| $Z_{\theta JC}$ | transient thermal impedance, junction-to-case | |

## PART 6 - BASIC DATA SHEET STRUCTURE

The front page of the data sheet begins with a list of key features such as trigger current sensitivity, current ratings and voltage ratings. In addition, the top view of the device is shown with the pinout provided. Next the absolute maximum ratings (e.g., withstand voltages, current levels and temperatures) applicable over the operating case temperature range are presented. If the device is used outside these values, it may be permanently destroyed or at least it would not function as intended.

The next section provides tables of characteristic information. The first table is for the electrical characteristics at 25°C case temperature (unless otherwise noted). These are presented as appropriate minimum, typical and maximum values. Next, a table of thermal characteristics is presented. Typically the maximum values of the junction to case and junction to ambient thermal resistance are given. For TO-220 packaged unidirectional thyristors (SCRs), there follows a table of switching times. Finally, if any specialized test circuits are used to measure device characteristic values, these circuits are specified under the heading of parametric measurement information.
At the end of the data sheet additional information on typical electrical characteristics and thermal information may be given. Details of the device package dimensions are given in the mechanical chapter.

# *Technical Specifications*

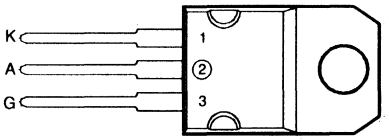
***SCR Devices***

TEXAS INSTRUMENTS

APRIL 1971 - REVISED JANUARY 1995

- **5 A Continuous On-State Current**
- **30 A Surge-Current**
- **Glass Passivated Wafer**
- **800 V Off-State Voltage**
- **Max $I_{GT}$ of 200 µA**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC1AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC106D | $V_{DRM}$ | 400 | V |
| | TIC106M | | 600 | |
| | TIC106S | | 700 | |
| | TIC106N | | 800 | |
| Repetitive peak reverse voltage | TIC106D | $V_{RRM}$ | 400 | V |
| | TIC106M | | 600 | |
| | TIC106S | | 700 | |
| | TIC106N | | 800 | |
| Continuous on-state current at (or below) 80°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 5 | A |
| Average on-state current (180° conduction angle) at (or below) 80°C case temperature (see Note 3) | | $I_{T(AV)}$ | 3.2 | A |
| Surge on-state current (see Note 4) | | $I_{TM}$ | 30 | A |
| Peak positive gate current (pulse width ≤ 300 µs) | | $I_{GM}$ | 0.2 | A |
| Peak gate power dissipation (pulse width ≤ 300 µs) | | $P_{GM}$ | 1.3 | W |
| Average gate power dissipation (see Note 5) | | $P_{G(AV)}$ | 0.3 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply when the gate-cathode resistance $R_{GK}$ = 1 kΩ.
2. These values apply for continuous dc operation with resistive load. Above 80°C derate linearly to zero at 110°C.
3. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 80°C derate linearly to zero at 110°C.
4. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
5. This value applies for a maximum averaging time of 20 ms.

**PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all the parameters.**

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TEXAS INSTRUMENTS

APRIL 1971 - REVISED JANUARY 1995

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $R_{GK}$ = 1 kΩ | $T_C$ = 110°C | | | 400 | μA |
| $I_{RRM}$ | Repetitive peak reverse current | $V_R$ = rated $V_{RRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | 1 | mA |
| $I_{GT}$ | Gate trigger current | $V_{AA}$ = 6 V | $R_L$ = 100 Ω | $t_{p(g)}$ ≥ 20 μs | | 60 | 200 | μA |
| $V_{GT}$ | Gate trigger voltage | $V_{AA}$ = 6 V<br>$t_{p(g)}$ ≥ 20 μs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | $T_C$ = -40°C | | | 1.2 | V |
| | | $V_{AA}$ = 6 V<br>$t_{p(g)}$ ≥ 20 μs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | | 0.4 | 0.6 | 1 | |
| | | $V_{AA}$ = 6 V<br>$t_{p(g)}$ ≥ 20 μs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | $T_C$ = 110°C | 0.2 | | | |
| $I_H$ | Holding current | $V_{AA}$ = 6 V<br>Initiating $I_T$ = 10 mA | $R_{GK}$ = 1 kΩ | $T_C$ = -40°C | | | 8 | mA |
| | | $V_{AA}$ = 6 V<br>Initiating $I_T$ = 10 mA | $R_{GK}$ = 1 kΩ | | | | 5 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = 5 A | (See Note 6) | | | | 1.7 | V |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = rated $V_D$ | $R_{GK}$ = 1 kΩ | $T_C$ = 110°C | | 10 | | V/μs |

NOTE 6: This parameter must be measured using pulse techniques, $t_p$ = 300 μs, duty cycle ≤ 2 %. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 3.5 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## resistive-load-switching characteristics at 25°C case temperature

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $t_{gt}$ | Gate-controlled turn-on time | $I_T$ = 5 A | $I_G$ = 10 mA | See Figure 1 | | 1.75 | | μs |
| $t_q$ | Circuit-commutated turn-off time | $I_T$ = 5 A<br>$I_{RM}$ = 8 A | $I_G$ = 10 mA | See Figure 2 | | 7.7 | | μs |

## PARAMETER MEASUREMENT INFORMATION

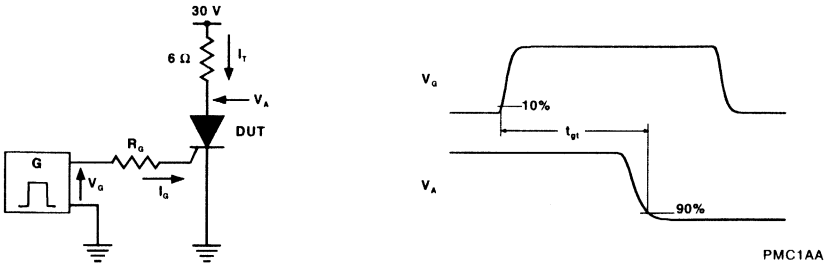
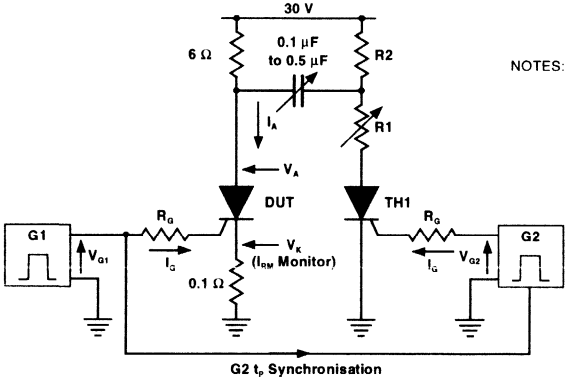



**Figure 1. Gate-controlled turn-on time**




NOTES: A. Resistor R1 is adjusted for the specified value of $I_{RM}$.
B. Resistor R2 value is $30/I_H$, where $I_H$ is the holding current value of thyristor TH1.
C. Thyristor TH1 is the same device type as the DUT.
D. Pulse Generators, G1 and G2, are synchronised to produce an on-state anode current waveform with the following characteristics:
$t_p$ = 50 µs to 300 µs
duty cycle = 1%
F. Pulse Generators, G1 and G2, have output pulse amplitude, $V_G$, of ≥ 20 V and duration of 10 µs to 20 µs.

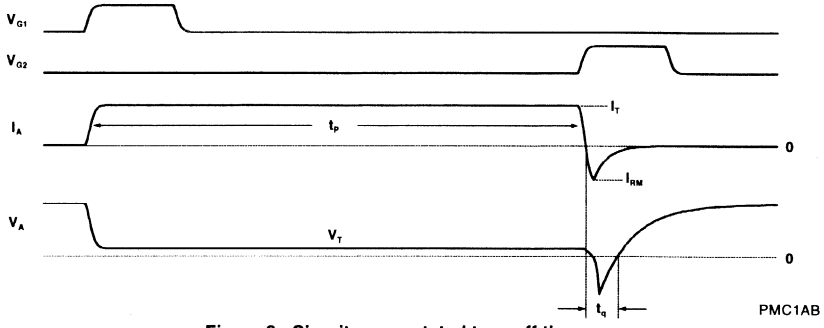



**Figure 2. Circuit-commutated turn-off time**

APRIL 1971 - REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

### AVERAGE ANODE FORWARD CURRENT DERATING CURVE

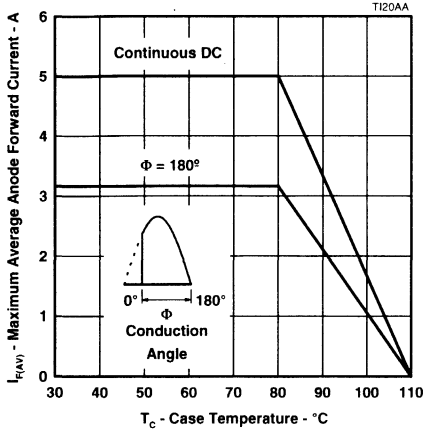



Figure 3.

### MAX CONTINUOUS ANODE POWER DISSIPATED vs CONTINUOUS ON-STATE CURRENT

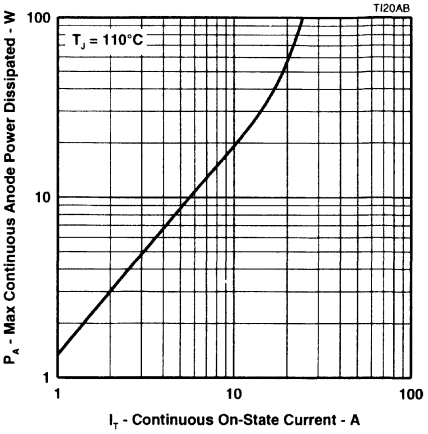



Figure 4.

### SURGE ON-STATE CURRENT vs CYCLES OF CURRENT DURATION

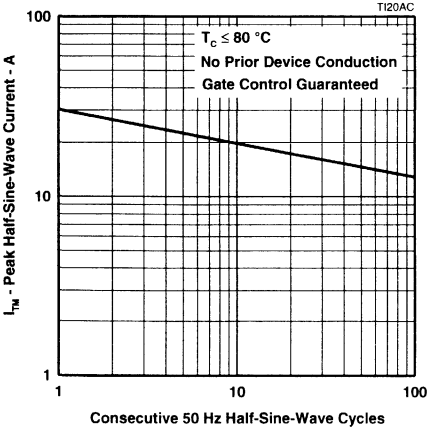



Figure 5.

### TRANSIENT THERMAL RESISTANCE vs CYCLES OF CURRENT DURATION

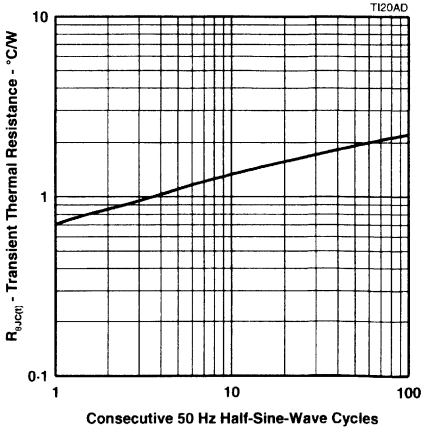



Figure 6.

## TYPICAL CHARACTERISTICS

### GATE TRIGGER CURRENT vs CASE TEMPERATURE

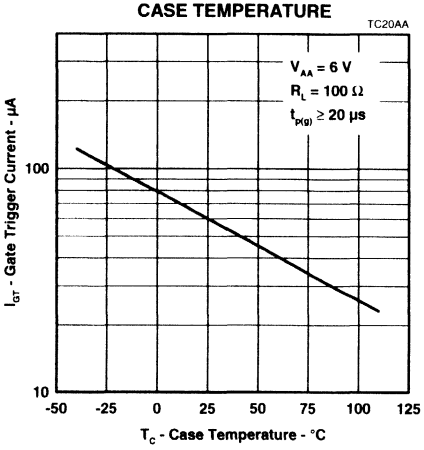



Figure 7.

### GATE TRIGGER VOLTAGE vs CASE TEMPERATURE

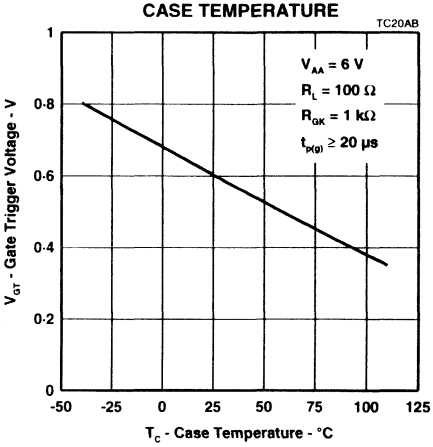



Figure 8.

### GATE FORWARD VOLTAGE vs GATE FORWARD CURRENT

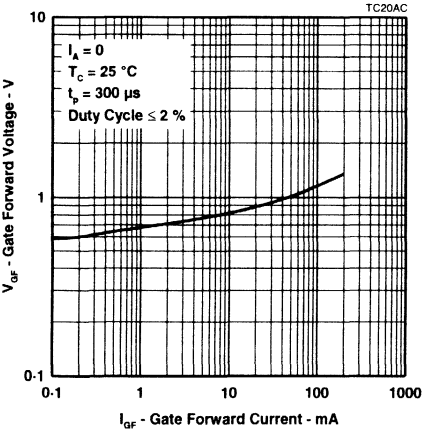



Figure 9.

### HOLDING CURRENT vs CASE TEMPERATURE

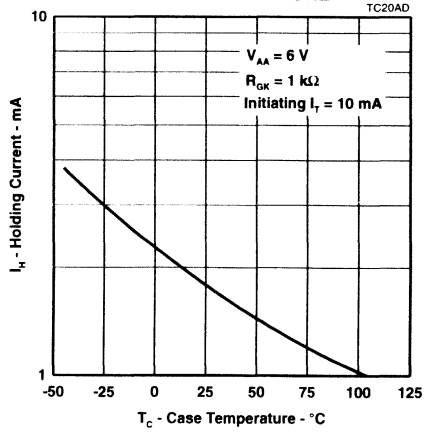



Figure 10.

## TYPICAL CHARACTERISTICS

### PEAK ON-STATE VOLTAGE vs PEAK ON-STATE CURRENT

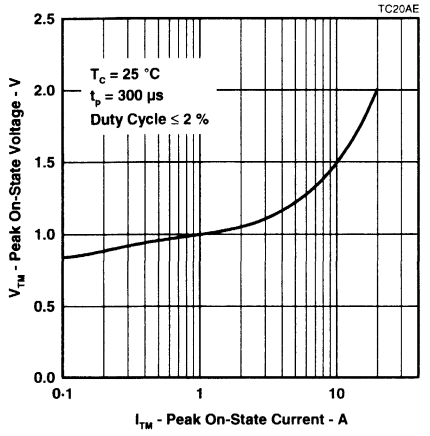



Figure 11.

### GATE-CONTROLLED TURN-ON TIME vs GATE CURRENT

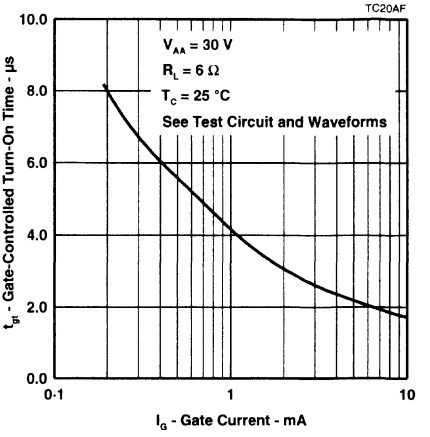



Figure 12.

### CIRCUIT-COMMUTATED TURN-OFF TIME vs CASE TEMPERATURE

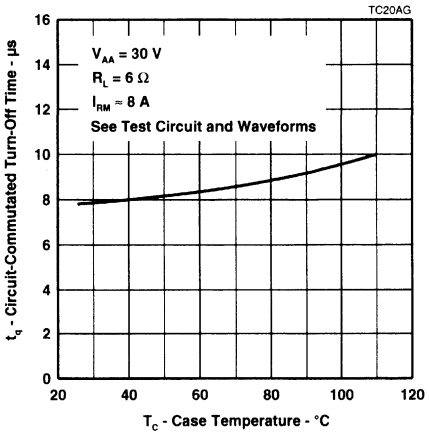
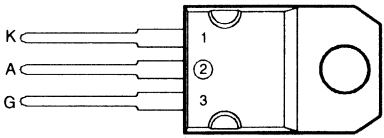



Figure 13.

JUNE 1982 - REVISED JANUARY 1995

- **5 A Continuous On-State Current**
- **20 A Surge-Current**
- **Glass Passivated Wafer**
- **800 V Off-State Voltage**
- **Max $I_{GT}$ of 1 mA**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC1AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC108D | $V_{DRM}$ | 400 | V |
| | TIC108M | | 600 | |
| | TIC108S | | 700 | |
| | TIC108N | | 800 | |
| Repetitive peak reverse voltage | TIC108D | $V_{RRM}$ | 400 | V |
| | TIC108M | | 600 | |
| | TIC108S | | 700 | |
| | TIC108N | | 800 | |
| Continuous on-state current at (or below) 80°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 5 | A |
| Average on-state current (180° conduction angle) at (or below) 80°C case temperature (see Note 3) | | $I_{T(AV)}$ | 3.2 | A |
| Surge on-state current (see Note 4) | | $I_{TM}$ | 20 | A |
| Peak positive gate current (pulse width ≤ 300 µs) | | $I_{GM}$ | 0.2 | A |
| Peak gate power dissipation (pulse width ≤ 300 µs) | | $P_{GM}$ | 1.3 | W |
| Average gate power dissipation (see Note 5) | | $P_{G(AV)}$ | 0.3 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply when the gate-cathode resistance $R_{GK}$ = 1 kΩ.
2. These values apply for continuous dc operation with resistive load. Above 80°C derate linearly to zero at 110°C.
3. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 80°C derate linearly to zero at 110°C.
4. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
5. This value applies for a maximum averaging time of 20 ms.

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## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $R_{GK}$ = 1 kΩ | $T_C$ = 110°C | | | 400 | μA |
| $I_{RRM}$ | Repetitive peak reverse current | $V_R$ = rated $V_{RRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | 1 | mA |
| $I_{GT}$ | Gate trigger current | $V_{AA}$ = 6 V | $R_L$ = 100 Ω | $t_{p(g)} \geq 20$ μs | 0.2 | | 1 | mA |
| $V_{GT}$ | Gate trigger voltage | $V_{AA}$ = 6 V<br>$t_{p(g)} \geq 20$ μs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | $T_C$ = - 40°C | | | 1.2 | V |
| | | $V_{AA}$ = 6 V<br>$t_{p(g)} \geq 20$ μs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | | 0.4 | 0.6 | 1 | |
| | | $V_{AA}$ = 6 V<br>$t_{p(g)} \geq 20$ μs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | $T_C$ = 110°C | 0.2 | | | |
| $I_H$ | Holding current | $V_{AA}$ = 6 V<br>Initiating $I_T$ = 20 mA | $R_{GK}$ = 1 kΩ | $T_C$ = - 40°C | | | 15 | mA |
| | | $V_{AA}$ = 6 V<br>Initiating $I_T$ = 20 mA | $R_{GK}$ = 1 kΩ | | | | 10 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = 5 A | (see Note 6) | | | | 1.7 | V |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = rated $V_D$ | $R_{GK}$ = 1 kΩ | $T_C$ = 110°C | | 80 | | V/μs |

NOTE 6: This parameter must be measured using pulse techniques, $t_p$ = 300 μs, duty cycle ≤ 2 %. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 3.5 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## resistive-load-switching characteristics at 25°C case temperature

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $t_{gt}$ | Gate-controlled turn-on time | $I_T$ = 5 A | $I_G$ = 10 mA | See Figure 1 | | 2.9 | | μs |
| $t_q$ | Circuit-commutated turn-off time | $I_T$ = 5 A | $I_{RM}$ = 8 A | See Figure 2 | | 13.3 | | μs |

## PARAMETER MEASUREMENT INFORMATION

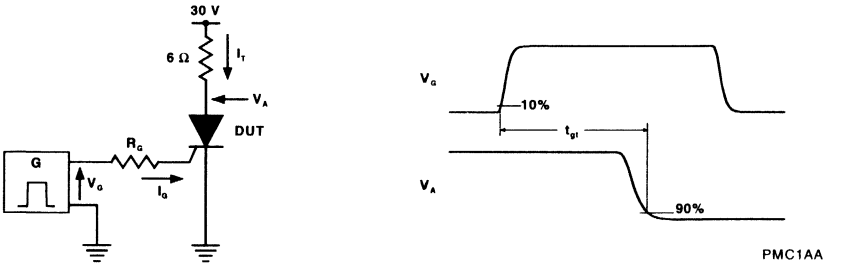
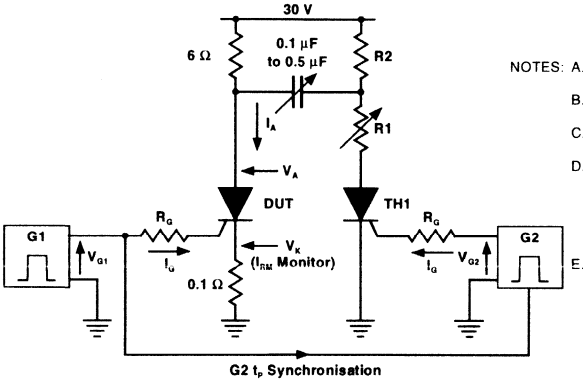



**Figure 1. Gate-controlled turn-on time**




NOTES: A. Resistor R1 is adjusted for the specified value of $I_{RM}$.
B. Resistor R2 value is $30/I_H$, where $I_H$ is the holding current value of thyristor TH1.
C. Thyristor TH1 is the same device type as the DUT.
D. Pulse Generators, G1 and G2, are synchronised to produce an on-state anode current waveform with the following characteristics:
$t_r$ = 50 µs to 300 µs
duty cycle = 1%
E. Pulse Generators, G1 and G2, have output pulse amplitude, $V_G$, of ≥ 20 V and duration of 10 µs to 20 µs.

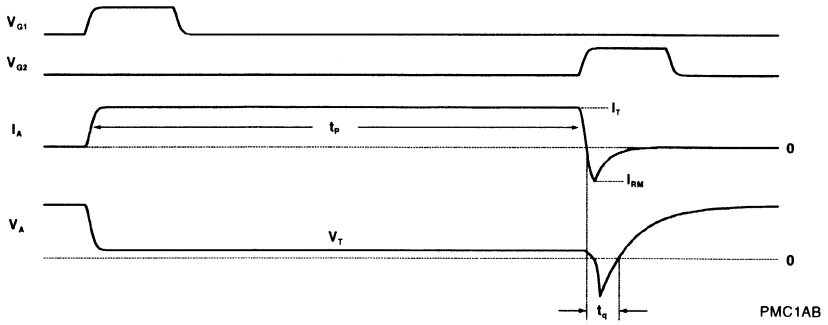



**Figure 2. Circuit-commutated turn-off time**

## TYPICAL CHARACTERISTICS

### AVERAGE ANODE FORWARD CURRENT DERATING CURVE

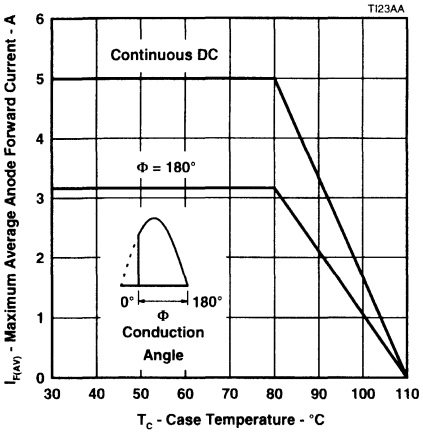



Figure 3.

### MAX CONTINUOUS ANODE POWER DISSIPATED vs CONTINUOUS ANODE FORWARD CURRENT

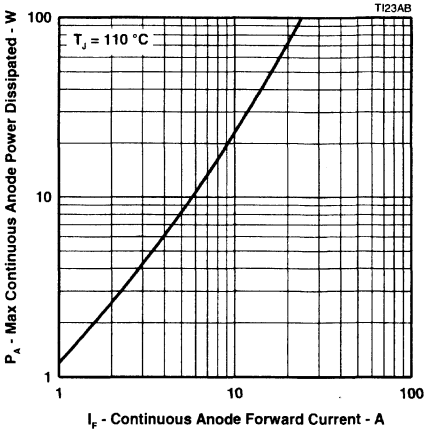



Figure 4.

### SURGE ON-STATE CURRENT vs CYCLES OF CURRENT DURATION

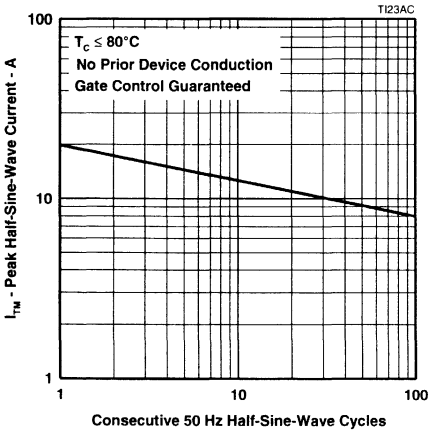



Figure 5.

### TRANSIENT THERMAL RESISTANCE vs CYCLES OF CURRENT DURATION

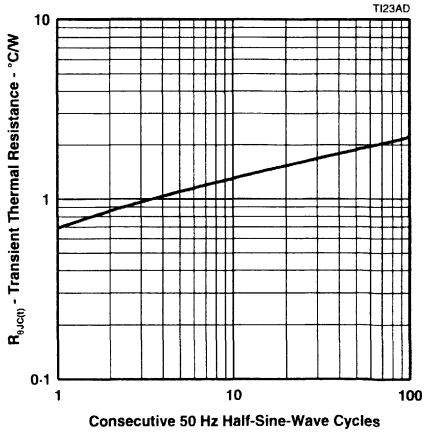



Figure 6.

JUNE 1982 - REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

GATE TRIGGER CURRENT
vs
CASE TEMPERATURE

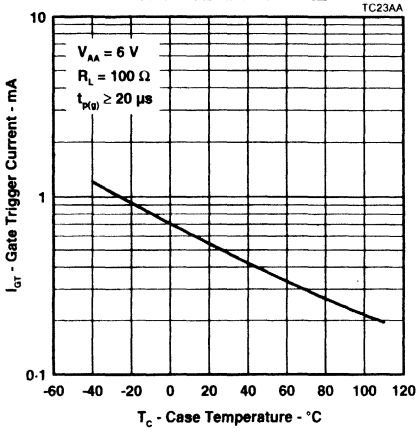



Figure 7.

GATE TRIGGER VOLTAGE
vs
CASE TEMPERATURE

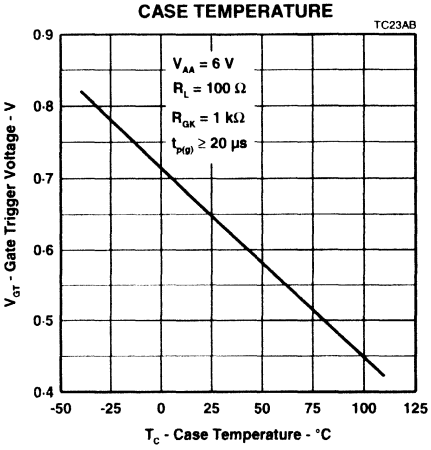



Figure 8.

GATE FORWARD VOLTAGE
vs
GATE FORWARD CURRENT

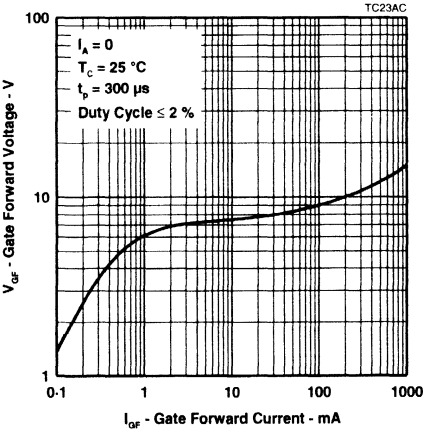



Figure 9.

HOLDING CURRENT
vs
CASE TEMPERATURE

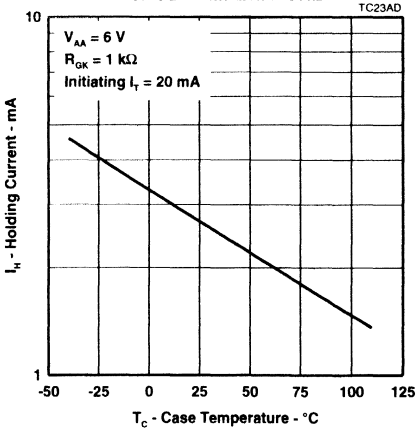



Figure 10.

## TYPICAL CHARACTERISTICS

### PEAK ON-STATE VOLTAGE vs PEAK ON-STATE CURRENT

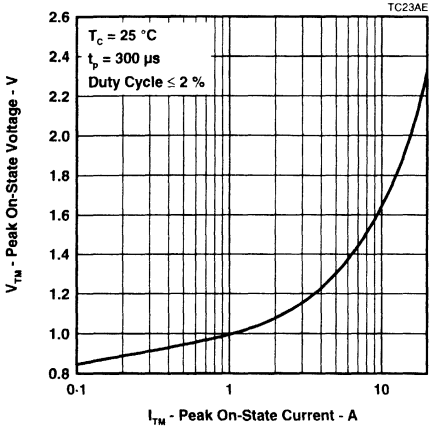



Figure 11.

### GATE-CONTROLLED TURN-ON TIME vs GATE CURRENT

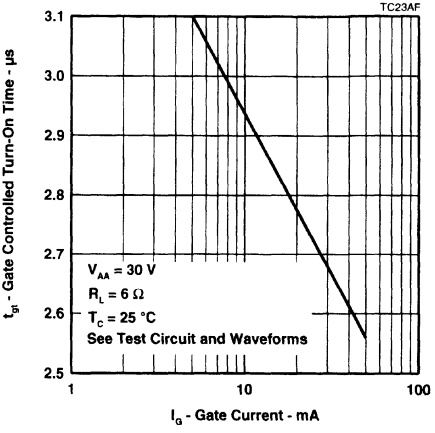



Figure 12.

### CIRCUIT-COMMUTATED TURN-OFF TIME vs CASE TEMPERATURE

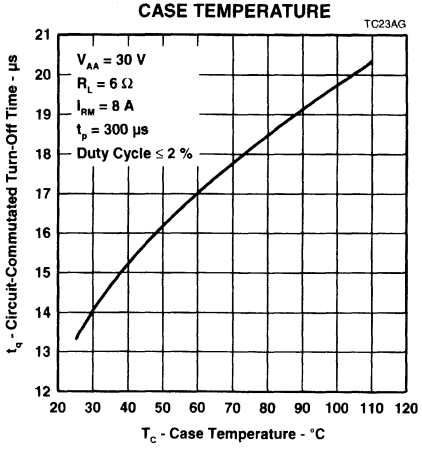
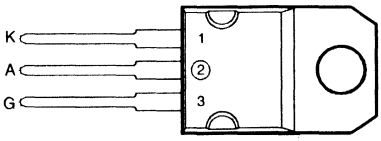



Figure 13.

APRIL 1971 - REVISED JANUARY 1995

- **8 A Continuous On-State Current**
- **80 A Surge-Current**
- **Glass Passivated Wafer**
- **800 V Off-State Voltage**
- **Max $I_{GT}$ of 20 mA**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC1AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC116D | $V_{DRM}$ | 400 | V |
| | TIC116M | | 600 | |
| | TIC116S | | 700 | |
| | TIC116N | | 800 | |
| Repetitive peak reverse voltage | TIC116D | $V_{RRM}$ | 400 | V |
| | TIC116M | | 600 | |
| | TIC116S | | 700 | |
| | TIC116N | | 800 | |
| Continuous on-state current at (or below) 80°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 8 | A |
| Average on-state current (180° conduction angle) at (or below) 80°C case temperature (see Note 3) | | $I_{T(AV)}$ | 5 | A |
| Surge on-state current (see Note 4) | | $I_{TM}$ | 80 | A |
| Peak positive gate current (pulse width ≤ 300 µs) | | $I_{GM}$ | 3 | A |
| Peak gate power dissipation (pulse width ≤ 300 µs) | | $P_{GM}$ | 5 | W |
| Average gate power dissipation (see Note 5) | | $P_{G(AV)}$ | 1 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply when the gate-cathode resistance $R_{GK}$ = 1 kΩ.
2. These values apply for continuous dc operation with resistive load. Above 80°C derate linearly to zero at 110°C.
3. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 80°C derate linearly to zero at 110°C.
4. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
5. This value applies for a maximum averaging time of 20 ms.

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## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $R_{GK}$ = 1 kΩ | $T_C$ = 110°C | | | 2 | mA |
| $I_{RRM}$ | Repetitive peak reverse current | $V_R$ = rated $V_{RRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | 2 | mA |
| $I_{GT}$ | Gate trigger current | $V_{AA}$ = 6 V | $R_L$ = 100 Ω | $t_{p(g)} \geq 20$ µs | | 5 | 20 | mA |
| $V_{GT}$ | Gate trigger voltage | $V_{AA}$ = 6 V<br>$t_{p(g)} \geq 20$ µs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | $T_C$ = - 40°C | | | 2.5 | V |
| | | $V_{AA}$ = 6 V<br>$t_{p(g)} \geq 20$ µs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | | | 0.8 | 1.5 | |
| | | $V_{AA}$ = 6 V<br>$t_{p(g)} \geq 20$ µs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | $T_C$ = 110°C | 0.2 | | | |
| $I_H$ | Holding current | $V_{AA}$ = 6 V<br>Initiating $I_T$ = 100 mA | $R_{GK}$ = 1 kΩ | $T_C$ = - 40°C | | | 70 | mA |
| | | $V_{AA}$ = 6 V<br>Initiating $I_T$ = 100 mA | $R_{GK}$ = 1 kΩ | | | | 40 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = 8 A | (see Note 6) | | | | 1.7 | V |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = rated $V_D$ | $I_G$ = 0 | $T_C$ = 110°C | | 100 | | V/µs |

NOTE 6: This parameter must be measured using pulse techniques, $t_p$ = 300 µs, duty cycle ≤ 2 %. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 3 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## resistive-load-switching characteristics at 25°C case temperature

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $t_{gt}$ | Gate-controlled turn-on time | $I_T$ = 5 A | $I_G$ = 200 mA | See Figure 1 | | 0.8 | | µs |
| $t_q$ | Circuit-commutated turn-off time | $I_T$ = 5 A | $I_{RM}$ = 10 A | See Figure 2 | | 11 | | µs |

## PARAMETER MEASUREMENT INFORMATION

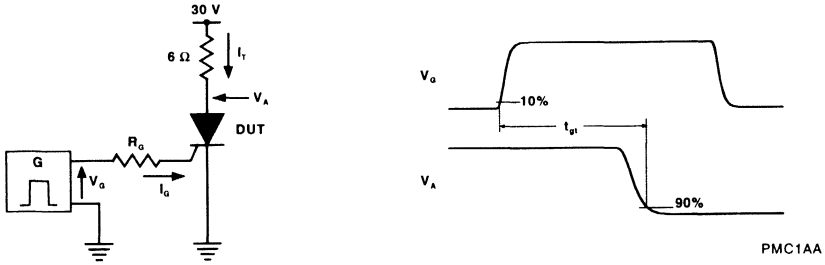
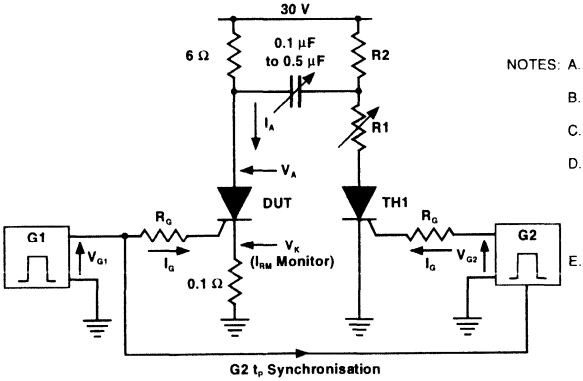



**Figure 1. Gate-controlled turn-on time**




NOTES: A. Resistor R1 is adjusted for the specified value of $I_{RM}$.
B. Resistor R2 value is $30/I_H$, where $I_H$ is the holding current value of thyristor TH1.
C. Thyristor TH1 is the same device type as the DUT.
D. Pulse Generators, G1 and G2, are synchronised to produce an on-state anode current waveform with the following characteristics:
$t_p$ = 50 µs to 300 µs
duty cycle = 1%
E. Pulse Generators, G1 and G2, have output pulse amplitude, $V_G$, of ≥ 20 V and duration of 10 µs to 20 µs.

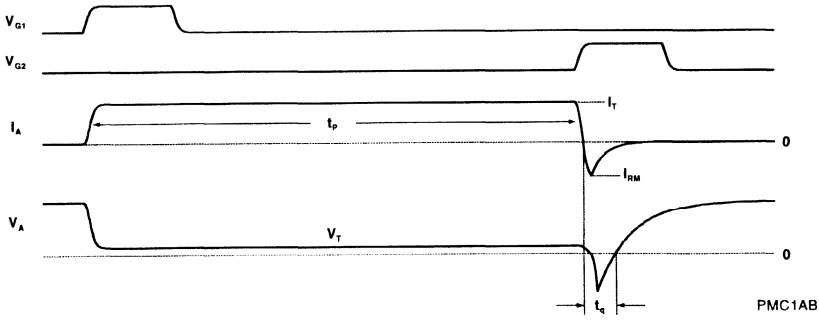



**Figure 2. Circuit-commutated turn-off time**

## TYPICAL CHARACTERISTICS

### AVERAGE ON-STATE CURRENT DERATING CURVE

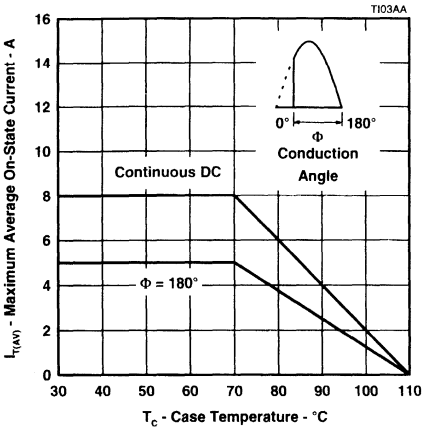



Figure 3.

### MAX CONTINUOUS ANODE POWER DISSIPATED VS CONTINUOUS ON-STATE CURRENT

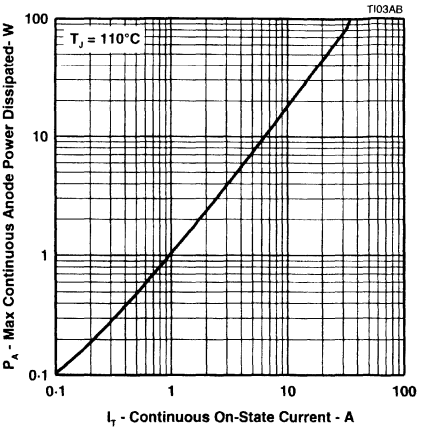



Figure 4.

### SURGE ON-STATE CURRENT VS CYCLES OF CURRENT DURATION

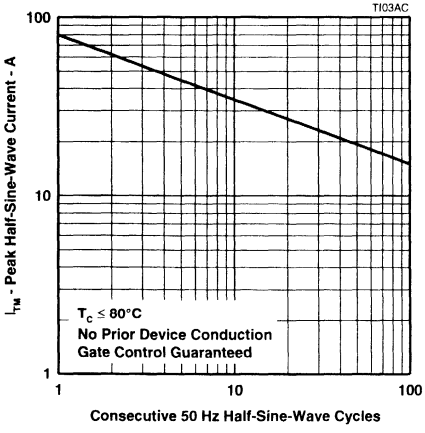



Figure 5.

### TRANSIENT THERMAL RESISTANCE VS CYCLES OF CURRENT DURATION

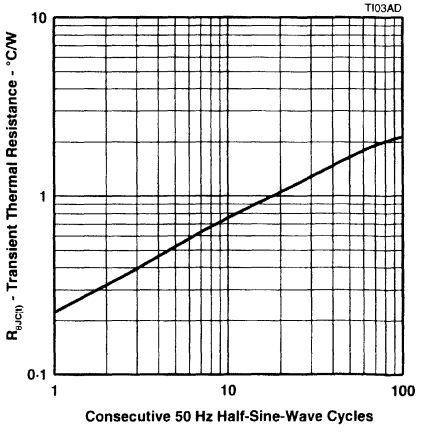



Figure 6.

## TYPICAL CHARACTERISTICS

GATE TRIGGER CURRENT
vs
CASE TEMPERATURE

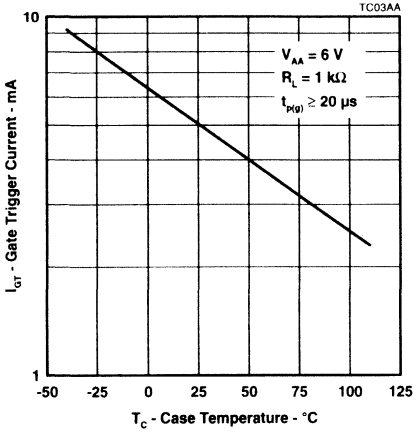



Figure 7.

GATE TRIGGER VOLTAGE
vs
CASE TEMPERATURE

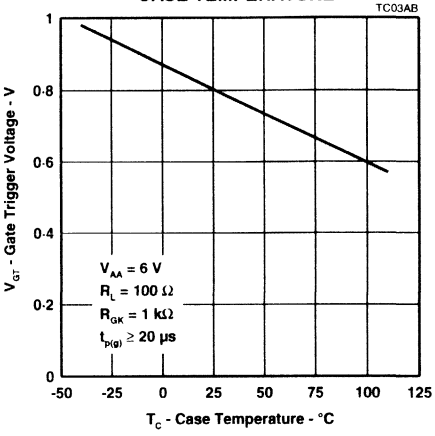



Figure 8.

GATE FORWARD VOLTAGE
vs
GATE FORWARD CURRENT

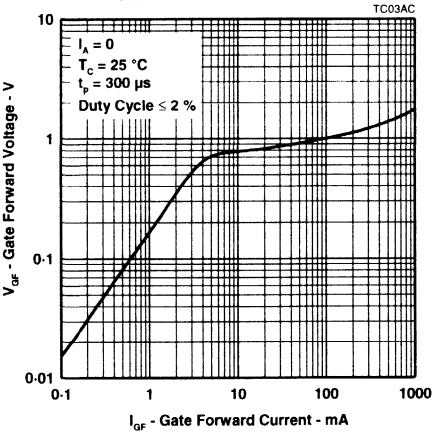



Figure 9.

HOLDING CURRENT
vs
CASE TEMPERATURE

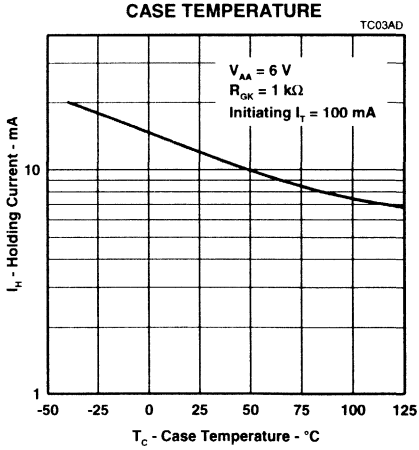



Figure 10.

## TYPICAL CHARACTERISTICS

PEAK ON-STATE VOLTAGE
vs
PEAK ON-STATE CURRENT

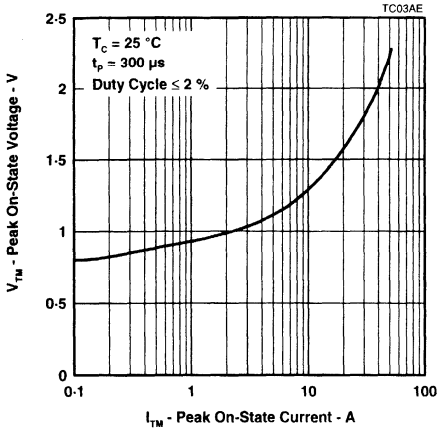



Figure 11.

GATE-CONTROLLED TURN-ON TIME
vs
GATE CURRENT

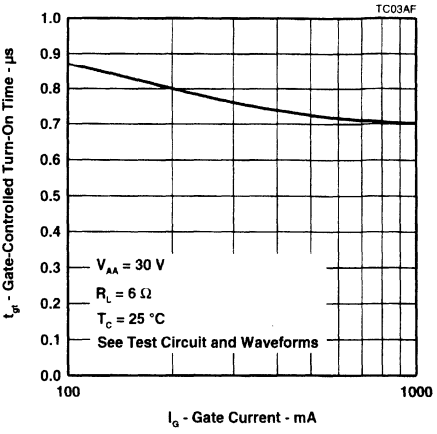



Figure 12.

CIRCUIT-COMMUTATED TURN-OFF TIME
vs
CASE TEMPERATURE

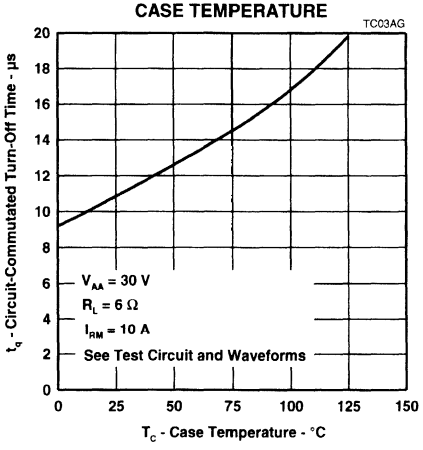
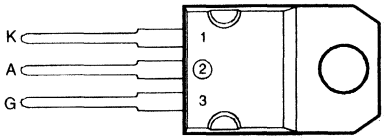



Figure 13.

APRIL 1971 - REVISED JANUARY 1995

- **12 A Continuous On-State Current**
- **100 A Surge-Current**
- **Glass Passivated Wafer**
- **800 V Off-State Voltage**
- **Max $I_{GT}$ of 20 mA**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC1AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC126D | $V_{DRM}$ | 400 | V |
| | TIC126M | | 600 | |
| | TIC126S | | 700 | |
| | TIC126N | | 800 | |
| Repetitive peak reverse voltage | TIC126D | $V_{RRM}$ | 400 | V |
| | TIC126M | | 600 | |
| | TIC126S | | 700 | |
| | TIC126N | | 800 | |
| Continuous on-state current at (or below) 80°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 12 | A |
| Average on-state current (180° conduction angle) at (or below) 80°C case temperature (see Note 3) | | $I_{T(AV)}$ | 7.5 | A |
| Surge on-state current (see Note 4) | | $I_{TM}$ | 100 | A |
| Peak positive gate current (pulse width ≤ 300 µs) | | $I_{GM}$ | 3 | A |
| Peak gate power dissipation (pulse width ≤ 300 µs) | | $P_{GM}$ | 5 | W |
| Average gate power dissipation (see Note 5) | | $P_{G(AV)}$ | 1 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply when the gate-cathode resistance $R_{GK}$ = 1 kΩ.
2. These values apply for continuous dc operation with resistive load. Above 80°C derate linearly to zero at 110°C.
3. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 80°C derate linearly to zero at 110°C.
4. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
5. This value applies for a maximum averaging time of 20 ms.

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APRIL 1971 - REVISED JANUARY 1995

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $R_{GK}$ = 1 kΩ | $T_C$ = 110°C | | | 2 | mA |
| $I_{RRM}$ | Repetitive peak reverse current | $V_R$ = rated $V_{RRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | 2 | mA |
| $I_{GT}$ | Gate trigger current | $V_{AA}$ = 6 V | $R_L$ = 100 Ω | $t_{p(g)} \geq 20$ µs | | 5 | 20 | mA |
| $V_{GT}$ | Gate trigger voltage | $V_{AA}$ = 6 V<br>$t_{p(g)} \geq 20$ µs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | $T_C$ = - 40°C | | | 2.5 | V |
| | | $V_{AA}$ = 6 V<br>$t_{p(g)} \geq 20$ µs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | | | 0.8 | 1.5 | |
| | | $V_{AA}$ = 6 V<br>$t_{p(g)} \geq 20$ µs | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | $T_C$ = 110°C | 0.2 | | | |
| $I_H$ | Holding current | $V_{AA}$ = 6 V<br>Initiating $I_T$ = 100 mA | $R_{GK}$ = 1 kΩ | $T_C$ = - 40°C | | | 70 | mA |
| | | $V_{AA}$ = 6 V<br>Initiating $I_T$ = 100 mA | $R_{GK}$ = 1 kΩ | | | | 40 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = 12 A | (see Note 6) | | | | 1.4 | V |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = rated $V_D$ | $I_G$ = 0 | $T_C$ = 110°C | | 100 | | V/µs |

NOTE 6: This parameter must be measured using pulse techniques, $t_p$ = 300 µs, duty cycle ≤ 2 %. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 2.4 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## resistive-load-switching characteristics at 25°C case temperature

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $t_{gt}$ | Gate-controlled turn-on time | $I_T$ = 5 A | $I_G$ = 200 mA | See Figure 1 | | 0.8 | | µs |
| $t_q$ | Circuit-commutated turn-off time | $I_T$ = 5 A | $I_{RM}$ = 10 A | See Figure 2 | | 11 | | µs |

## PARAMETER MEASUREMENT INFORMATION

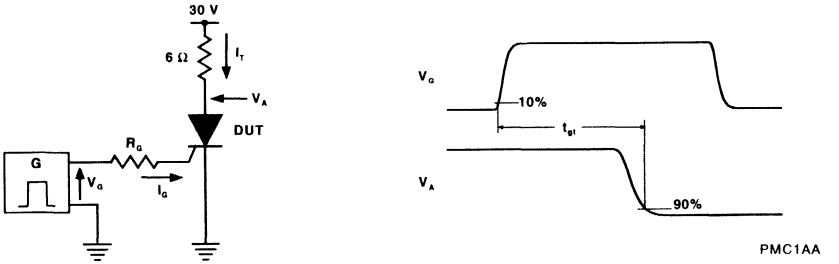
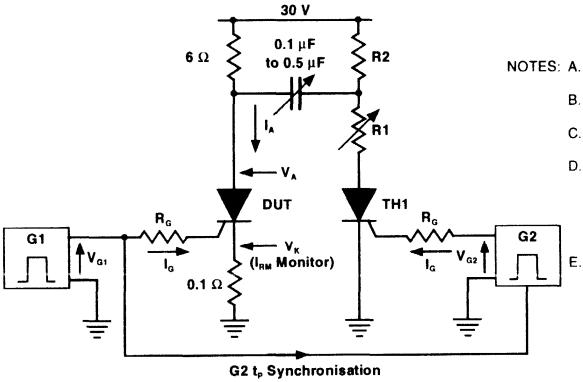



**Figure 1. Gate-controlled turn-on time**




NOTES: A. Resistor R1 is adjusted for the specified value of $I_{RM}$.
B. Resistor R2 value is $30/I_H$, where $I_H$ is the holding current value of thyristor TH1.
C. Thyristor TH1 is the same device type as the DUT.
D. Pulse Generators, G1 and G2, are synchronised to produce an on-state anode current waveform with the following characteristics:
$t_p$ = 50 µs to 300 µs
duty cycle = 1%
E. Pulse Generators, G1 and G2, have output pulse amplitude, $V_G$, of ≥ 20 V and duration of 10 µs to 20 µs.

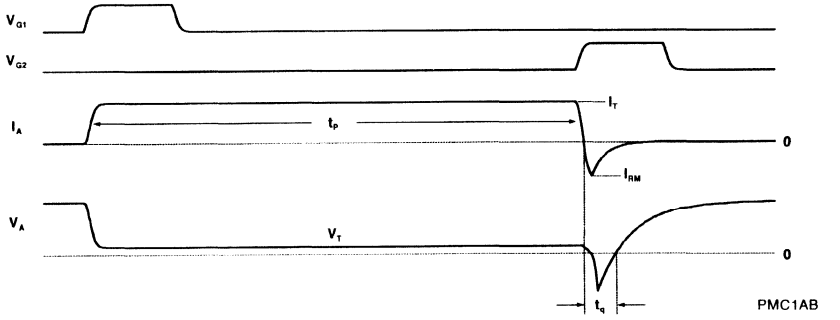



**Figure 2. Circuit-commutated turn-off time**

## TYPICAL CHARACTERISTICS

### AVERAGE ON-STATE CURRENT DERATING CURVE

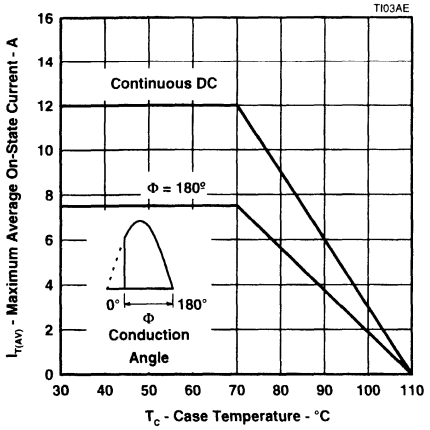



Figure 3.

### MAX CONTINUOUS ANODE POWER DISSIPATED vs CONTINUOUS ON-STATE CURRENT

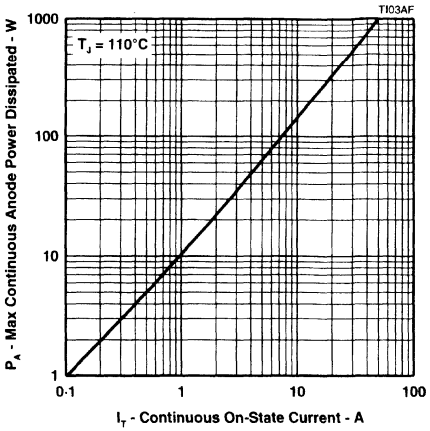



Figure 4.

### SURGE ON-STATE CURRENT vs CYCLES OF CURRENT DURATION

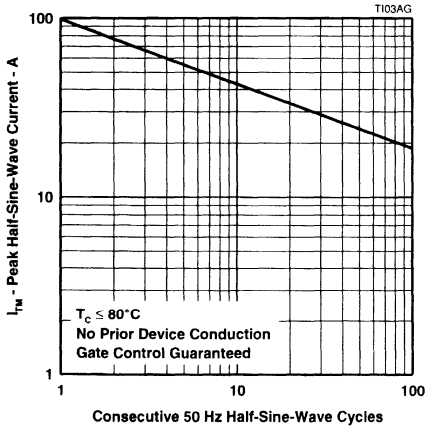



Figure 5.

### TRANSIENT THERMAL RESISTANCE vs CYCLES OF CURRENT DURATION

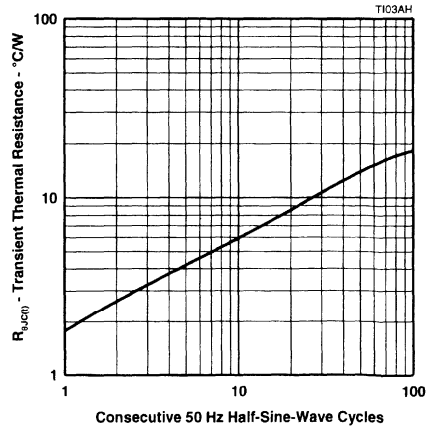



Figure 6.

APRIL 1971 - REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs CASE TEMPERATURE**

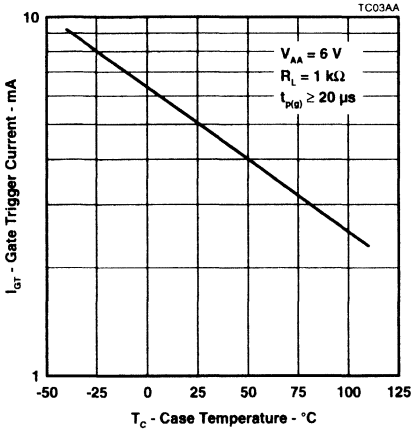



Figure 7.

**GATE TRIGGER VOLTAGE vs CASE TEMPERATURE**

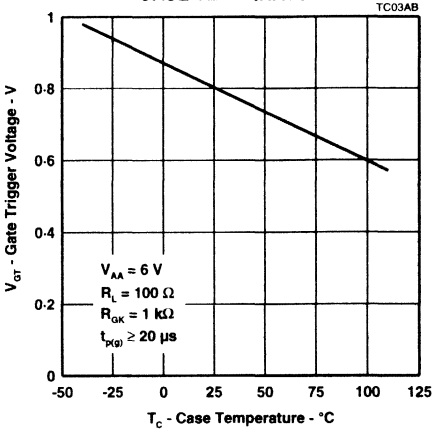



Figure 8.

**GATE FORWARD VOLTAGE vs GATE FORWARD CURRENT**

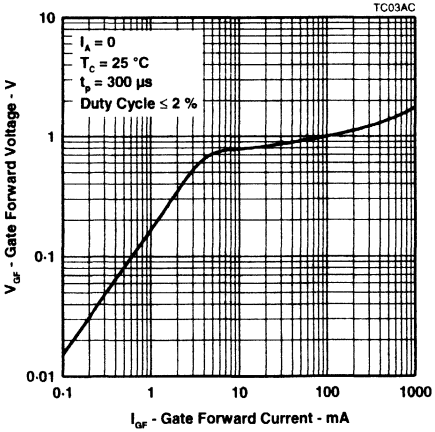



Figure 9.

**HOLDING CURRENT vs CASE TEMPERATURE**

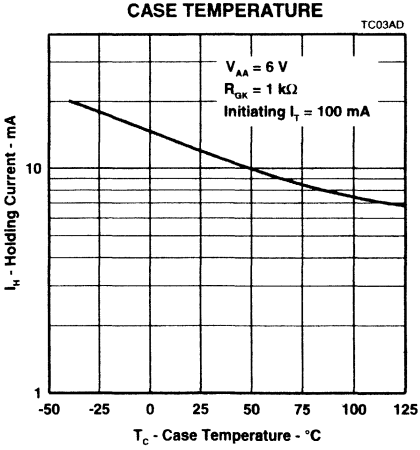



Figure 10.

## TYPICAL CHARACTERISTICS

PEAK ON-STATE VOLTAGE
vs
PEAK ON-STATE CURRENT

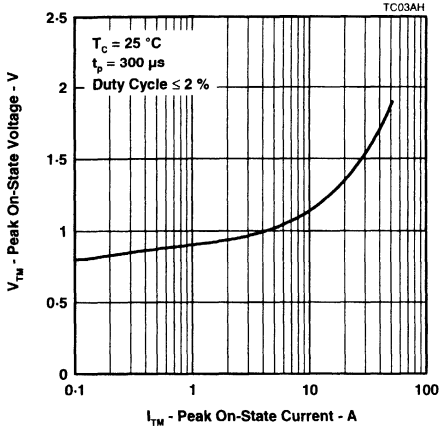



Figure 11.

GATE-CONTROLLED TURN-ON TIME
vs
GATE CURRENT

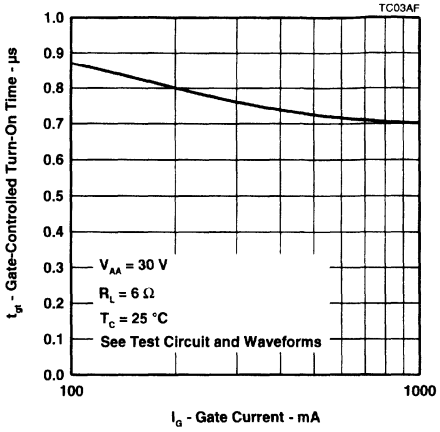



Figure 12.

CIRCUIT-COMMUTATED TURN-OFF TIME
vs
CASE TEMPERATURE

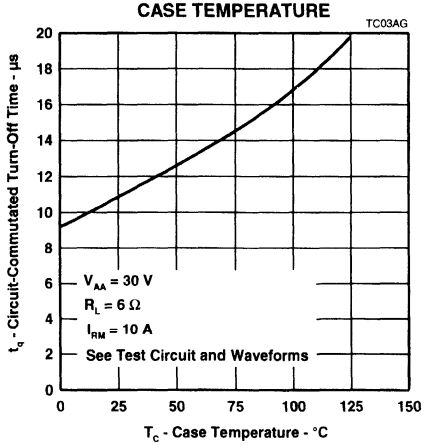


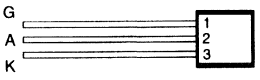

Figure 13.

MARCH 1988 - REVISED JANUARY 1995

- **2 A Continuous On-State Current**
- **15 A Surge-Current**
- **600 V Off-State Voltage**
- **Max $I_{GT}$ of 200 µA**

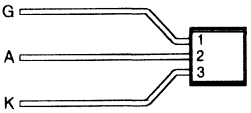
| PACKAGE | PACKING | PART # SUFFIX |
|---|---|---|
| LP | Bulk | (None) |
| LP with formed leads | Tape and Reel | R |

**LP PACKAGE**
**(TOP VIEW)**




MDC1AA

**LP PACKAGE**
**WITH FORMED LEADS**
**(TOP VIEW)**




MDC1AB

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TICP106D<br>TICP106M | $V_{DRM}$ | 400<br>600 | V |
| Repetitive peak reverse voltage | TICP106D<br>TICP106M | $V_{RRM}$ | 400<br>600 | V |
| Continuous on-state current at (or below) 85°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 2 | A |
| Surge on-state current (see Note 3) | | $I_{TSM}$ | 15 | A |
| Peak positive gate current (pulse width ≤ 300 µs) | | $I_{GM}$ | 0.2 | A |
| Average gate power dissipation (see Note 4) | | $P_{G(AV)}$ | 0.3 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 3.2 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply when the gate-cathode resistance $R_{GK}$ = 1 kΩ.
2. These values apply for continuous dc operation with resistive load. Above 85°C derate linearly to zero at 110°C.
3. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
4. This value applies for a maximum averaging time of 20 ms.

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## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $R_{GK}$ = 1 kΩ | | | | 20 | μA |
| $I_{RRM}$ | Repetitive peak reverse current | $V_R$ = rated $V_{RRM}$ | $I_G$ = 0 | | | | 200 | μA |
| $I_{GT}$ | Gate trigger current | $V_{AA}$ = 6 V | $R_L$ = 100 Ω | $t_{p(g)} \geq 20$ μs | | 60 | 200 | μA |
| $V_{GT}$ | Gate trigger voltage | $V_{AA}$ = 6 V | $R_L$ = 100 Ω<br>$R_{GK}$ = 1 kΩ | $t_{p(g)} \geq 20$ μs | 0.4 | | 1 | V |
| $I_H$ | Holding current | $V_{AA}$ = 6 V | $R_{GK}$ = 1 kΩ | Initiating $I_T$ = 10 mA | | | 5 | mA |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = 1 A | (see Note 5) | | | | 1.5 | V |

NOTE 5: This parameter must be measured using pulse techniques, $t_p$ = 1 ms, duty cycle ≤ 2 %. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

# *Technical Specifications*

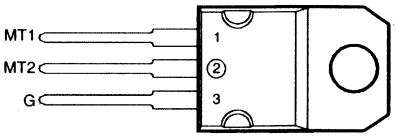
***Triac Devices***

TEXAS INSTRUMENTS

JANUARY 1977 · REVISED JANUARY 1995

- **Sensitive Gate Triacs**
- **2.5 A RMS**
- **400 V to 800 V**
- **Max $I_{GT}$ of 5 mA (Quadrant 1)**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC201D | $V_{DRM}$ | 400 | V |
| | TIC201M | | 600 | |
| | TIC201S | | 700 | |
| | TIC201N | | 800 | |
| Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 2.5 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 12 | A |
| Peak on-state surge current half-sine-wave (see Note 4) | | $I_{TSM}$ | 14 | A |
| Peak gate current | | $I_{GM}$ | ±0.2 | A |
| Peak gate power dissipation at (or below) 85°C case temperature (pulse width ≤ 200 µs) | | $P_{GM}$ | 1.3 | W |
| Average gate power dissipation at (or below) 85°C case temperature (see Note 5) | | $P_{G(AV)}$ | 0.3 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 100 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
5. This value applies for a maximum averaging time of 20 ms.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±1 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | 5 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | -8 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | -10 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | 25 | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.9 | 2.5 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -1.2 | -2.5 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -1.2 | -2.5 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 1.2 | | |

† All voltages are with respect to Main Terminal 1.

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±3.5 A | $I_G$ = 50 mA | (see Note 6) | | | ±1.9 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | | 30 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = - 100 mA | | | -30 | |
| $I_L$ | Latching current | $V_{supply}$ = +12 V† | (see Note 7) | | | | 40 | mA |
| | | $V_{supply}$ = -12 V† | | | | | -40 | |
| dv/dt | Critical rate of rise of off-state voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | ±50 | | V/μs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_{TRM}$ = ±3.5 A | $T_C$ = 85°C | ±2 | | | V/μs |

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 μs, $t_r$ = ≤ 15 ns, f = 1 kHz.

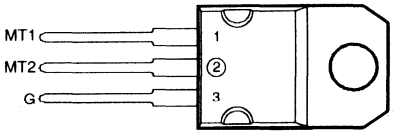
## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 10 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

DECEMBER 1971 - REVISED JANUARY 1995

- **Sensitive Gate Triacs**
- **4 A RMS**
- **400 V to 800 V**
- **Max $I_{GT}$ of 5 mA (Quadrants 1 - 3)**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC206D | $V_{DRM}$ | 400 | V |
| | TIC206M | | 600 | |
| | TIC206S | | 700 | |
| | TIC206N | | 800 | |
| Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 4 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 25 | A |
| Peak on-state surge current half-sine-wave (see Note 4) | | $I_{TSM}$ | 30 | A |
| Peak gate current | | $I_{GM}$ | ±0.2 | A |
| Peak gate power dissipation at (or below) 85°C case temperature (pulse width ≤ 200 µs) | | $P_{GM}$ | 1.3 | W |
| Average gate power dissipation at (or below) 85°C case temperature (see Note 5) | | $P_{G(AV)}$ | 0.3 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 160 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
5. This value applies for a maximum averaging time of 20 ms.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±1 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.5 | 5 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -1.5 | -5 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -2 | -5 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 3.6 | 10 | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.7 | 2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.7 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.8 | 2 | |

† All voltages are with respect to Main Terminal 1.

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±4.2 A | $I_G$ = 50 mA | (see Note 6) | | ±1.3 | ±2.2 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | 2 | 15 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | -4 | -15 | |
| $I_L$ | Latching current | $V_{supply}$ = +12 V† | (see Note 7) | | | | 30 | mA |
| | | $V_{supply}$ = -12 V† | | | | | -30 | |
| dv/dt | Critical rate of rise of off-state voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | ±50 | | V/µs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_{TRM}$ = ±4.2 A | $T_C$ = 85°C | ±1 | ±1.3 | ±2.5 | V/µs |

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 µs, $t_r$ = ≤ 15 ns, f = 1 kHz.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 7.8 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs TEMPERATURE**

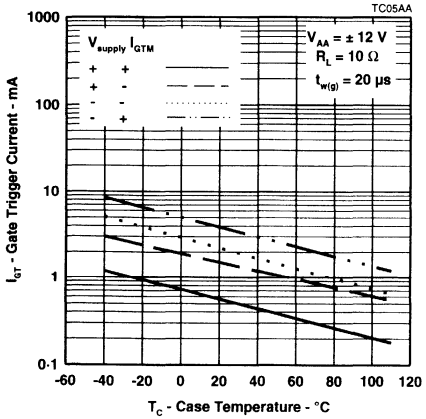



Figure 1.

**GATE TRIGGER VOLTAGE vs TEMPERATURE**

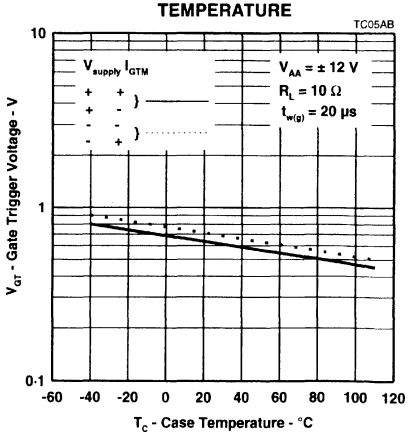



Figure 2.

TEXAS INSTRUMENTS

DECEMBER 1971 REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

HOLDING CURRENT
vs
CASE TEMPERATURE

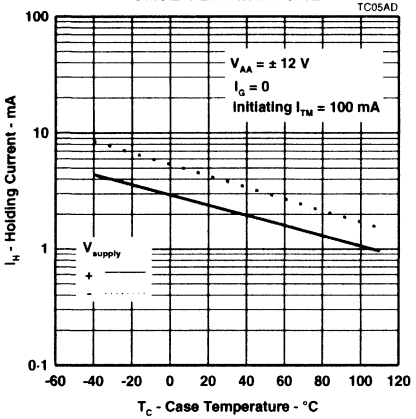



Figure 3.

GATE FORWARD VOLTAGE
vs
GATE FORWARD CURRENT

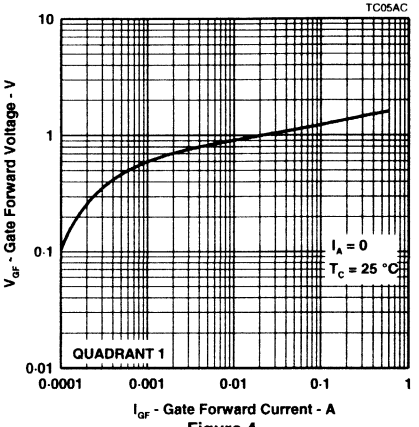



Figure 4.

LATCHING CURRENT
vs
CASE TEMPERATURE

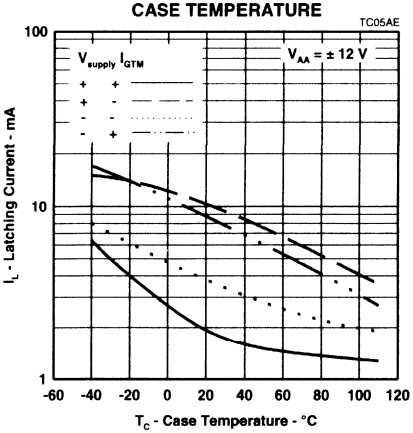
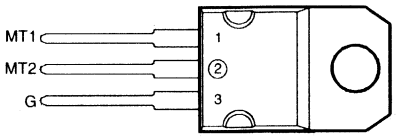



Figure 5.

DECEMBER 1971 - REVISED JANUARY 1995

- **Sensitive Gate Triacs**
- **400 V to 800 V**
- **Max $I_{GT}$ of 5 mA (Quadrants 1 - 3)**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC216D | $V_{DRM}$ | 400 | V |
| | TIC216M | | 600 | |
| | TIC216S | | 700 | |
| | TIC216N | | 800 | |
| Full-cycle RMS on-state current at (or below) 70°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 6 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 60 | A |
| Peak on-state surge current half-sine-wave (see Note 4) | | $I_{TSM}$ | 70 | A |
| Peak gate current | | $I_{GM}$ | 1 | A |
| Peak gate power dissipation at (or below) 85°C case temperature (pulse width ≤ 200 µs) | | $P_{GM}$ | 2.2 | W |
| Average gate power dissipation at (or below) 85°C case temperature (see Note 5) | | $P_{G(AV)}$ | 0.9 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 70°C derate linearly to 110°C case temperature at the rate of 150 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
5. This value applies for a maximum averaging time of 20 ms.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±2 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | 5 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | -5 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | -5 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | 10 | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | 2.2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | -2.2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | -2.2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | 3 | |

† All voltages are with respect to Main Terminal 1.

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±8.4 A | $I_G$ = 50 mA | (see Note 6) | | | ±1.7 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | | 30 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | | -30 | |
| $I_L$ | Latching current | $V_{supply}$ = +12 V† | (see Note 7) | | | 50 | | mA |
| | | $V_{supply}$ = -12 V† | | | | -20 | | |
| dv/dt | Critical rate of rise of off-state voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | ±50 | | V/μs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_{TRM}$ = ±8.4 A | $T_C$ = 70°C | ±5 | | | V/μs |

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 μs, $t_r$ = ≤ 15 ns, f = 1 kHz.

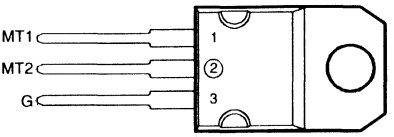
## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 2.5 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

JULY 1975 - REVISED JANUARY 1995

- **Sensitive Gate Triacs**
- **8 A RMS, 70 A Peak**
- **400 V to 800 V**
- **Max $I_{GT}$ of 5 mA (Quadrant 1)**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC225D | $V_{DRM}$ | 400 | V |
| | TIC225M | | 600 | |
| | TIC225S | | 700 | |
| | TIC225N | | 800 | |
| Full-cycle RMS on-state current at (or below) 70°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 8 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 70 | A |
| Peak on-state surge current half-sine-wave (see Note 4) | | $I_{TSM}$ | 80 | A |
| Peak gate current | | $I_{GM}$ | 1 | A |
| Peak gate power dissipation at (or below) 85°C case temperature (pulse width ≤ 200 µs) | | $P_{GM}$ | 2.2 | W |
| Average gate power dissipation at (or below) 85°C case temperature (see Note 5) | | $P_{G(AV)}$ | 0.9 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 70°C derate linearly to 110°C case temperature at the rate of 200 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
5. This value applies for a maximum averaging time of 20 ms.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±2 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.8 | 5 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -4.5 | -20 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -3.5 | -10 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 11.7 | 30 | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.7 | 2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.7 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.9 | 2 | |

† All voltages are with respect to Main Terminal 1.

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±12 A | $I_G$ = 50 mA | (see Note 6) | | ±1.6 | ±2.1 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | 3 | 20 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | -4.7 | -20 | |
| $I_L$ | Latching current | $V_{supply}$ = +12 V† | (see Note 7) | | | | 30 | mA |
| | | $V_{supply}$ = -12 V† | | | | | -30 | |
| dv/dt | Critical rate of rise of off-state voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | ±50 | | V/µs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_{TRM}$ = ±12 A | $T_C$ = 70°C | ±1 | ±1.5 | ±4.5 | V/µs |

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 µs, $t_r$ = ≤ 15 ns, f = 1 kHz

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 2.5 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs CASE TEMPERATURE**

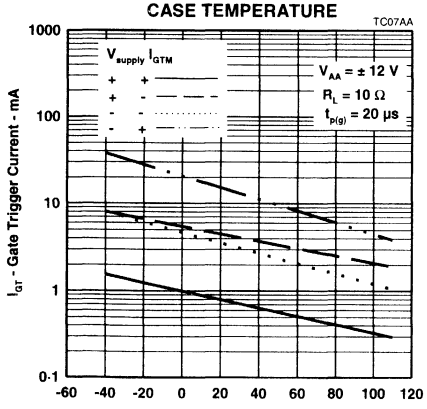



Figure 1.

**GATE TRIGGER VOLTAGE vs CASE TEMPERATURE**

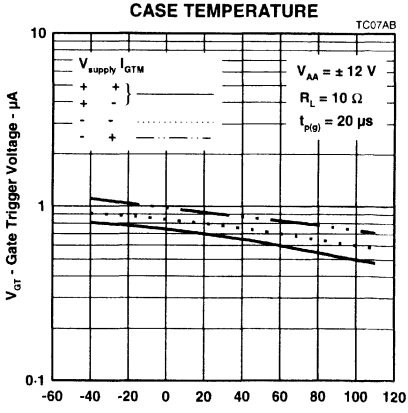



Figure 2.

TEXAS INSTRUMENTS

## TYPICAL CHARACTERISTICS

HOLDING CURRENT
vs
CASE TEMPERATURE

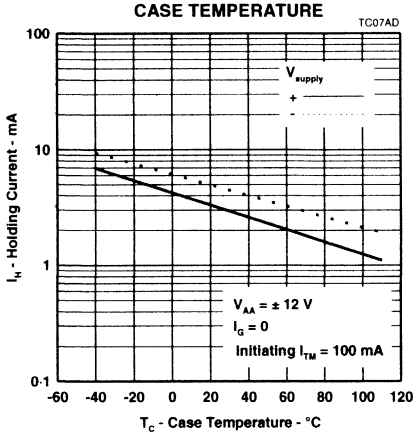



Figure 3.

GATE FORWARD VOLTAGE
vs
GATE FORWARD CURRENT

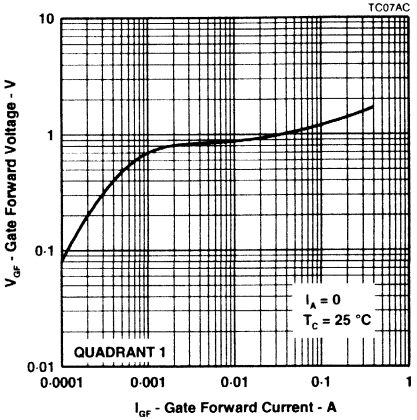



Figure 4.

LATCHING CURRENT
vs
CASE TEMPERATURE

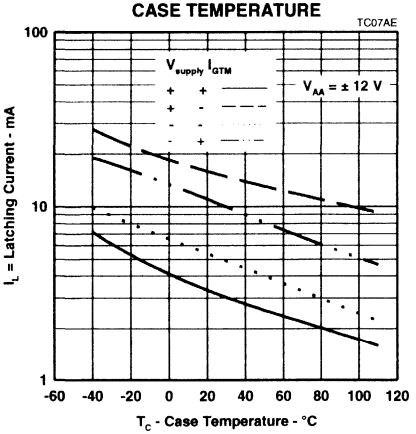



Figure 5.

SURGE ON-STATE CURRENT
vs
CYCLES OF CURRENT DURATION

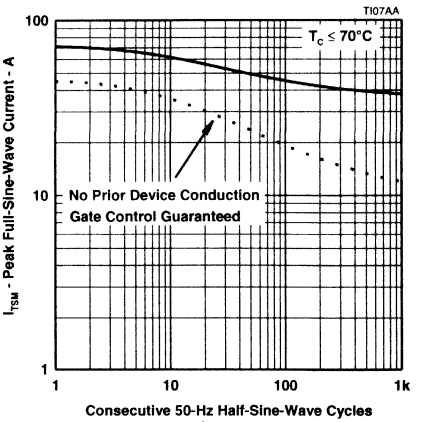



Figure 6.

## TYPICAL CHARACTERISTICS

**MAXIMUM RMS ON-STATE CURRENT**
**vs**
**CASE TEMPERATURE**

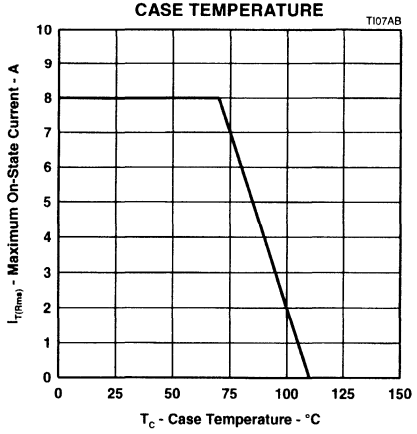
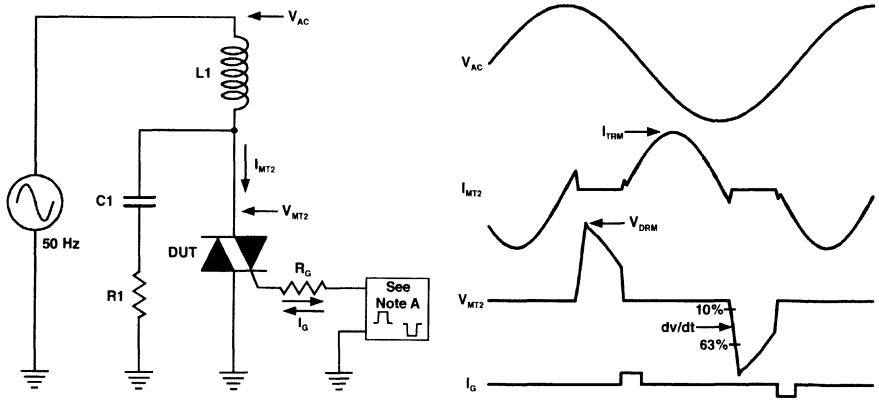



**Figure 7.**

## PARAMETER MEASUREMENT INFORMATION




NOTE A: The gate-current pulse is furnished by a trigger circuit which presents essentially an open circuit between pulses. The pulse is timed so that the off-state-voltage duration is approximately 800 μs.

PMC2AA

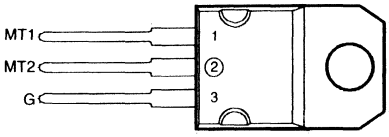
**Figure 8.**

TEXAS INSTRUMENTS

APRIL 1971 - REVISED JANUARY 1995

- **8 A RMS, 70 A Peak**
- **400 V to 800 V**
- **Max $I_{GT}$ of 50 mA (Quadrants 1 - 3)**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC226D | $V_{DRM}$ | 400 | V |
| | TIC226M | | 600 | |
| | TIC226S | | 700 | |
| | TIC226N | | 800 | |
| Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 8 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 70 | A |
| Peak on-state surge current half-sine-wave (see Note 4) | | $I_{TSM}$ | 80 | A |
| Peak gate current | | $I_{GM}$ | 1 | A |
| Peak gate power dissipation at (or below) 85°C case temperature (pulse width ≤ 200 µs) | | $P_{GM}$ | 2.2 | W |
| Average gate power dissipation at (or below) 85°C case temperature (see Note 5) | | $P_{G(AV)}$ | 0.9 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 320 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
5. This value applies for a maximum averaging time of 20 ms.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±2 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 2 | 50 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -12 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -9 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 20 | | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.7 | 2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.9 | 2 | |

† All voltages are with respect to Main Terminal 1.

**PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all the parameters.**

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±12 A | $I_G$ = 50 mA | (see Note 6) | | ±1.6 | ±2.1 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | 5 | 30 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | -9 | -30 | |
| $I_L$ | Latching current | $V_{supply}$ = +12 V† | (see Note 7) | | | | 50 | mA |
| | | $V_{supply}$ = -12 V† | | | | | -50 | |
| dv/dt | Critical rate of rise of off-state voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | ±100 | | V/µs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_{DRM}$ = Rated $V_{DRM}$ | $I_{TRM}$ = ±12 A | $T_C$ = 85°C | ±5 | | | V/µs |

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 µs, $t_r$ = ≤ 15 ns, f = 1 kHz.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 1.8 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT**
**vs**
**CASE TEMPERATURE**

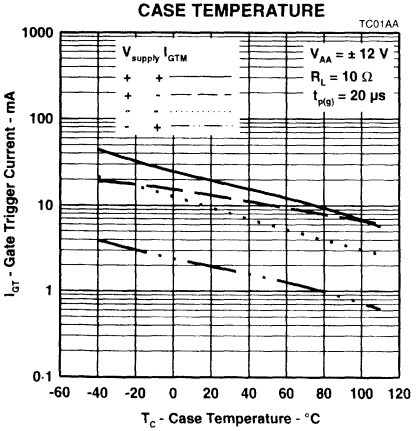



Figure 1.

**GATE TRIGGER VOLTAGE**
**vs**
**CASE TEMPERATURE**

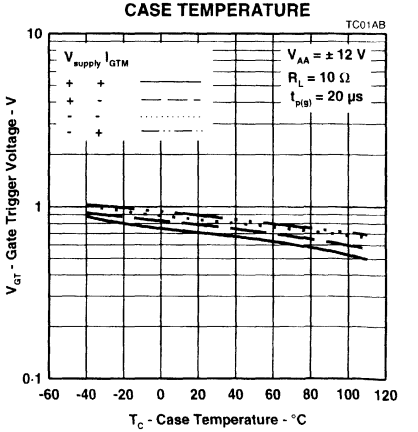



Figure 2.

TEXAS INSTRUMENTS

APRIL 1971 - REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

### HOLDING CURRENT vs CASE TEMPERATURE

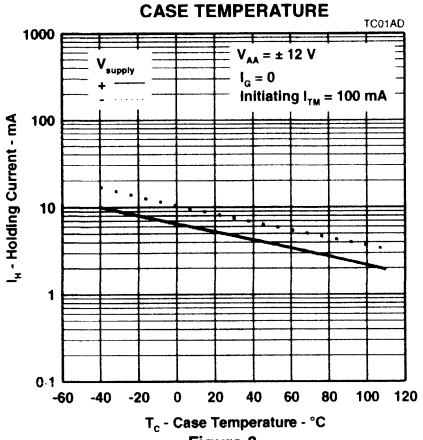



Figure 3.

### GATE FORWARD VOLTAGE vs GATE FORWARD CURRENT

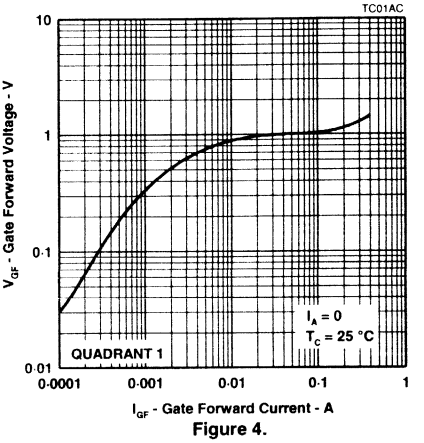



Figure 4.

### LATCHING CURRENT vs CASE TEMPERATURE

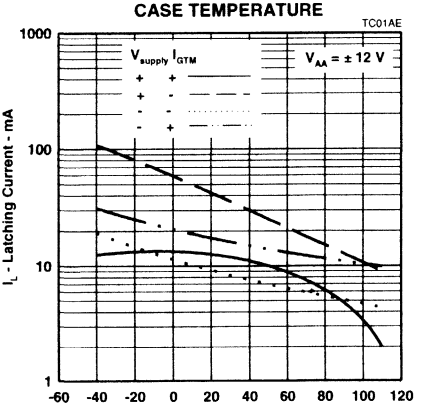



Figure 5.

### SURGE ON-STATE CURRENT vs CYCLES OF CURRENT DURATION

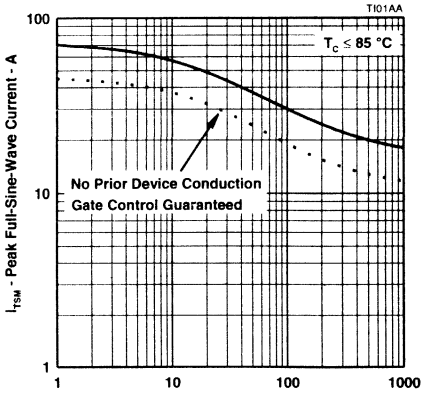



Figure 6.

## TYPICAL CHARACTERISTICS

**MAX RMS ON-STATE CURRENT vs CASE TEMPERATURE**

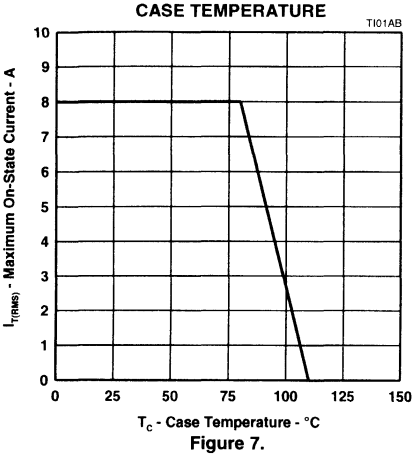



**Figure 7.**

**MAX AVERAGE POWER DISSIPATED vs RMS ON-STATE CURRENT**

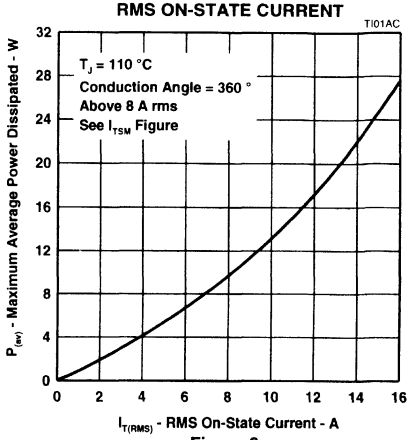
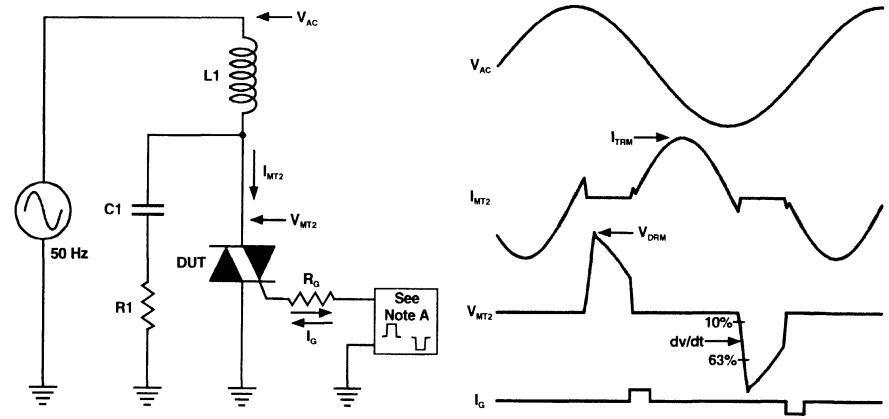



**Figure 8.**

## PARAMETER MEASUREMENT INFORMATION




NOTE A: The gate-current pulse is furnished by a trigger circuit which presents essentially an open circuit between pulses. The pulse is timed so that the off-state-voltage duration is approximately 800 µs.

PMC2AA

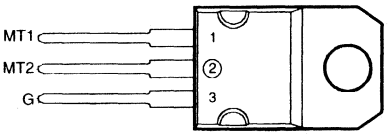
**Figure 9.**

TEXAS INSTRUMENTS

DECEMBER 1971 - REVISED JANUARY 1995

- **High Current Triacs**
- **12 A RMS**
- **400 V to 800 V**
- **Max $I_{GT}$ of 50 mA (Quadrants 1 - 3)**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC236D | $V_{DRM}$ | 400 | V |
| | TIC236M | | 600 | |
| | TIC236S | | 700 | |
| | TIC236N | | 800 | |
| Full-cycle RMS on-state current at (or below) 70°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 12 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 100 | A |
| Peak gate current | | $I_{GM}$ | ±1 | A |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 70°C derate linearly to 110°C case temperature at the rate of 300 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±2 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 5 | 50 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -11 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -20 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 28 | | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.7 | 2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.9 | 2 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±17 A | $I_G$ = 100 mA | (see Note 4) | | ±1.5 | ±2.1 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | 12 | 40 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | -12 | -40 | |

† All voltages are with respect to Main Terminal 1.

NOTE 4: This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_L$ | Latching current | $V_{supply}$ = +12 V† $V_{supply}$ = -12 V† | (see Note 5) | | | | 80 -80 | mA |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = Rated $V_D$ | $I_G$ = 0 | $T_C$ = 110°C | | ±400 | | V/µs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_D$ = Rated $V_D$ di/dt = 0.5 $I_{T(RMS)}$/ms | | $T_C$ = 80°C $I_T$ = 1.4 $I_{T(RMS)}$ | ±1.2 | ±2 | | V/µs |
| di/dt | Critical rate of rise of on -state current | $V_D$ = Rated $V_D$ $di_G/dt$ = 50 mA/µs | $I_{GT}$ = 50 mA | $T_C$ = 110°C | | ±200 | | A/µs |

† All voltages are with respect to Main Terminal 1.

NOTE 5: The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 µs, $t_r$ = ≤ 15 ns, f = 1 kHz.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 2 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs CASE TEMPERATURE**

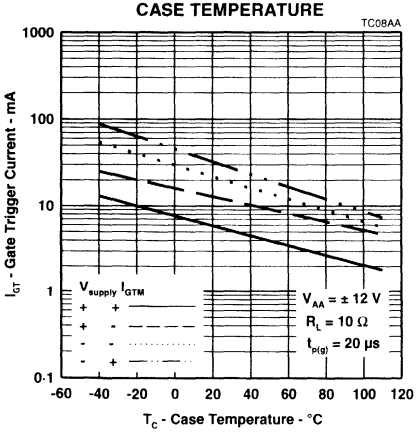



Figure 1.

**GATE TRIGGER VOLTAGE vs CASE TEMPERATURE**

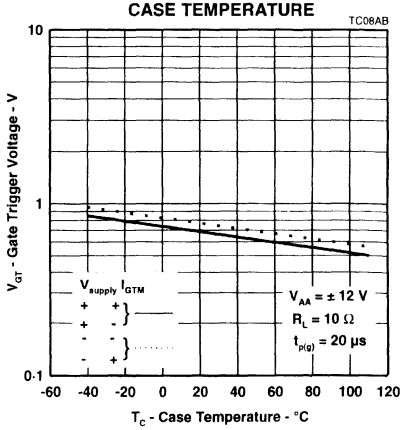



Figure 2.

## TYPICAL CHARACTERISTICS

HOLDING CURRENT
vs
CASE TEMPERATURE

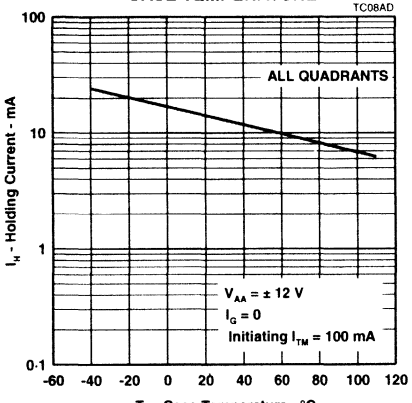



Figure 3.

GATE FORWARD VOLTAGE
vs
GATE FORWARD CURRENT

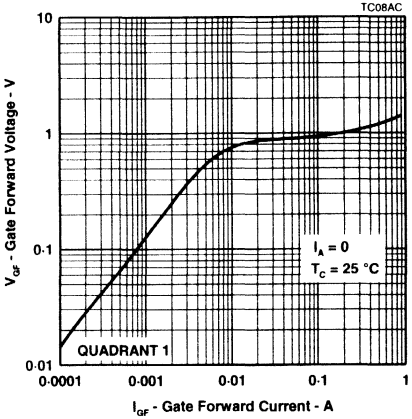



Figure 4.

LATCHING CURRENT
vs
CASE TEMPERATURE

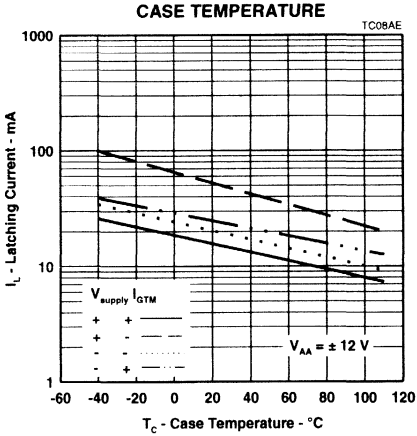
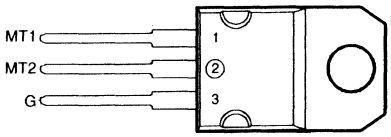



Figure 5.

DECEMBER 1971 - REVISED JANUARY 1995

- **High Current Triacs**
- **16 A RMS**
- **400 V to 800 V**
- **125 A Peak Current**
- **Max $I_{GT}$ of 50 mA (Quadrants 1 - 3)**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC246D | $V_{DRM}$ | 400 | V |
| | TIC246M | | 600 | |
| | TIC246S | | 700 | |
| | TIC246N | | 800 | |
| Full-cycle RMS on-state current at (or below) 70°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 16 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 125 | A |
| Peak gate current | | $I_{GM}$ | ±1 | A |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 70°C derate linearly to 110°C case temperature at the rate of 400 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±2 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 5 | 50 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -11 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -20 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 28 | | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.7 | 2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.9 | 2 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±22.5 A | $I_G$ = 100 mA | (see Note 4) | | ±1.4 | ±1.7 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | 12 | 40 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | -12 | -40 | |

† All voltages are with respect to Main Terminal 1.

NOTE 4: This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_L$ | Latching current | $V_{supply}$ = +12 V†<br>$V_{supply}$ = -12 V† | (see Note 5) | | | | 80<br>-80 | mA |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = Rated $V_D$ | $I_G$ = 0 | $T_C$ = 110°C | | ±400 | | V/µs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_D$ = Rated $V_D$<br>di/dt = 0.5 $I_{T(RMS)}$/ms | | $T_C$ = 80°C<br>$I_T$ = 1.4 $I_{T(RMS)}$ | ±1.2 | ±2 | | V/µs |
| di/dt | Critical rate of rise of on -state current | $V_D$ = Rated $V_D$<br>$di_G/dt$ = 50 mA/µs | $I_{GT}$ = 50 mA | $T_C$ = 110°C | | ±200 | | A/µs |

† All voltages are with respect to Main Terminal 1.

NOTE 5: The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 µs, $t_r$ = ≤ 15 ns, f = 1 kHz.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 1.9 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs CASE TEMPERATURE**

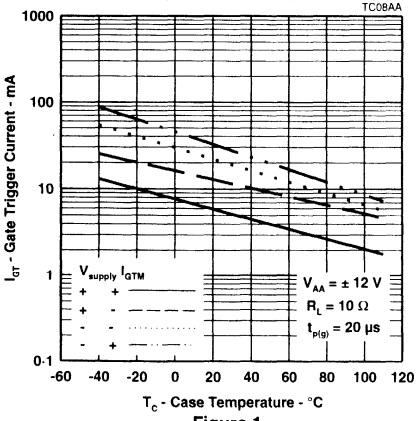



Figure 1.

**GATE TRIGGER VOLTAGE vs CASE TEMPERATURE**

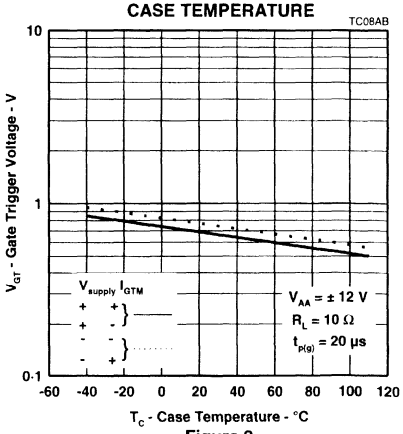



Figure 2.

TEXAS INSTRUMENTS

DECEMBER 1971 - REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

HOLDING CURRENT
vs
CASE TEMPERATURE

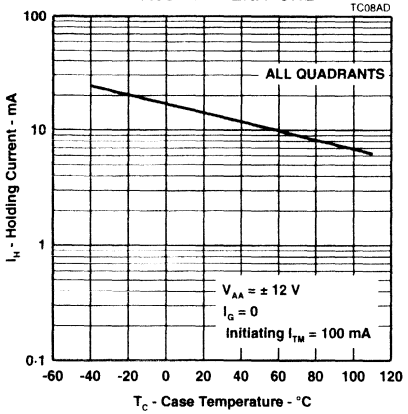



Figure 3.

GATE FORWARD VOLTAGE
vs
GATE FORWARD CURRENT

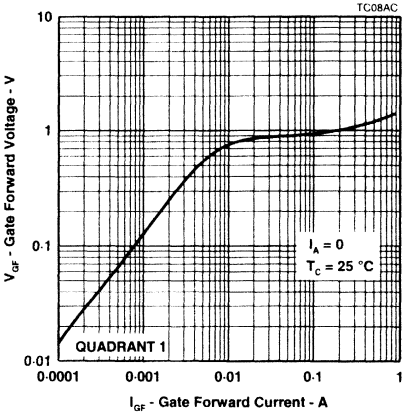



Figure 4.

LATCHING CURRENT
vs
CASE TEMPERATURE

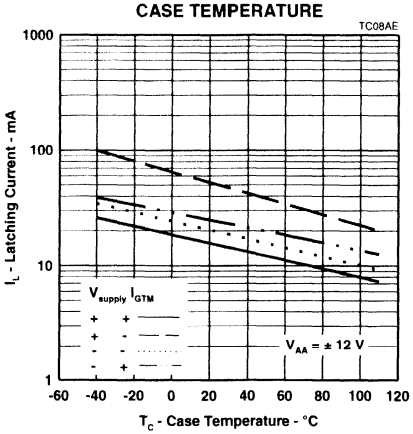
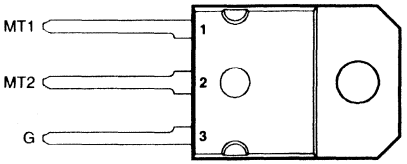



Figure 5.

DECEMBER 1971 - REVISED JANUARY 1995

- **High Current Triacs**
- **20 A RMS**
- **400 V to 800 V**
- **150 A Peak Current**
- **Max $I_{GT}$ of 50 mA (Quadrants 1 - 3)**

**SOT-93 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AD

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC253D | $V_{DRM}$ | 400 | V |
| | TIC253M | | 600 | |
| | TIC253S | | 700 | |
| | TIC253N | | 800 | |
| Full-cycle RMS on-state current at (or below) 70°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 20 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 150 | A |
| Peak gate current | | $I_{GM}$ | ±1 | A |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1 6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 70°C derate linearly to 110°C case temperature at the rate of 500 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±2 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 7 | 50 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -15 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -16 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 28 | | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.7 | 2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.7 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.8 | 2 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±28.2 A | $I_G$ = 50 mA | (see Note 4) | | ±1.4 | ±1.7 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | 6 | 40 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | -13 | -40 | |

† All voltages are with respect to Main Terminal 1.

NOTE 4: This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_L$ | Latching current | $V_{supply}$ = +12 V†<br>$V_{supply}$ = -12 V† | (see Note 5) | | | 20<br>-20 | | mA |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = Rated $V_D$ | $I_G$ = 0 | $T_C$ = 110°C | | ±450 | | V/μs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_D$ = Rated $V_D$<br>$di/dt = 0.5\ I_{T(RMS)}$/ms | | $T_C$ = 80°C<br>$I_T = 1.4\ I_{T(RMS)}$ | | ±1 | | V/μs |
| di/dt | Critical rate of rise of on -state current | $V_D$ = Rated $V_D$<br>$di_G/dt$ = 50 mA/μs | $I_{GT}$ = 50 mA | $T_C$ = 110°C | | ±200 | | A/μs |

† All voltages are with respect to Main Terminal 1.

NOTE 5: The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 μs, $t_r$ = ≤ 15 ns, f = 1 kHz.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 1.52 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 36 | °C/W |

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs CASE TEMPERATURE**

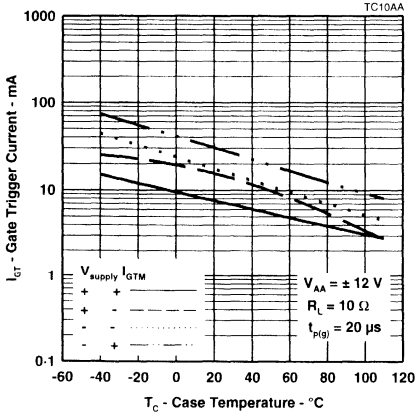



Figure 1.

**GATE TRIGGER VOLTAGE vs CASE TEMPERATURE**

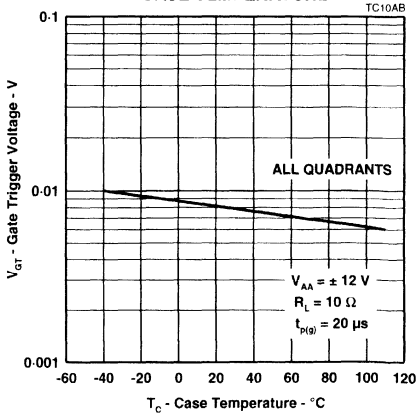



Figure 2.

TEXAS INSTRUMENTS

DECEMBER 1971 - REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

**HOLDING CURRENT**
**vs**
**CASE TEMPERATURE**

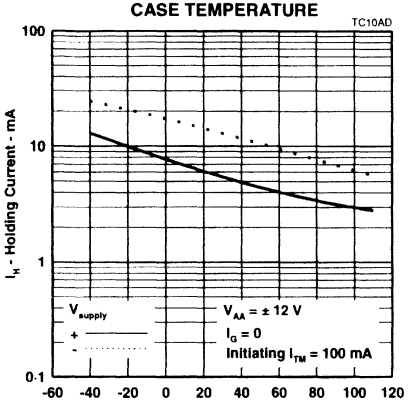



Figure 3.

**GATE FORWARD VOLTAGE**
**vs**
**GATE FORWARD CURRENT**

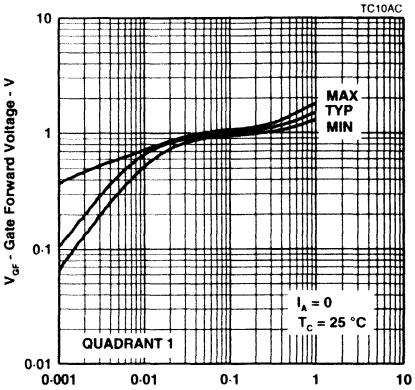



Figure 4.

**LATCHING CURRENT**
**vs**
**CASE TEMPERATURE**

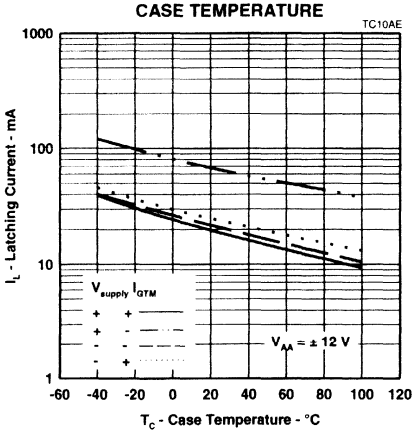
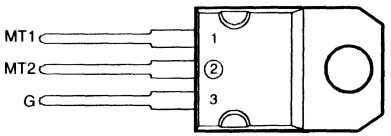



Figure 5.

JULY 1991 - REVISED JANUARY 1995

- **High Current Triacs**
- **20 A RMS**
- **400 V to 800 V**
- **150 A Peak Current**
- **Max $I_{GT}$ of 50 mA (Quadrants 1 - 3)**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC256D | $V_{DRM}$ | 400 | V |
| | TIC256M | | 600 | |
| | TIC256S | | 700 | |
| | TIC256N | | 800 | |
| Full-cycle RMS on-state current at (or below) 60°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 20 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 150 | A |
| Peak gate current | | $I_{GM}$ | ±1 | A |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 60°C derate linearly to 110°C case temperature at the rate of 500 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±2 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 7 | 50 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -15 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -16 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 28 | | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.7 | 2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.7 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.8 | 2 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±28.2 A | $I_G$ = 50 mA | (see Note 4) | | ±1.4 | ±1.7 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | 6 | 40 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | -13 | -40 | |

† All voltages are with respect to Main Terminal 1.

NOTE 4: This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_L$ | Latching current | $V_{supply}$ = +12 V†<br>$V_{supply}$ = -12 V† | (see Note 5) | | | 20<br>-20 | | mA |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = Rated $V_D$ | $I_G$ = 0 | $T_C$ = 110°C | | ±450 | | V/μs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_D$ = Rated $V_D$<br>di/dt = 0.5 $I_{T(RMS)}$/ms | | $T_C$ = 80°C<br>$I_T$ = 1.4 $I_{T(RMS)}$ | | ±1 | | V/μs |
| di/dt | Critical rate of rise of on -state current | $V_D$ = Rated $V_D$<br>$di_G/dt$ = 50 mA/μs | $I_{GT}$ = 50 mA | $T_C$ = 110°C | | ±200 | | A/μs |

† All voltages are with respect to Main Terminal 1.

NOTE 5: The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 μs, $t_r$ = ≤ 15 ns, f = 1 kHz.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 1.9 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 62.5 | °C/W |

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs CASE TEMPERATURE**

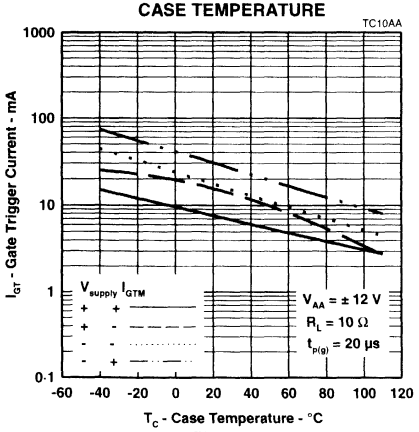



Figure 1.

**GATE TRIGGER VOLTAGE vs CASE TEMPERATURE**

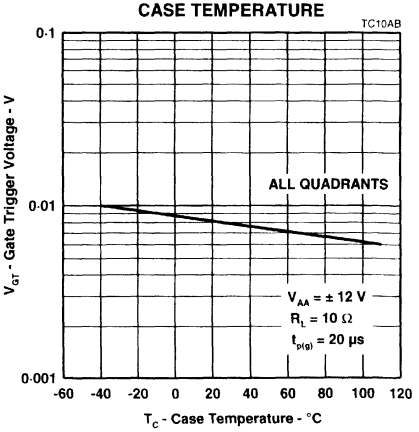



Figure 2.

TEXAS INSTRUMENTS

JULY 1991 - REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

**HOLDING CURRENT**
**vs**
**CASE TEMPERATURE**

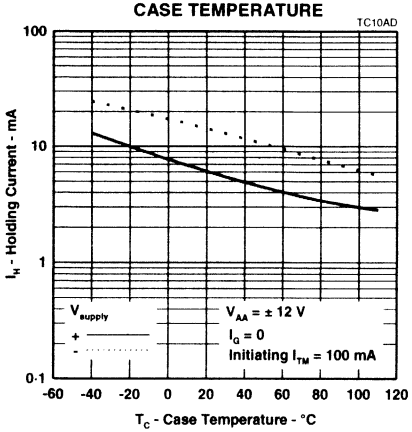



Figure 3.

**GATE FORWARD VOLTAGE**
**vs**
**GATE FORWARD CURRENT**

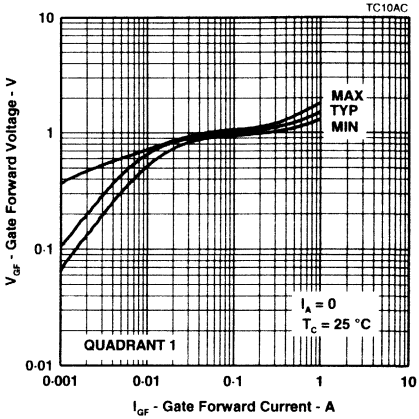



Figure 4.

**LATCHING CURRENT**
**vs**
**CASE TEMPERATURE**

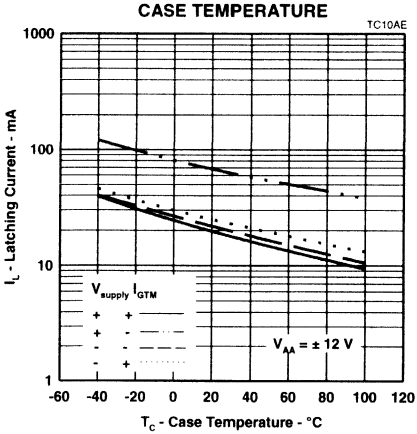
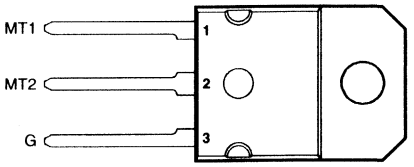



Figure 5.

DECEMBER 1971 - REVISED JANUARY 1995

- **High Current Triacs**
- **25 A RMS**
- **400 V to 800 V**
- **175 A Peak Current**
- **Max $I_{GT}$ of 50 mA (Quadrants 1 - 3)**

**SOT-93 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AD

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC263D | $V_{DRM}$ | 400 | V |
| | TIC263M | | 600 | |
| | TIC263S | | 700 | |
| | TIC263N | | 800 | |
| Full-cycle RMS on-state current at (or below) 70°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 25 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 175 | A |
| Peak gate current | | $I_{GM}$ | ±1 | A |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 70°C derate linearly to 110°C case temperature at the rate of 625 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±2 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | 7 | 50 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | -15 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | -16 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | 28 | | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | 0.7 | 2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | -0.7 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | 0.8 | 2 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±35.2 A | $I_G$ = 50 mA | (see Note 4) | | ±1.5 | ±1.7 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | 6 | 40 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | -13 | -40 | |

† All voltages are with respect to Main Terminal 1.

NOTE 4: This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

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TEXAS INSTRUMENTS

DECEMBER 1971 - REVISED JANUARY 1995

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_L$ | Latching current | $V_{supply}$ = +12 V† | (see Note 5) | | | 20 | | mA |
| | | $V_{supply}$ = -12 V† | | | | -20 | | |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = Rated $V_D$ | $I_G$ = 0 | $T_C$ = 110°C | | ±450 | | V/μs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_D$ = Rated $V_D$ | | $T_C$ = 80°C | | ±1 | | V/μs |
| | | di/dt = 0.5 $I_{T(RMS)}$/ms | | $I_T$ = 1.4 $I_{T(RMS)}$ | | | | |
| di/dt | Critical rate of rise of on -state current | $V_D$ = Rated $V_D$ | $I_{GT}$ = 50 mA | $T_C$ = 110°C | | ±200 | | A/μs |
| | | $di_G/dt$ = 50 mA/μs | | | | | | |

† All voltages are with respect to Main Terminal 1.

NOTE 5: The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 μs, $t_r$ = ≤ 15 ns, f = 1 kHz.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 1.52 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 36 | °C/W |

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs CASE TEMPERATURE**

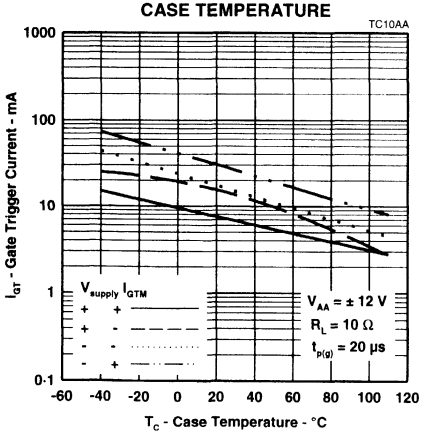



Figure 1.

**GATE TRIGGER VOLTAGE vs CASE TEMPERATURE**

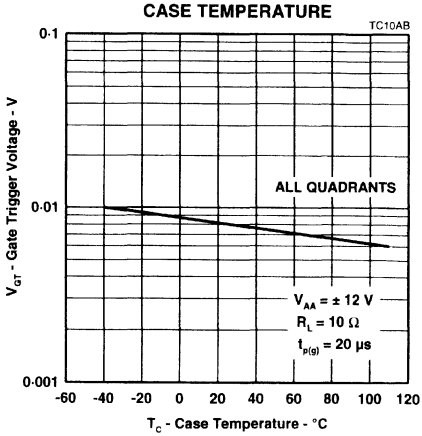



Figure 2.

TEXAS INSTRUMENTS

DECEMBER 1971 - REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

HOLDING CURRENT
vs
CASE TEMPERATURE

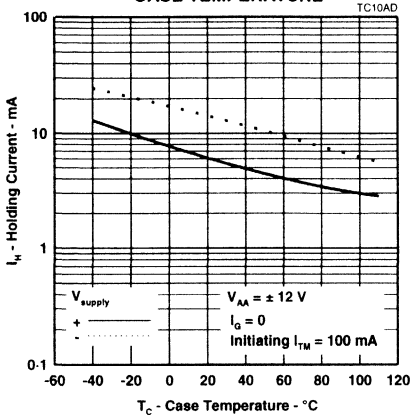



Figure 3.

GATE FORWARD VOLTAGE
vs
GATE FORWARD CURRENT

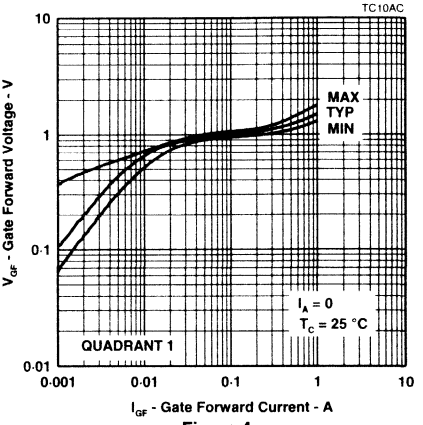



Figure 4.

LATCHING CURRENT
vs
CASE TEMPERATURE

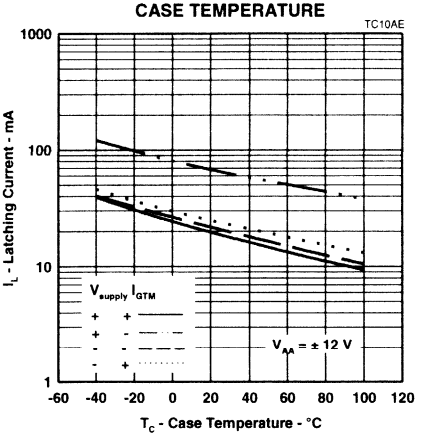
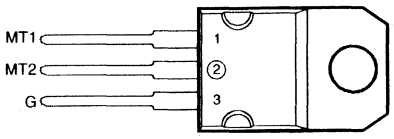



Figure 5.

JULY 1991 - REVISED JANUARY 1995

- **High Current Triacs**
- **25 A RMS**
- **400 V to 800 V**
- **175 A Peak Current**
- **Max $I_{GT}$ of 50 mA (Quadrants 1 - 3)**

**TO-220 PACKAGE**
**(TOP VIEW)**




Pin 2 is in electrical contact with the mounting base.

MDC2AC

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TIC266D | $V_{DRM}$ | 400 | V |
| | TIC266M | | 600 | |
| | TIC266S | | 700 | |
| | TIC266N | | 800 | |
| Full-cycle RMS on-state current at (or below) 50°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 25 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 175 | A |
| Peak gate current | | $I_{GM}$ | ±1 | A |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 50°C derate linearly to 110°C case temperature at the rate of 625 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = Rated $V_{DRM}$ | $I_G$ = 0 | $T_C$ = 110°C | | | ±2 | mA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 7 | 50 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -15 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -16 | -50 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 28 | | |
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.7 | 2 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.7 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | -0.8 | -2 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | 0.8 | 2 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±35.2 A | $I_G$ = 50 mA | (see Note 4) | | ±1.5 | ±1.7 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | 6 | 40 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | -13 | -40 | |

† All voltages are with respect to Main Terminal 1.

NOTE 4: This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

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TEXAS INSTRUMENTS

## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_L$ | Latching current | $V_{supply}$ = +12 V† | (see Note 5) | | | 20 | | mA |
| | | $V_{supply}$ = -12 V† | | | | -20 | | |
| dv/dt | Critical rate of rise of off-state voltage | $V_D$ = Rated $V_D$ | $I_G$ = 0 | $T_C$ = 110°C | | ±450 | | V/μs |
| $dv/dt_{(c)}$ | Critical rise of commutation voltage | $V_D$ = Rated $V_D$ | | $T_C$ = 80°C | | ±1 | | V/μs |
| | | di/dt = 0.5 $I_{T(RMS)}$/ms | | $I_T$ = 1.4 $I_{T(RMS)}$ | | | | |
| di/dt | Critical rate of rise of on -state current | $V_D$ = Rated $V_D$ | $I_{GT}$ = 50 mA | $T_C$ = 110°C | | ±200 | | A/μs |
| | | $di_G/dt$ = 50 mA/μs | | | | | | |

† All voltages are with respect to Main Terminal 1.

NOTE 5: The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 μs, $t_r$ = ≤ 15 ns, f = 1 kHz.

## thermal characteristics

| PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $R_{\theta JC}$ | Junction to case thermal resistance | | | 1.52 | °C/W |
| $R_{\theta JA}$ | Junction to free air thermal resistance | | | 36 | °C/W |

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs CASE TEMPERATURE**

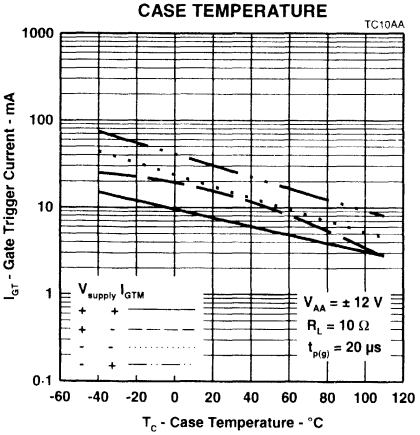



Figure 1.

**GATE TRIGGER VOLTAGE vs CASE TEMPERATURE**

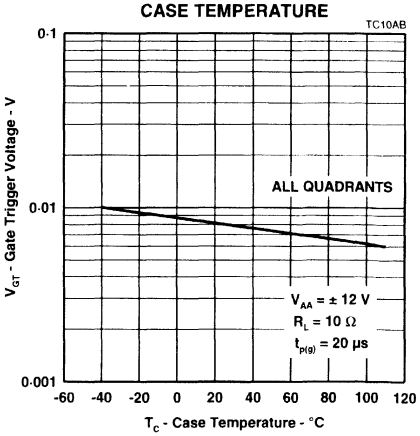



Figure 2.

TEXAS INSTRUMENTS

## TYPICAL CHARACTERISTICS

**HOLDING CURRENT**
**vs**
**CASE TEMPERATURE**

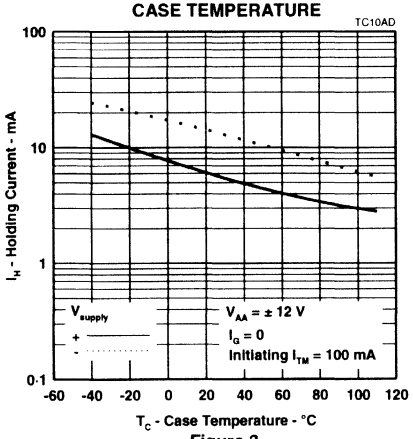



Figure 3.

**GATE FORWARD VOLTAGE**
**vs**
**GATE FORWARD CURRENT**

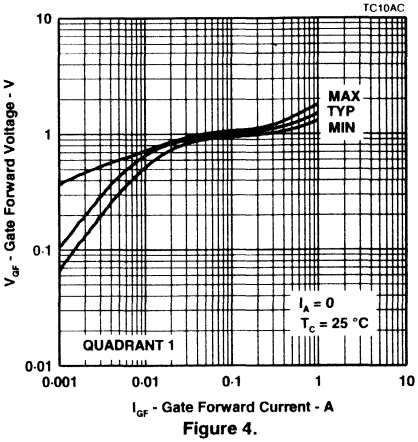



Figure 4.

**LATCHING CURRENT**
**vs**
**CASE TEMPERATURE**

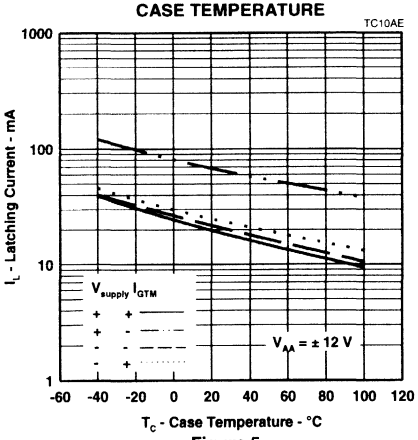


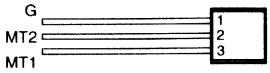

Figure 5.

MARCH 1988 - REVISED JANUARY 1995

- **1.5 A RMS**
- **400 V to 600 V**
- **Max $I_{GT}$ of 10 mA**
- **Package Options**

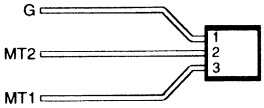
| PACKAGE | PACKING | PART # SUFFIX |
|---|---|---|
| LP | Bulk | (None) |
| LP with fomed leads | Tape and Reel | R |

**LP PACKAGE**
**(TOP VIEW)**




MDC2AA

**LP PACKAGE**
**WITH FORMED LEADS**
**(TOP VIEW)**




MDC2AB

## absolute maximum ratings over operating case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|---|---|---|---|
| Repetitive peak off-state voltage (see Note 1) | TICP206D<br>TICP206M | $V_{DRM}$ | 400<br>600 | V |
| Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2) | | $I_{T(RMS)}$ | 1.5 | A |
| Peak on-state surge current full-sine-wave (see Note 3) | | $I_{TSM}$ | 10 | A |
| Peak on-state surge current half-sine-wave (see Note 4) | | $I_{TSM}$ | 12 | A |
| Peak gate current | | $I_{GM}$ | ±0.2 | A |
| Average gate power dissipation at (or below) 85°C case temperature (see Note 5) | | $P_{G(AV)}$ | 0.3 | W |
| Operating case temperature range | | $T_C$ | -40 to +110 | °C |
| Storage temperature range | | $T_{stg}$ | -40 to +125 | °C |
| Lead temperature 1.6 mm from case for 10 seconds | | $T_L$ | 230 | °C |

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 60 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
5. This value applies for a maximum averaging time of 20 ms.

## electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{DRM}$ | Repetitive peak off-state current | $V_D$ = rated $V_{DRM}$ | $I_G$ = 0 | | | | ±20 | μA |
| $I_{GTM}$ | Peak gate trigger current | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | | 8 | mA |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | | -8 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | | -8 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 μs | | | 10 | |

† All voltages are with respect to Main Terminal 1.

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## electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

| PARAMETER | | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $V_{GTM}$ | Peak gate trigger voltage | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | 2.5 | V |
| | | $V_{supply}$ = +12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | -2.5 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | -2.5 | |
| | | $V_{supply}$ = -12 V† | $R_L$ = 10 Ω | $t_{p(g)}$ > 20 µs | | | 2.5 | |
| $V_{TM}$ | Peak on-state voltage | $I_{TM}$ = ±1 A | $I_G$ = 50 mA | (see Note 6) | | | ±2.2 | V |
| $I_H$ | Holding current | $V_{supply}$ = +12 V† | $I_G$ = 0 | Init' $I_{TM}$ = 100 mA | | | 30 | mA |
| | | $V_{supply}$ = -12 V† | $I_G$ = 0 | Init' $I_{TM}$ = -100 mA | | | -30 | |
| $I_L$ | Latching current | $V_{supply}$ = +12 V† | (see Note 7) | | | | 40 | mA |
| | | $V_{supply}$ = -12 V† | | | | | -40 | |

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, $t_p$ = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics: $R_G$ = 100 Ω, $t_{p(g)}$ = 20 µs, $t_r$ = ≤ 15 ns, f = 1 kHz.

## TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT vs TEMPERATURE**

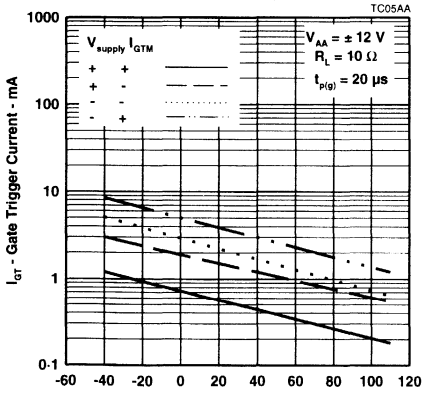



Figure 1.

**GATE TRIGGER VOLTAGE vs TEMPERATURE**

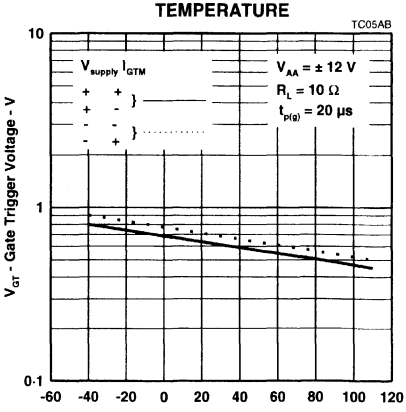



Figure 2.

TEXAS INSTRUMENTS

MARCH 1988 - REVISED JANUARY 1995

## TYPICAL CHARACTERISTICS

**HOLDING CURRENT**
**vs**
**CASE TEMPERATURE**

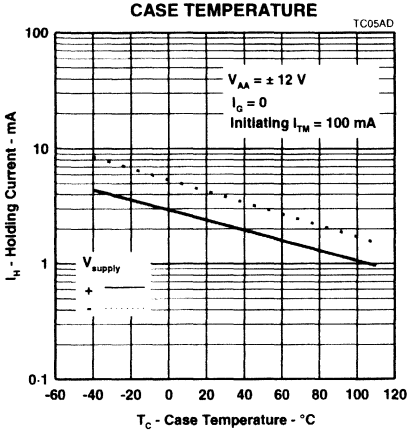



Figure 3.

**GATE FORWARD VOLTAGE**
**vs**
**GATE FORWARD CURRENT**

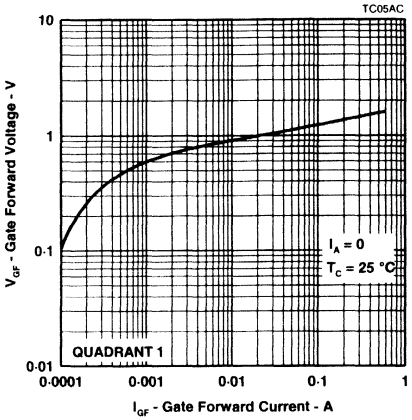



Figure 4.

**LATCHING CURRENT**
**vs**
**CASE TEMPERATURE**

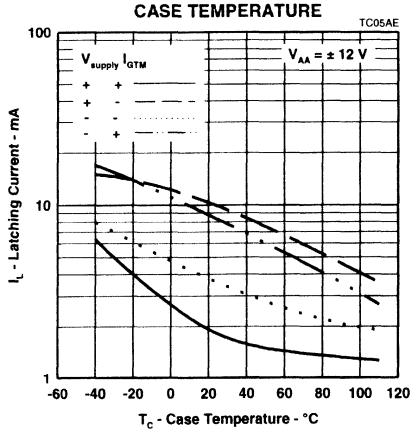



Figure 5.

# *Applications Information*

TEXAS INSTRUMENTS

*Dedication*

*Under the leadership of Bryan Norris, the Texas Instruments Application Laboratory at Bedford England produced over 200 Application Reports and 5 Semiconductor Circuit Design Books. The information presented in this chapter is based on the "B" series of Application Reports written by Jurek Budek*

# Thyristors - Theory, Parameters and Applications

**Jurek Budek**
**Bedford Applications Laboratory**
**(Edited by M J Maytum)**
**Bedford Power Department**

## ABSTRACT

The operational characteristics of the Thyristor are derived from the basic silicon structure and its equivalent circuit. Actual device characteristics and ratings are then discussed with illustrations of the temperature and operating mode sensitivities. Based on this, design approaches are formulated for triggering, selection and control of current and voltage, finishing with cooling requirements. Finally, some typical application circuits are discussed

## INTRODUCTION

The name of Thyristor is derived from the Greek word "ηθνρα" meaning "a door". A Thyristor is a bistable semiconductor device that comprises three or more junctions and can be switched from the off state to the on state or vice versa. Switching from the off state to the on state is normally initiated by a control signal. Switch off is normally caused by the current though the Thyristor dropping below a critical level. This chapter is concerned with the two main Thyristor types called SCRs (Silicon Controlled Rectifiers - Ref. 1.) and Triacs (Ref. 2.). Chapter 2, Glossary, should be consulted for further information on types, terms and definitions.

The first commercial SCRs appeared in the late 1950s. They were an immediate success by providing an efficient, long life, bounceless switch to replace relays, rheostats, thyratrons and such like. The SCR is a unidirectional Thyristor and so it can only be controlled in one voltage polarity. To control both polarities of the ac supply either two SCRs had to be used, connected in anti-parallel, or a single SCR inside a full wave bridge rectifier (Ref. 1, Chapter 8 - AC Phase Controlled Circuits).

In the 1960s, bidirectional Thyristors, called Triacs, where introduced. AC control was now possible with a single silicon power device. Today, through better understanding and technology, SCRs, Triacs and their derivatives are pre-eminent in the solid state control of ac power.

## THEORY

### BIPOLAR JUNCTION HIERARCHY

The Thyristor NPNP silicon layer structure can be considered the result of an evolution the basic PN layer junction rectifier diode, Figure 1. The following treatment of bipolar junction behaviour assumes readers are familiar with basic semiconductor theory.

#### Diodes

A PN junction diode has a low impedance when the P-type layer is positively (forward) voltage biased with respect to the N-type layer. The electrode connecting to the P-type layer is called the anode, symbol A, and that connecting to the N-type layer is called the cathode, symbol K. Forward conduction begins at a threshold voltage of about 0.5 V and a junction strongly in current conduction will develop voltages of 0.7 V and above. The direction of this current conduction is indicated by the arrow direction of the diode symbol.

The diode has a high impedance when the P-type layer is negatively (reverse) voltage biased with respect to the N-type layer. The maximum value of reverse voltage that the junction blocks to will depend on the junction design. Above this voltage the junction will breakdown, symbol (BR), either at the surface or internally. Internal breakdowns below about 6 V are due to the

"Zener" effect and above 6 V by the "Avalanche" effect. Zener voltages decrease with increasing temperature, whilst Avalanche voltage increase at approximately 0.1%/°C. When the breakdown is internal, reasonable amounts of breakdown power can be reliably dissipated. This, together with a low impedance in the breakdown condition, is the basis of reference/regulator/Zener diodes. Such diodes are indicated by a "hook" on the diode crossbar.

Both majority and minority carriers take part in the forward conduction (bipolar action). This causes conduction delays. A fast rising forward conduction current may initially cause a forward voltage higher than the dc value. More importantly, as the conduction current reverses, the stored charge in the diode prevents instantaneous switching back to the reverse-blocking state.

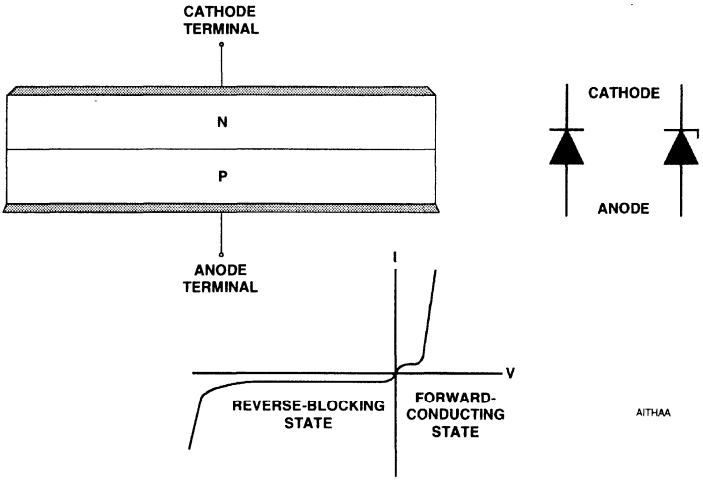



**Figure 1. Diodes**

### Transistors

Adding a second junction creates the bipolar junction transistor, Figure 2. Depending where the second junction is added the transistor can be a PNP or a NPN layer device. Figure 2, shows the structure of an NPN transistor. By making a thin central base layer, the majority of the carriers injected from the emitter layer travel straight through the base layer and into the collector layer. The uncollected carriers form the base current, $I_B$. For injection to take place the base-emitter junction must be forward biased, but the base current needed to establish the bias is much smaller than the collector current, $I_C$. Thus the bipolar transistor is considered as a current amplifier with a gain, $H_{FE}$, of $I_C/I_B$.

The voltage drop across the base-emitter junction will be similar to a diode, 0.5 V threshold and 0.7 V or above when in full conduction. The transistor symbol marks the base-emitter junction with an arrow in the emitter, the arrow being oriented to show the direction of current flow. An NPN transistor has the arrow pointing away from the base and a PNP transistor has the arrow pointing to the base. Although the base-collector junction is another diode, the normal direction of collector current flow is in the same direction as the emitter current flow, i.e. in the opposite direction to the current flow of a forward biased base-collector junction.

When the external circuit does not allow the transistor to pass its full value of collector current, the current difference is added to the base current. The relative increase in base current lowers the transistors gain, $I_C/I_B$, and the transistor is said to be in saturation, symbol (SAT). Under these conditions the base-collector junction starts to become forward biased, which reduces its

collection efficiency. If the base-collector junction is at the threshold of forward conduction, 0.5 V, and the base-emitter junction saturation voltage, $V_{BE(SAT)}$, is 0.7 V, the collector-emitter saturation voltage, $V_{CE(SAT)}$, will be the voltage difference of the two junction drops, i.e. $V_{CE(SAT)} = 0.7\text{-}0.5 = 0.2V$. When in saturation large amounts of stored charge are developed which delays the transistor switch off.

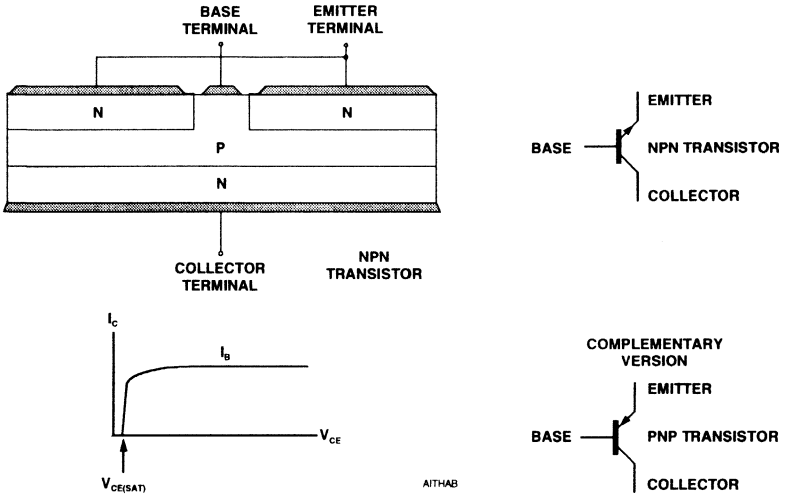



**Figure 2. Transistors**

**Unidirectional Thyristors (SCR)**

Adding a fourth layer creates an NPNP layer structure Figure 3. For anode voltages negative with respect to the cathode, the PN junction connected to the anode blocks any current flow until the breakdown condition is reached. When a positive voltage is applied, the PN junction connected to the gate blocks any current flow until a junction breakdown condition is reached. In this polarity the breakdown voltage is not sustained, but switching into a low voltage state occurs (condition "a" in Figure 3.). This low voltage on-state condition is maintained until the current falls below a critical value called the holding current. The SCR may also be switched on below the breakdown voltage by applying a control current to the gate (curve "b" in Figure 3 where the anode is at an off-state bias of $V_1$).

This structure is normally analysed as an NPN transistor, TR1, and a PNP transistor, TR2, connected such that they share a common collector-base junction. The outer N layer forms the emitter of the NPN transistor, called the Thyristor cathode, and the outer P layer forms the emitter of the PNP, called the Thyristor anode. This connection of the two transistors forms a regenerative loop with the collector current of the NPN supplying the base current of the PNP and the collector current of the PNP supplying to the base current of the NPN. This configuration causes the Thyristor to act as a switch - either off or on.

To initiate switch conduction current must be applied to a transistor base region. Connections to the base regions, gates, allow externally applied currents to initiate switch on. Normally, the NPN transistor base is connected to and this forms a P-type gate, or simply "gate". The control current direction is into the gate and the gate voltage value will be a transistor $V_{BE}$. There are some SCRs where connection is made to the base of the PNP transistor, forming an N-type gate. In this case the control current direction is out of the gate.

If an external base current of $I_{B(NPN)}$ was supplied to the NPN transistor its unlimited collector current would be $H_{FE(NPN)}*I_{B(NPN)}$ which would be the base current of the PNP transistor. The PNP transistor would amplify this current by $H_{FE(PNP)}$ and supply a current of $H_{FE(PNP)}*H_{FE(NPN)}*I_{B(NPN)}$ back to the base of the NPN transistor. For the transistor pair to remain permanently conducting the externally supplied NPN base current must be zero, satisfying the relationship:-

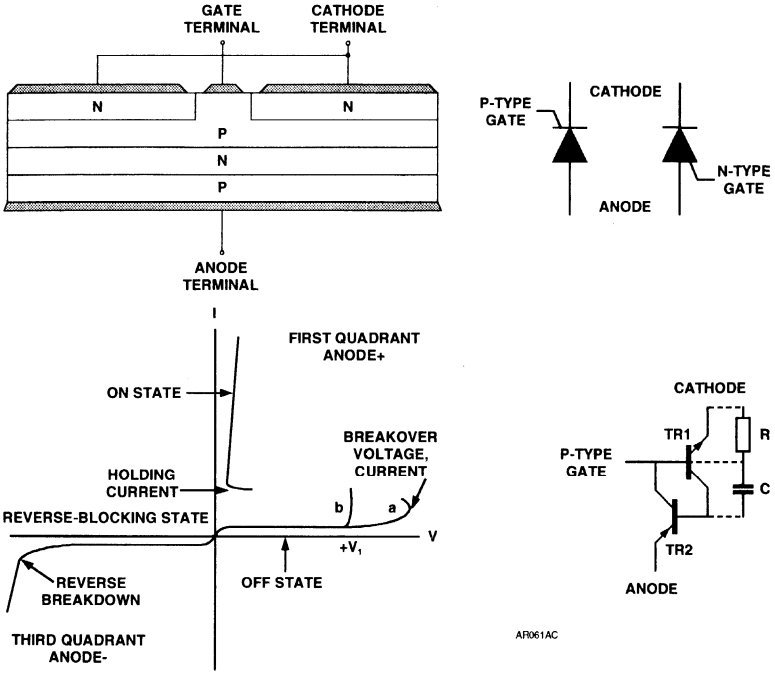



**Figure 3. SCRs**

$I_{B(NPN)} - H_{FE(PNP)}*H_{FE(NPN)}*I_{B(NPN)} <= 0$

or

$1 - H_{FE(PNP)}*H_{FE(NPN)} <= 0$

The values of $H_{FE(PNP)}$ and $H_{FE(NPN)}$ will be current and temperature dependent. At low currents the $H_{FE}$ product falls with reducing current until it is below unity and the SCR switches off. As mentioned earlier, the switch-off current level is called the holding current.

In addition to voltage breakdown and external gate current induced switch on, the SCR may also be switched on as a result of rapid voltage rise, dv/dt. The dv/dt causes the junction capacitance, C, to pass a displacement current of C*dv/dt into the transistor bases. Values of 100 V/µs and 50 pF would cause a current of 5 mA. SCR dv/dt ratings can be increased by integrating a resistance, R, across the gate junction to bypass the capacitive current. For this example, with a gate threshold voltage of 0.5 V,

a resistor value of below 100 W would need to be integrated. As this resistor will also bypass dc, the holding current will be increased by about 5 mA.

In the on state, TR1 and TR2 will be operating in a saturated condition. The anode to cathode voltage will be the sum of one transistors $V_{BE(SAT)}$ and the others $V_{CE(SAT)}$. This means that the on-state voltage will be about 0.7 + 0.2 = 0.9 V. The SCR will typically switch into the on state in 1 µs, but stored charge will normally result in switch off times in 5 to 50 µs region. Gate control will be normally lost once switching occurs.

In summary, the SCR is a three terminal device which conducts current in one direction only. It is triggered into conduction by positive gate current, when the anode is at a positive potential. Gate control is lost once switching occurs and conduction ceases when the current drops below the holding current. Turn on is rapid, but turn off is an order of magnitude slower.

**Bidirectional Thyristors (Triacs)**

Bidirectional Thyristors are formed by integrating two NPNP structures in antiparallel (Figure 4.). Anode and cathode terminal designations have no meaning for this structure. The terminals which conduct the switched current are called the main terminals. Main Terminal 1, MT1, is the reference terminal and the gate control circuit return connection is made to this terminal. Main Terminal 2, MT2, is the other main terminal. The circuit symbol for a Triac is shown in Figure 4.

In terms of voltage-current characteristics the Triac looks like two SCRs connected in anti-parallel, permitting switching in both voltage polarities. The Triac structure shows that the Main Terminal 1 has NPNP and PNPN paths to the Main Terminal 2, permitting positive and negative current flow when the appropriate SCR section is switched. In the equivalent circuits, the path for NPNP conduction is represented by TR1 and TR2, while the path for PNPN conduction is represented by TR4 and TR5.

The gate electrode connects to both N-type and P-type regions. This enables the Triac to be switched on with only one gate terminal, for positive or negative Main Terminal 2 voltage and with any polarity of gate current. The triggering operation is complicated, and the equivalent circuits are also shown for positive and negative Main Terminal 2 voltage polarities. The resistive components are formed by the resistance of the P-type and N-type layers. Shunting resistances are produced by the shorting produced by the Gate and Main Terminal electrodes. Triggering paths from the N-type and P-type gate regions are indicated by the dotted boxes. The triggering transistors, TR3 and TR6 through to TR8 are formed by the gate regions and the antiparallel SCR layers.

When the Main Terminal 2 voltage is positive the Thyristor structure formed by TR1 and TR2 can be directly triggered by a positive gate current via the series resistance into the base of TR1. The gate voltage value will be a transistor $V_{BE}$ plus any resistive voltage drops. Negative gate current triggering is also possible. In this case TR3 operates in a common base configuration and feeds current to the base of TR2. Here the gate voltage value will be a transistor $V_{BE}$ plus any resistive voltage drops.

When the Main Terminal 2 voltage is negative the Thyristor structure formed by TR4 and TR5 can be triggered by a negative gate current which flows through TR6, operating in common base configuration, and into the base of TR4. The gate voltage value will be a transistor $V_{CE(SAT)}$ plus a $V_{BE}$. Positive gate current triggering is also possible, but the mechanism is complex and high levels of trigger current are needed. In this case, the positive gate current switches TR7 on and its collector then connects the base of TR8 to Main Terminal 1. In this condition, some of the positive gate current will be fed to the base of TR5 by TR8 operating in common base configuration. The gate voltage value will be a transistor $V_{CE(SAT)}$ plus a $V_{BE}$.

The Triac should only conduct when triggered by the gate control current. The integrated structure of the Triac means that charge from the conducting section can reduce the dv/dt withstand of the non-conducting section. This can result in uncontrolled conduction of the Triac. The commutating dv/dt, $dv_c/dt$, is the measure of the device performance under these conditions. It is defined as the maximum rate of rise of principal voltage that will not cause switching from the off-state to the on-state immediately following on-state current conduction in the opposite quadrant. This parameter is particularly important with

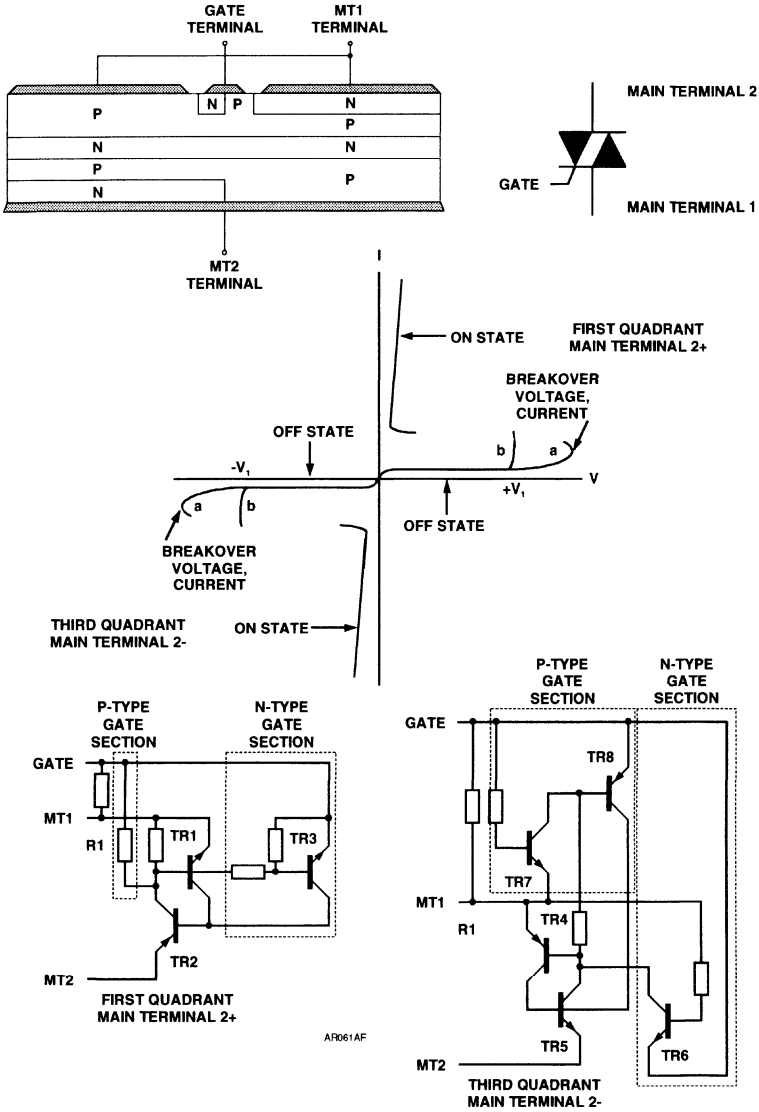



Figure 4. Triacs

inductive loads, as these cause rapid rates of voltage rise.

In summary, the Triac is a three terminal device which conducts current in either direction. It may be triggered into conduction by any polarity of gate current for either polarity of Main Terminal 2 voltage. Similar to an SCR, gate control is lost once switching occurs and conduction ceases when the current drops below the holding current. The rate of voltage rise under inductive load conditions needs to be lower than the commutating dv/dt. Triacs offer simplified circuitry over two Thyristors as only one device and gate trigger circuit are needed.

## PARAMETERS

The selection of a Thyristor normally starts with the necessary voltage and current ratings determined from the nature of the load and its supply voltage (See Chapter 1, Selection Guide). Some loads will draw currents that vary with time, e.g. motor locked, starting and running currents. Device capabilities for such conditions can be assessed by reference to the surge current versus time curves. Inductive loads can produce rapid voltage rises and some form of dv/dt parameter will be needed.

The final device selection will depend on the relative importance of factors such as available cooling, triggering power, package and cost.

### SCRs

This section covers the key parameters of SCRs. To illustrate the selection and design procedure graphs and values from the TIC126 data sheet will be used.

#### Voltage Ratings

The theory section explained how SCRs can be triggered into conduction by breakdown triggering in the positive polarity. This overvoltage protection mechanism does not happen in the reverse direction and the SCR can be damaged by reverse overvoltage transients. Thus the SCR should be selected on the peak repetitive reverse voltage rating, $V_{RRM}$, rather than the peak repetitive off-state voltage, $V_{DRM}$. Most of the SCRs in chapter 3 are available in voltages from 400 V to 800 V. The 400 V minimum value provides adequate safety margin on transient filtered 230 V (325 V maximum) ac supplies. In circuits where the SCR has series rectifier diodes to block reverse voltages, the voltage selection can be made on the $V_{DRM}$ requirements.

#### Current Ratings

The SCR average current rating, $I_{T(AV)}$, will be selected to be equal or greater than the normal load current. Where the load can draw higher short term currents, the ability of the SCR to survive these can be determined from graphs of on-state current versus current duration, See Figure 5.

#### Operating Temperature

Adequate cooling must be provided to ensure long term thermal stability. An estimate of the SCR power loss can be made from the power loss curve, See figure 6. This curve is plotted for continuous current, $I_T$, and a conservative estimate of the equivalent average on-state current (180° conduction angle), $I_{T(AV)}$, can made from $I_{T(AV)}$, = 0.6*$I_T$. If the expected average SCR current was 3.5 A, this would be power equivalent to a continuous current of about 6 A. The loss at this current is 8 W. This loss level is for a junction temperature, $T_J$, of 110°C, and if the highest ambient temperature, $T_A$, is 40°C, the maximum junction to ambient thermal resistance, $R_{QJA}$, will be:

$$R_{QJA} = (110 - 40)/8 \text{ °C/W}$$

$$= 8.75\text{°C/W}$$

As the junction to case thermal resistance, $R_{QJC}$, of the TIC126 is 2.4°C/W, the mounting and heat sink thermal resistance must not exceed 8.75 - 2.4 = 6.35°C/W.

This requirement could be met by a simple square aluminium heat sink plate of 9 cm x 9 cm.

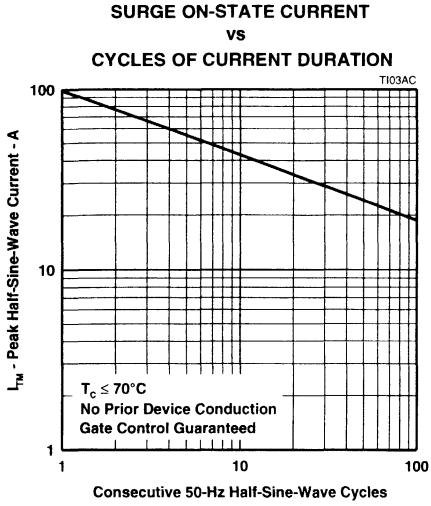



Figure 5.

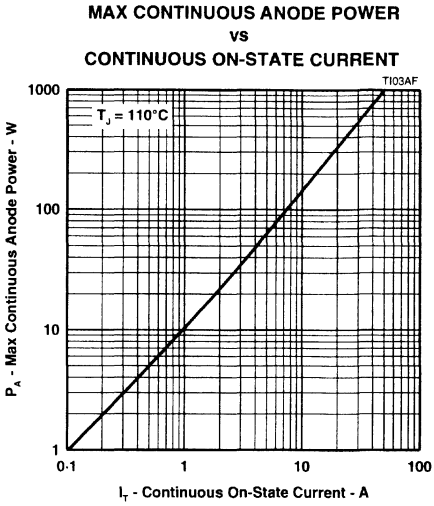



Figure 6.

**Triggering**

The typical temperature variation of gate trigger voltage and current are shown in Figures 7 and 8. Compared to 25°C, at 0°C the voltage has increased by 10% and the current by 30%. The data sheet maximum values at 25°C are 1.5 V and 20 mA. A trigger circuit designed to work down to 0°C should provide a gate current drive of 20*1.3 = 26 mA at a voltage of 1.5*1.1 = 1.65 V. After allowing for trigger circuit tolerances, a design giving a nominal drive of 30 mA into 2 V should be adequate.

**Latching and Holding Current**

Latching current is the minimum value of anode current required to maintain the Thyristor in the on-state immediately after switching from the off-state to the on-state has occurred and the triggering signal has been removed. If a latching current value is not specified, a reasonable assumption is to use a value of three times the holding current. The anode current must be larger than the latching current when the trigger pulse ends, otherwise the SCR could switch off. There are two design solutions to this potential problem. One is to ensure the trigger pulse duration is long enough at the lowest expected operating temperature to always ensure that the latching current is reached during the trigger pulse time. The other is to have short duration multiple trigger pulses so that the device is re-triggered until latched conduction occurs. Generally the minimum trigger pulse width should not be less than 20 µs to allow for current propagation in the chip. Latching is mainly a problem for inductive loads, which will have a slow initial current rise.

Holding current is the minimum value of anode current required to maintain the Thyristor in the on-state. When the load current falls below this value, current switch off occurs and purely inductive loads will generate high values of dv/dt and peak voltage.

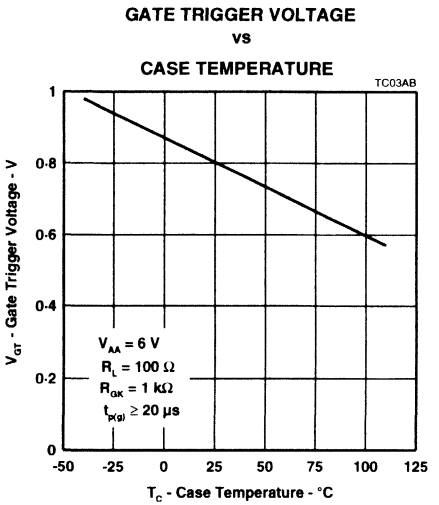



Figure 7.

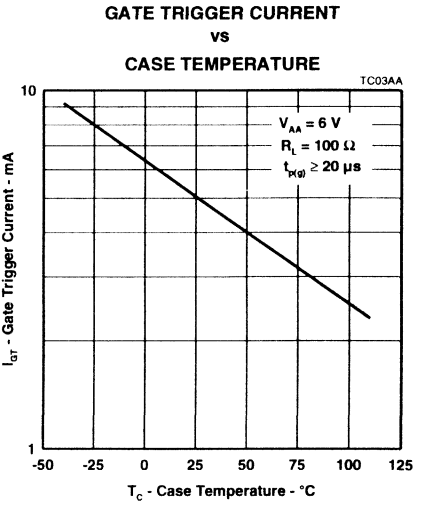



Figure 8.

## TRIACS

This section covers the key parameters of Triacs. To illustrate the selection and design procedure graphs and values from the TIC226 data sheet will be used.

### Voltage Ratings

The theory section explained how Triacs can be triggered into conduction by breakdown triggering in both voltage polarities. Most of the Triacs in chapter 4 are available in voltages from 400 V to 800 V. The 400 V minimum value provides adequate safety margin on transient filtered 230 V (325 V maximum) ac supplies. Where transients are known to occur and voltage dependent resistors are being used to limit the transient voltage Triac $V_{DRM}$ values of 600 V and above should be selected.

### Current Ratings

The Triac rms current rating, $I_{T(RMS)}$ should be selected to be equal or greater than the normal load current. Where the load can draw higher short term currents, the ability of the Triac to survive these can be determined from the graph of on-state current versus current duration. See Figure 9. Note that this graph has two curves. One curve is for the condition that gate control is maintained and the other is for loss of gate control. Although gate control can be restored when the current level reduces, the use of this second curve should be restricted to fault conditions.

### Operating Temperature

Adequate cooling must be provided to ensure long term thermal stability. An estimate of the Triac power loss can be made from a power loss curve or calculation based on $V_{T(MAX)}$. The basis of the calculation is to assume on-state symmetry and approximate the on-state voltage characteristic to a threshold voltage, $V_{T(TO)}$, and a fixed slope resistance, $r_T$. See Figure 10.

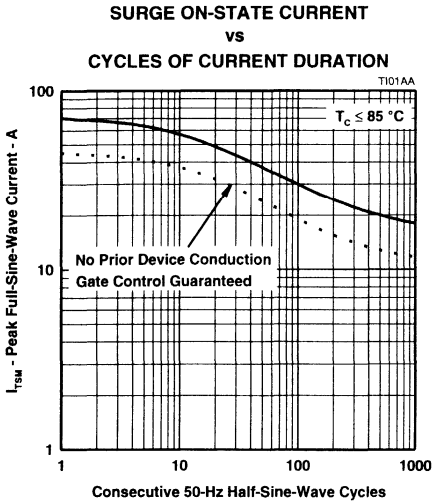



**Figure 9.**

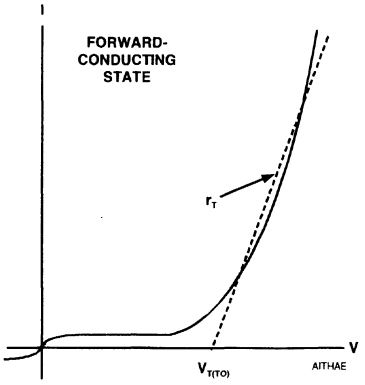



**Figure 10. Linear Approximation**

The instantaneous power at current $i_T$, will be $i_T * V_{T(TO)} + (i_T)^2 * r_T$. Integrating and averaging these two power components over a whole sinewave gives the result:

$$P_T = I_{T(AV)} * V_{T(TO)} + (I_{T(RMS)})^2 * r_T$$

where:

$P_T$ = On-State Power Loss

$I_{T(AV)}$ = Average Current per Half Cycle

$I_{T(RMS)}$ = RMS Current

For sinewave currents the equation can be rewritten as:

$$P_T = 0.9 * I_{T(RMS)} * V_{T(TO)} + (I_{T(RMS)})^2 * r_T$$

The power loss, $P_T$, at the design rms current, $I_{T(RMS)}$, can be calculated provided the Triac values of $V_{T(TO)}$ and $r_T$ are available. At the maximum junction operating temperature the $V_{T(TO)}$ value will be in the region of 0.7 V for the Triacs. The maximum value of $r_T$ can be calculated from $V_{T(MAX)}$ on the assumption that usually the 25°C and 110°C values are similar. Thus the equation for $r_T$ is:

$$r_T = (V_{T(MAX)} - 0.7)/I_T$$

The calculated $r_T$ values for the Triacs of chapter 4 are shown in the table below.

Calculated $r_T$ Values

| Triac | $r_T$ Ω | Triac | $r_T$ Ω | Triac | $r_T$ Ω |
|---|---|---|---|---|---|
| TIC201 | 0.34 | TIC226 | 0.12 | TIC256 | 0.035 |
| TIC206 | 0.36 | TIC236 | 0.082 | TIC263 | 0.028 |
| TIC216 | 0.12 | TIC246 | 0.044 | TIC266 | 0.028 |
| TIC225 | 0.12 | TIC253 | 0.035 | TICP206 | 1.5 |

Once the power loss has been calculated the required cooling can be determined in the same manner as described for SCRs.

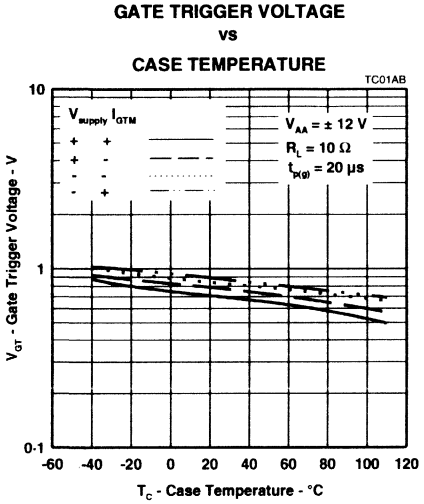



Figure 11.

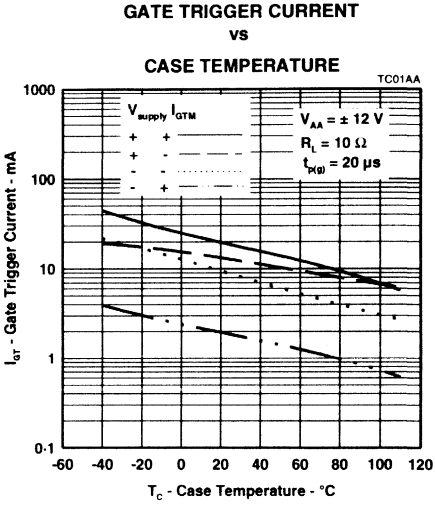



Figure 12.

**Triggering**

Triacs have four triggering combinations. The combination of negative MT2 and positive gate current is not recommended as it is the least sensitive and is not specified for the higher current Triacs (See the Selection Guide Chapter page 1-4). This is the result of a design strategy on the higher current Triacs to obtain the higher dv/dt ratings (400 V/µs) needed for inductive loads by trading gate sensitivity. Because of the reduced sensitivity, these devices are difficult to trigger with a positive gate current when operating in the third quadrant. Consequently, the data sheet does not specify this type of operation. With the three triggering combinations left, the design strategy is governed by the trigger source polarity. If the trigger source has the same polarity, then negative trigger current should be used. If the trigger source is naturally the same polarity as the MT2 voltage then this approach uses the most sensitive pair of triggering combinations and gives the lowest latching current values.

The typical temperature variation of gate trigger voltage and current are shown in Figures 11 and 12. Compared to 25°C, at 0°C the voltage has increased by 10% and the current by 30%. The data sheet maximum values at 25°C are 2 V and 50 mA. A trigger circuit designed to work down to 0°C should provide a gate current drive of 50*1.3 = 65 mA at a voltage of 2*1.1 = 2.2 V. After allowing for trigger circuit tolerances, a design giving a nominal drive of 80 mA into 2.6 V should be ade-

quate.

**Latching and Holding Current**

Latching current is the minimum value of Main Terminal current required to maintain the Thyristor in the on-state immediately after switching from the off-state to the on-state has occurred and the triggering signal has been removed. The complex nature of the Triac triggering causes the latching current to range between two to five times the holding current (See Figures 13 and 14). The Main Terminal current must be larger than the latching current when the trigger pulse ends, otherwise the Triac could switch off. There are two design solutions to this potential problem. One is to ensure the trigger pulse duration is long enough at the lowest expected operating temperature to always ensure that the latching current is reached during the trigger pulse time. The other is to have short duration multiple trigger pulses so that the device is re-triggered until latched conduction occurs. Generally the minimum trigger pulse width should not be less than 20 µs to allow for current propagation in the chip. Latching is mainly a problem for inductive loads, which will have a slow initial current rise. Snubber circuits will often be used for voltage control with inductive loads and the discharge of this network can be used to increase the initial current value.

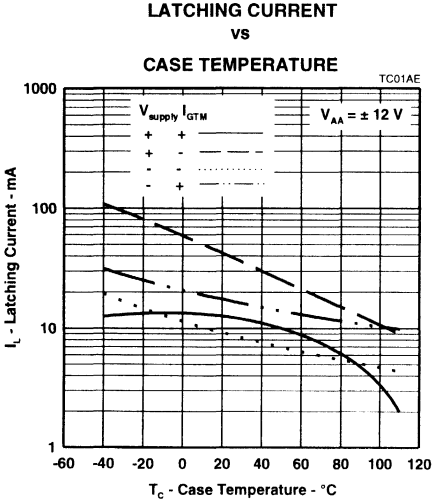



Figure 13.

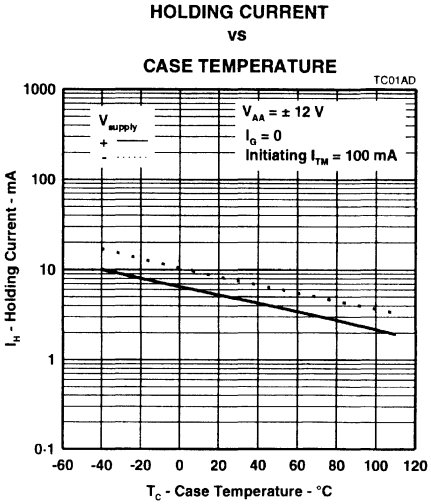


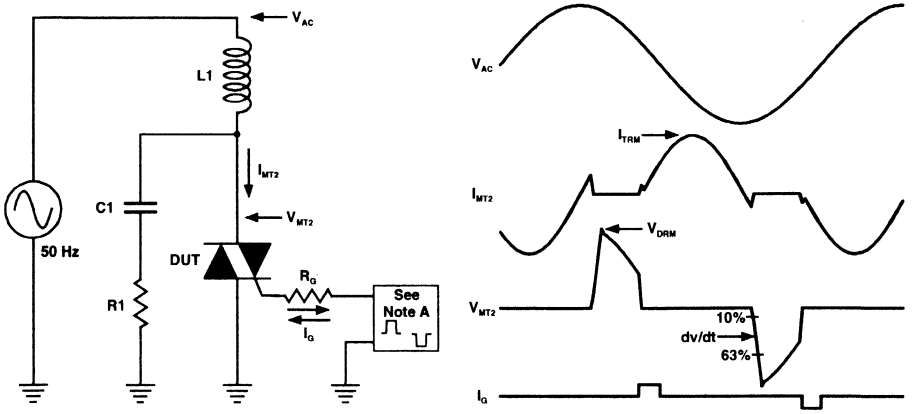

Figure 14.

**Commutating dv/dt, $dv_c/dt$**

This special Triac rating was discussed in the Triac theory section. Figure 15 shows the standard test circuit. The dv/dt is controlled by the RC snubber network and the peak on-state current is set by the inductor value. Setting the peak current will also set the commutating $di_c/dt$ (the rate of change of falling on-state current), a parameter which has a strong influence on the $dv_c/dt$ value. Triacs of 8 A and below are tested with a specified peak current value, $I_{TRM}$. Higher current Triacs are tested with a specified value of $di_c/dt$ equal to $0.5*I_{T(RMS)}$/ms. With the exception of the TIC206, all the other Triacs have $I_{TRM}$ or $I_T = 1.4*I_{T(RMS)}$.

The highest di/dt of a $T_P$ ms duration half sinewave will be $p*I_{TRM}/(T_P)$ A/ms. For the lower current Triacs, the off-state voltage duration is specified as 0.8 ms and so the on-state current duration will be 10 - 0.8 = 9.2 ms. This gives a commutating

$di_C/dt$ of $0.34*I_{TRM}$ A/ms or $0.48*I_{T(RMS)}$ A/s. Thus the $I_{TRM}$ or $0.5*I_{T(RMS)}$ specification approaches are equivalent.




NOTE A: The gate-current pulse is furnished by a trigger circuit which presents essentially an open circuit between pulses. The pulse is timed so that the off-state-voltage duration is approximately 800 µs.

PMC2AA

**Figure 15. Commutating Test Circuit**

## APPLICATION CIRCUITS

### CONTROL METHODS

#### Phase Control

Phase control is the technique of varying, within the cycle or half-cycle of the ac supply voltage, the instant at which the voltage is applied to the load and current conduction begins; current conduction continues until a zero crossing is reached which switches off the Thyristor. This technique is extensively used for incandescent lamp dimming and the speed control of some dc motors. Figure 16 shows a simple phase control circuit.

#### Burst Firing

SCRs and Triacs used in a phase control mode produce considerable radio frequency interference (r.f.i) due to the step change in current. A solution to the problem of suppression becomes more difficult and expensive as the load increases. In domestic appliances, particularly, the r.f.i. is acute and must be suppressed to comply with emc regulations. For domestic use phase controllable power up to 500 Watts may be acceptable. However, above this value the ratio between the phase controllable power to the total consumed power becomes significant and in addition to the expensive suppression circuit, the power factor may cause some concern.

Electric heaters and other loads with a long time constant may be controlled by passing through them a selected number of full or half cycles, See Figure 17. The current, then will be in phase with the voltage and there will be no problem of r.f.i., the switching taking place at the point when the voltage crosses zero. Such control is called Burst Firing or Zero Voltage Switching. Burst firing is not suitable for lamp dimming due to the flicker, or for Motor Speed Control and transformer input control.

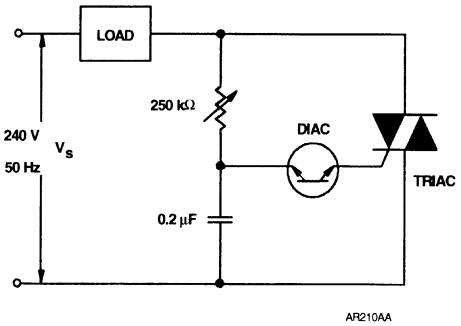



**Figure 16. Simple Phase Control Circuit**

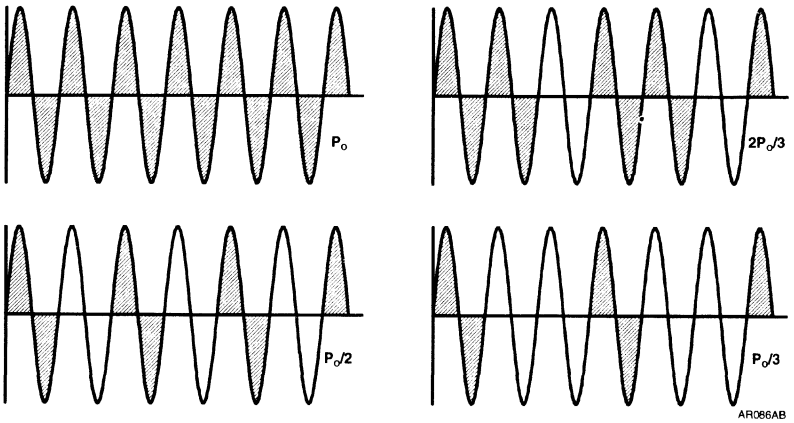



**Figure 17. Burst Firing**

## SCR CIRCUITS

### Half-Wave Motor Speed Control

Half-wave phase control of a universal motor allows the motor to run up to 80% of its maximum full wave speed. Thus a useful speed range is obtained with only half-wave control. The universal motor generates a back emf proportional to its speed. By placing the motor in series with the control loop, drops in the back emf, caused by speed reduction, reduce the time of the next SCR triggering pulse which applies more voltage to the motor on the next cycle. This arrangement provides motor speed regulation. The basic control circuit is shown in Figure 18.

### Gas Ignitor

This is an example of an application that requires high current and voltage capability with relatively little long term power

requirement. Typically a TO-92 TICP106 would be used as the high current switch. For time periods less than 1 ms the TICP106 has the same silicon current capability as the TO-220 TIC106. The basic circuit is shown in Figure 19.

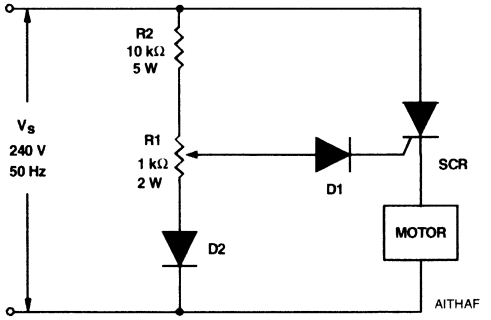



**Figure 18. Half-Wave Motor Control**

The high voltage secondary winding of the step up transformer, T1, produces a spark across the discharge gap to ignite the gas mixture. The high voltage is produced when the TICP106 switches on and connects the charged capacitor across the transformer primary. A resonance ensues which reverses the capacitor voltage and this serves to commutate the TICP106 when the current drops to zero. The capacitor is then recharges from the rectified ac supply for the next spark.

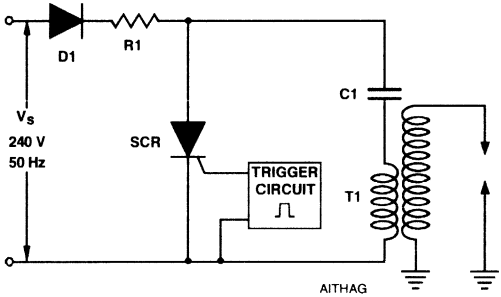



**Figure 19. Ignitor**

## TRIAC CIRCUITS

### Universal Motor Speed Control

The Thyristor has an established position in industrial applications for switching and regulating power. In addition, small SCRs are now widely used to give half-wave phase-control of universal motors in such applications as low-power domestic appliances and hand-tools.

For higher power, where full-wave phase-control is necessary, the Triac has now largely replaced 'back-to-back' connected SCRs. Triacs are widely used in light and heat controls; they can, however, give problems when used with inductive loads. This section discusses the use of Triacs in phase-control circuits with inductive loads, together with protective circuitry to ensure reliable operation. A 1000 Watt vacuum-cleaner with a universal motor is used as an example of this application.

*circuit*

A basic phase-control circuit was shown in Figure 16. The potentiometer and capacitor give variable phase-shift, and the trigger diode, or diac, ensures reliable triggering of the Triac. Although control is possible from approximately 0° to 180°C the circuit has some drawbacks. It may be noticed, when using the circuit, that once the Triac has been turned 'on' at the minimum voltage, the voltage may be further reduced by increasing the potentiometer resistance. In other words, the striking voltage appears to be higher than the turning 'off' voltage. This hysteresis type phenomenon is attributed to the trigger diode breakdown.

In order to reduce the effect on hysteresis and also extend the range of control a second RC network may be added as shown in Figure 20. After the trigger diode has turned 'on', the partly discharged capacitor 'C2' is recharged by some of the energy from capacitor 'C1'. This occurs during the time the Triac is conducting, hence the smaller hysteresis. This is a basic circuit recommended for light dimmers and universal motors as mentioned earlier. The selection of components will be discussed later.

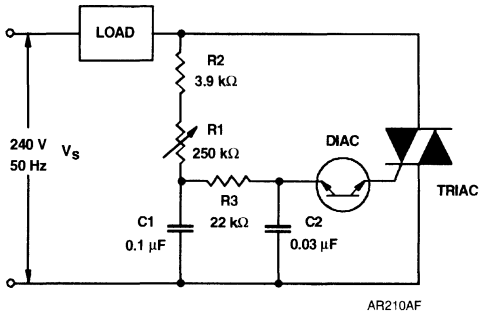



**Figure 20. Improved Phase Control Circuit**

*protection*

To ensure the satisfactory operation of equipment using semiconductor devices, the problem of protection must be solved. There are several points to which a designer must pay attention, i.e., the rate of rise of voltage (dv/dt), the rate of rise of current, (di/dt), voltage surges and overloads.

*commutation and critical dv/dt*

When used with inductive loads, Triacs and SCRs are subjected to a rapid rise of voltage. If a device is not capable of withstanding such fast rises in voltages, it will lose control. The problem of dv/dt becomes important especially after commutation when the capability of a device becomes lower.

From Figure 21 it can be seen the Triac will be exposed to 'commutation dv/dt'. 'Commutation dv/dt' occurs when the blocking voltage is being stressed across the device during the time it is recovering from the principle current. Malfunctioning can even occur due to fast voltage transients initiated at switch-on. This characteristic phenomenon of Triacs and SCRs is caused by capacitive coupling between gate and MT2 terminal for Triacs and gate and anode for SCR. Unwanted turn 'on at full voltage could bring some problems, especially when the equipment is feeding low impedance loads such as stationary motors or a bank of filament lamps. Excessive currents flowing, even for half a cycle, could blow the protective fuses or damage some of the semiconductors. The gates of the Triacs will resume control after half a cycle.

Solving and analysing the following equation :-

$$L(di/dt) + Ri\,(1/c)\,f\,i.d.t = Vmax \qquad (1)$$

gives

$$(dv/dt)max = Vmax/\sqrt{LC}$$

hence

$$C = V^2max/L.\ (dv/dt)max^2 \qquad (2)$$

where:

$V_{max}$ = peak supply voltage

$dv/dt_{max}$ = values obtained from the data sheets (V/μs)

If the supply reactance = X%, then

$$\omega L.\ I.\ 100/V = X \qquad (3)$$

where:

I = supply current, rms

V = supply voltage, rms

Substituting L from equation (3) into equation (2) the value of the capacitor becomes :-

$$C = 2.V.\pi.I/((dv/dt)^2.10^2.X)\ \mu F$$

assuming a frequency of 50Hz and (dv/dt) in volts/μs. The discharge of the capacitor through a Triac should be limited by adding a series resistor. This resistor should also be able to damp the ringing of the capacitance with the load inductance.

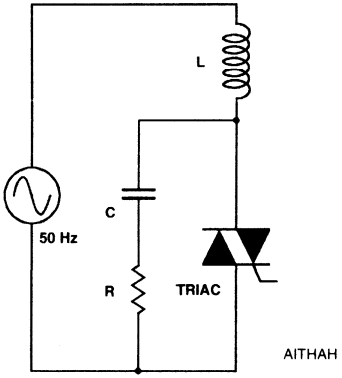



**Figure 21. dv/dt with Inductive Loads**

One way of slowing down the voltage rise of the switching supply voltage or transients is to bring the circuit into oscillation by adding a CR network and inductance if required. A suitable place to connect R and C is across the Triac. The accidental turning 'on' of a Triac may not be harmful, but it could lead to di/dt failure or half waving which in magnetic circuits could result in partial saturation and hence heavy overload. Because of this, precautions must be taken to avoid the possibility of turning on the Triac by dv/dt.

***rate of rise of current - di/dt***

If the rate of rise of current is very high as compared with the speed with which the current turning 'on' can spread across the junction of the Triac or SCR, a local "hot spot" may develop causing a device to fail. In most cases, there is not cause for concern as sufficient inductance exists in the circuit. In low inductive circuits where motor is parallel with resistive load the value of di/dt should be examined and related to the rate of rise which the Triac or SCR under consideration can handle. If necessary, some inductance should be added in the circuit to slow down the rise of current.

***voltage transients***

Diodes and SCRs can be destroyed when subjected to excessive voltage transients, unless they incorporate avalanche characteristics. The Triac, being a bidirectional switch, will simply break over in one or other direction, turning 'on' into conduction. In spite of these self protective capabilities, the turning "on" of a Triac, even for one isolated pulse, may not be acceptable as explained earlier. An effective surge absorbing device, therefore, is necessary for reliable operation. Voltage transients can be initiated by various means such as switching transformers, inductors, from Thyristor circuits as commutation spikes, etc. The suppression of transient voltages can easily be achieved if the sources and causes of transients are known. Voltage transients generated by switching 'off' transformers are known to a certain extent. The energy, E, stored in the magnetic field can be evaluated from the equation $E = \frac{1}{2}LI^2$ where 'I' is the peak magnetising current. By using a CR network as a surge absorbing device, a simple comparison of the magnetic energy with energy to be absorbed by the capacitor used ($\frac{1}{2}CV^2$) will give its required value. There are many surge absorbing devices on the market in the form of CR networks, VDR (voltage dependent resistors) or silicon carbide units. If the magnitude of the transient is unknown, a trial and error approach to the problem is often unavoidable

***current surges***

As an example a 1000 W vacuum cleaner has been chosen for evaluation to obtain typical data for the 1000 W universal motor. Motor control was achieved with the use of double RC circuit. No excessive di/dt transients were observed but the peak starting surge current was significant. At low speeds, a starting surge current of up to 50 A peak was noticed with immediate return to a steady state condition. There were more serious conditions at higher speeds when the return to steady state took much longer, about 20 cycles. The first switching on peak surge current is of the same order as stall current.

***snubber circuit***

It is necessary to have a circuit or device which will absorb voltage spikes and eliminate dv/dt switching. The simplest and cheapest circuit for this application is a RC network connected across the Triac as shown in Figure 21.
The basic function and design of the snubber was discussed in the previous paragraph. However, after selecting a suitable capacitor 'C', care must be taken not to damage the Triac by di/dt, as a result of 'C' discharging via a resistor R.

When the Triac is in the blocking state, capacitor 'C' is being charged. At the point of turning 'on', the capacitor 'C' is discharged rapidly, with a current limited only by resistor 'R'. Using a value of 0.1 µF for capacitor C, a resistor R value of 47 Ω gave a di/dt of 25 A/µs. Values of 100 Ω gave 15 A/µs and 820 Ω gave a satisfactory 1 A/µs.
At the point of turning 'off' with inductive loads, a blocking voltage is stressed across the device. If the rate of voltage rise (dv/dt) is too high, the device will turn 'on' again as explained previously. Using low values of resistor R was found to allow resonance and resulted in rapid voltage rises.

***snubber circuit recommendation***

After selecting capacitance 'C' which would adequately absorb the voltage transients spikes and/or give sufficient slope in voltage blocking, the following values of series resistors have been found to give acceptable results :-

0.022 µF in series with 560 Ω
0.047 µF in series with 680 Ω

0.1 μF in series with 820 Ω

The above capacitors will cover most of the requirements ranging from small, medium to large appliances.

***triac selection for 1000 W vacuum cleaner***

It has been demonstrated that the decisive point in selecting Triacs for vacuum cleaners is the surge current capability and di/dt rating. Surges of 50 A peak, decreasing after 20 cycles to a steady value, can be expected. However, a generous safety margin is essential, since other factors such as commutator wear, cleanliness and lubrication of bearings, and behaviour at low temperatures, could all result in higher current surges.

The Triac Type TIC236M (12 A, 600 V) is therefore recommended for the application. Without a snubber network, it can withstand a typical dv/dt of 2 V/μs. The use of a centre gate gives the unusually high di/dt of 200 A/μs, and this allows the use of a generous snubber network to further increase dv/dt capability. With the particular motor used, a snubber circuit consisting of 0.047 μF in series with 680 Ω was found satisfactory. The basic circuit shown in Figure 20 was used, with these components :-

R1 - 250 kΩ
R2 - 22 kΩ
R3 - 3.3 kΩ
C1 - 0.1 μF
C2 - 0.033 μF

**conclusion**

This section shows the importance of current ratings (steady state, surge and di/dt) when selecting Triacs to control universal motors. Similar considerations apply with other loads, such as filament lamps, where high surge current can also be expected. dv/dt with industrial loads, is usually less of a problem, since snubber networks can be used to improve capability. However, care must be taken that di/dt ratings are not exceeded. Whereas occasional false triggering as a result of excessive dv/dt is seldom destructive to the Triac, excessive di/dt can cause degradation and eventual failure.

In view of the many variables present in loads which Triacs are required to control, it is important to evaluate performance thoroughly and provide a generous safety margin to comprehend normal and faulty conditions.

**Lamp Dimmers**

The circuit of Figure 20 is suitable for incandescent lamp dimming and this section is concerned with Triac selection. With normal lamps the "cold" surge current is typically eight times the running current. Halogen lamps double this value and surges of fifteen times running occur when the lamp is cold. When a lamp fails, the filament can form a progressive short which, in bad cases, can blow the circuit fuses. If it is desirable that the Triac does not fail due to a high surge lamp failure, the Triac surge current rating should be selected to be at least one hundred times the lamp running current.

**Triac Switching using Optically Coupled Isolators**

Low power optocoupled Triacs simplify the interfacing between low voltage electronics and power Triacs. Three circuits are shown in Figure 22, which cover resistive loads and inductive loads with low and high sensitivity Triacs.

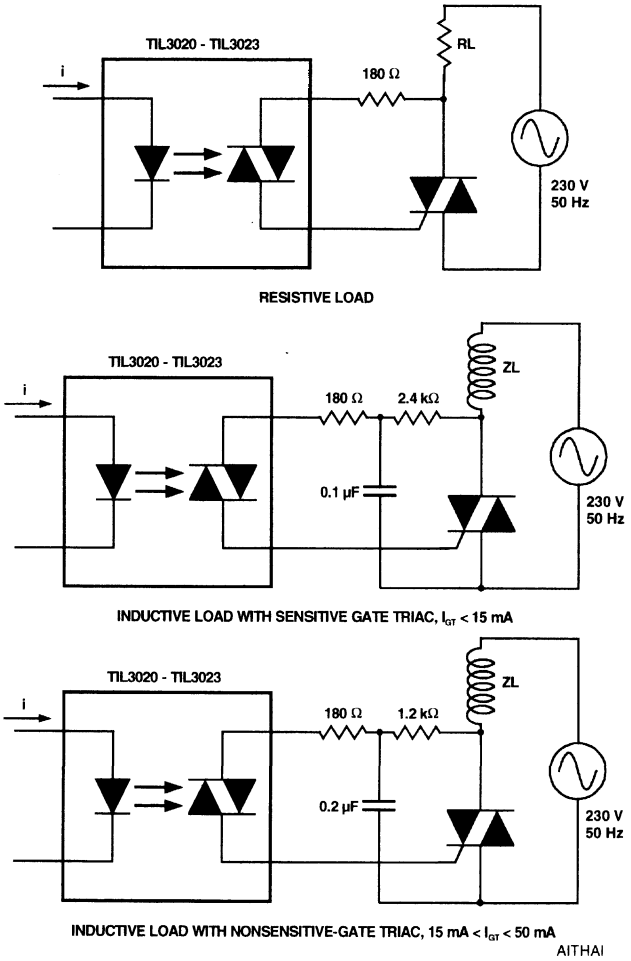



**Figure 22. Optocoupled Triac Drive**

**References**

1. "GE Silicon Controlled Rectifier Manual", Second Edition

2. "Semiconductor and Components Data Book 5 - Diodes, Rectifiers, Optoelectronics and microwave", Texas Instruments, 1969

The information presented in this book is based on the following "B" series of Application Reports written by Jurek Budek

"Triacs-Theory and General Applications", B61, July 1969

"Triacs with Resistive and Inductive Loads", B70, Revised November 1970

"Solid-State Switching using Triacs and Thyristors", B75, October 1969

"Burst Firing Techniques using Triacs", B86, March 1970

"Power Control with Triacs", B130

"Electric Cooker Control", B172

"Triac Speed Control of Universal Motors", B210

# *Mechanical Data*

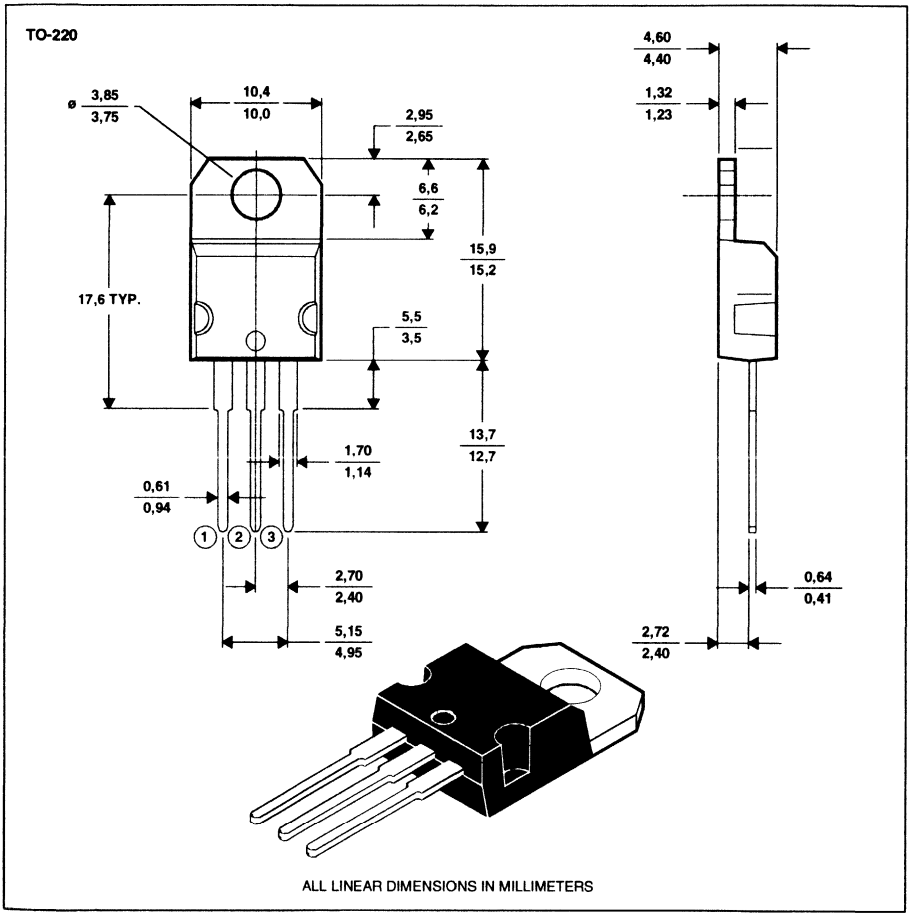
TEXAS INSTRUMENTS

## MECHANICAL DATA

### TO-220

### 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.




NOTE A: The centre pin is in electrical contact with the mounting tab.

MDXXAP

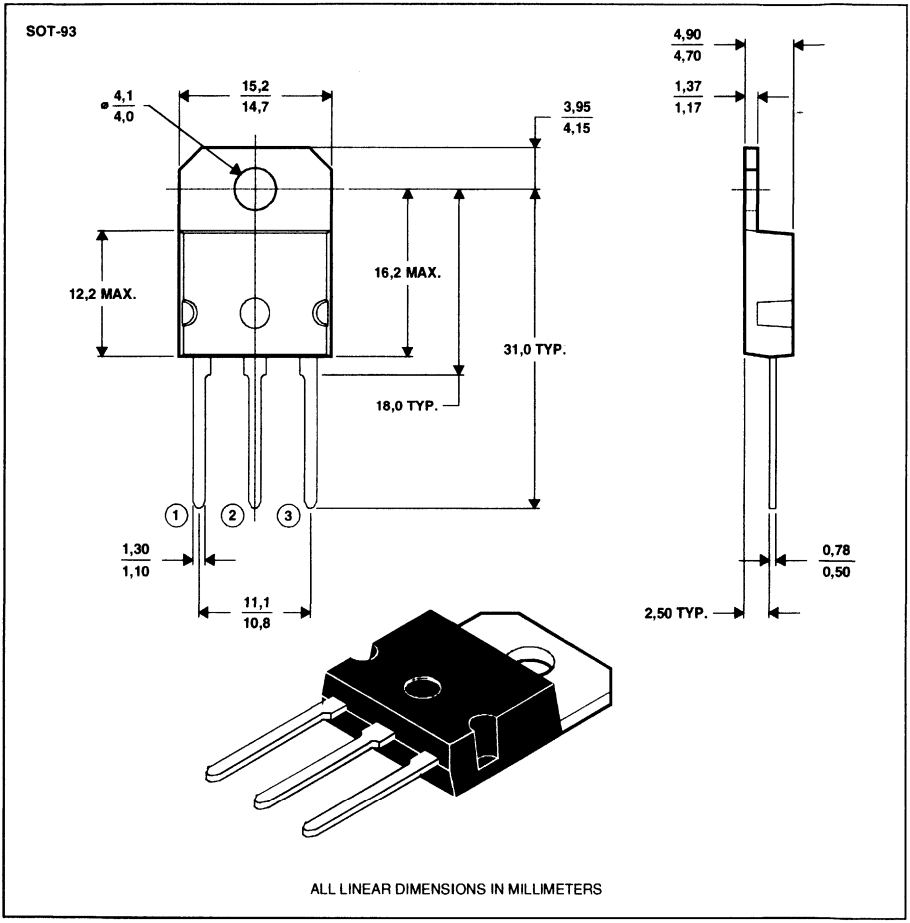
TEXAS INSTRUMENTS

## MECHANICAL DATA

### SOT-93

### 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.




NOTE A: The centre pin is in electrical contact with the mounting tab.

MDXXAW

TEXAS INSTRUMENTS

## MECHANICAL DATA

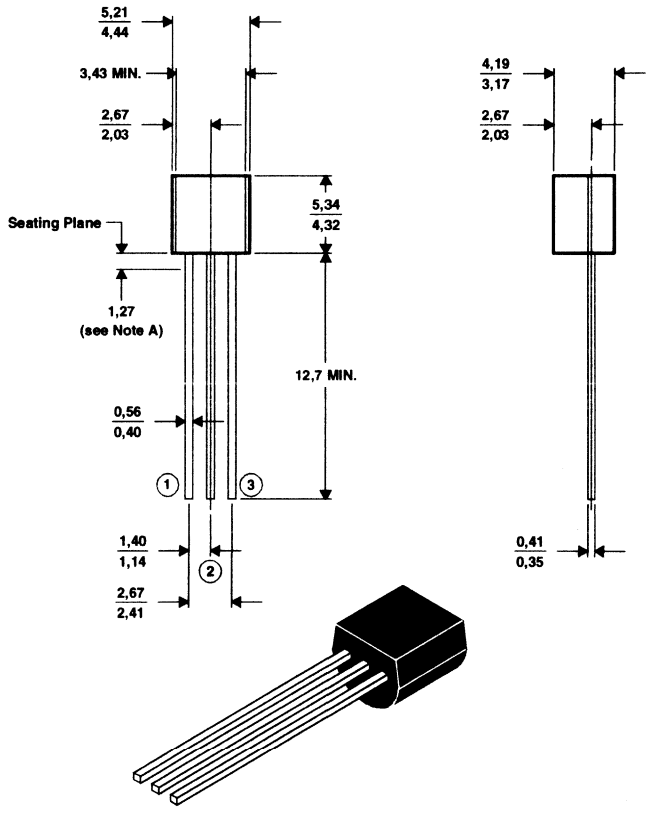
### LP003 (TO-92)

### 3-pin cylindical plastic package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.

LP003 (TO-92)

LP003 Falls Within JEDEC TO-226AA Dimensions

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NOTE A: Lead dimensions are not controlled in this area.

MDXXAX

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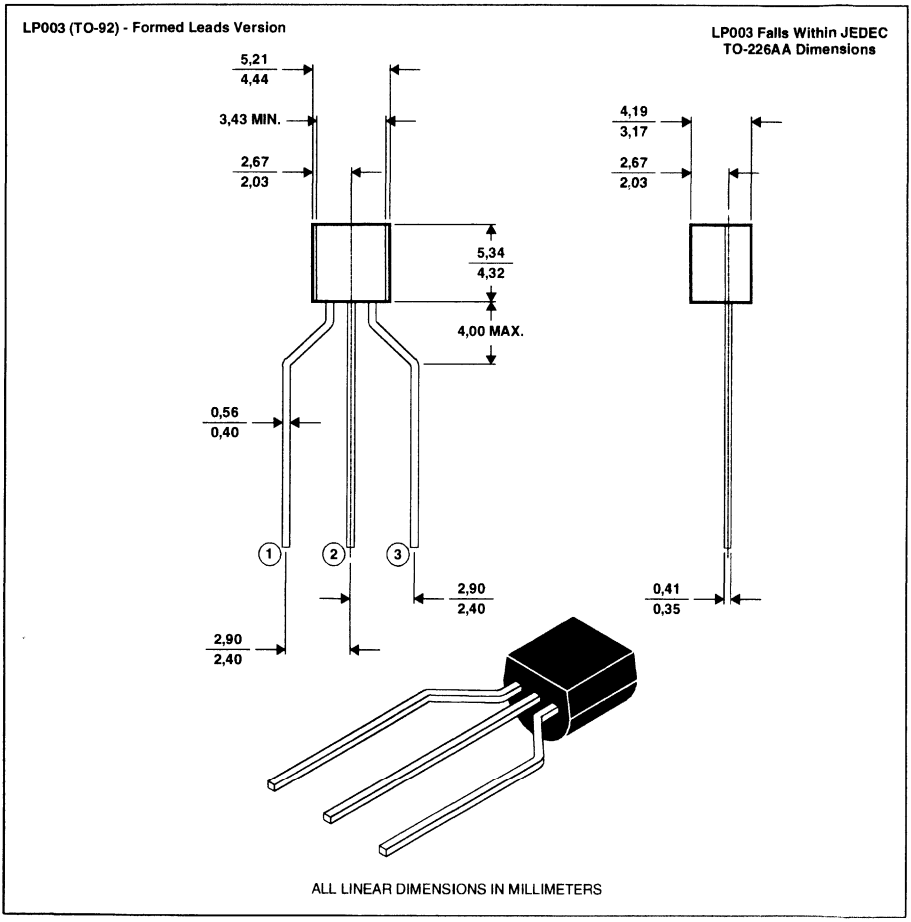
## MECHANICAL DATA

### LP003 (TO-92)

### 3-pin cylindical plastic package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.

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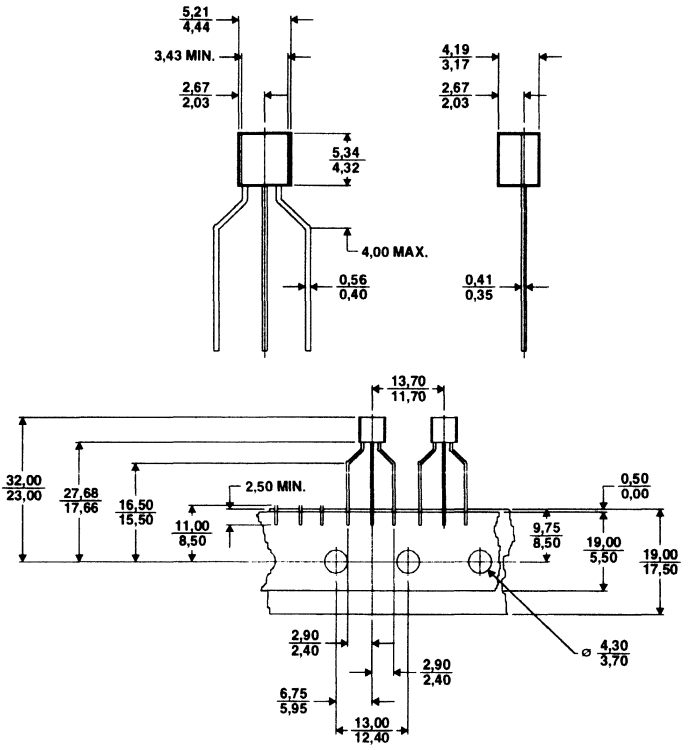
TEXAS INSTRUMENTS

## LPR

### tape dimensions

LP Package (TO-92) Tape (Formed Lead Version)

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